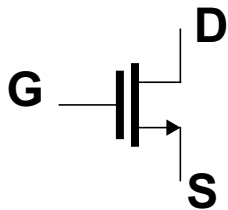

UE4002 Analog IC Design

Problem solutions, supplementary notes

Problems P39: NMOS Operating regions

1. What is the operating region of the following nmos transistors?
Take $V_t = 1V$ and assume the bulk is tied to the source.

(i)

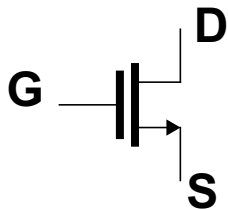


$$V_G = 2V$$

$$V_S = 0V$$

$$V_D = 3V$$

(ii)

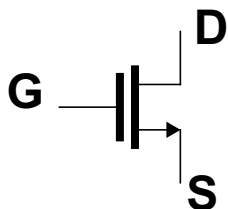


$$V_G = 2V$$

$$V_S = 0V$$

$$V_D = 0.5V$$

(iii)

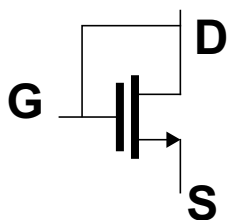


$$V_G = 0.5V$$

$$V_S = 0V$$

$$V_D = 3V$$

(iv)

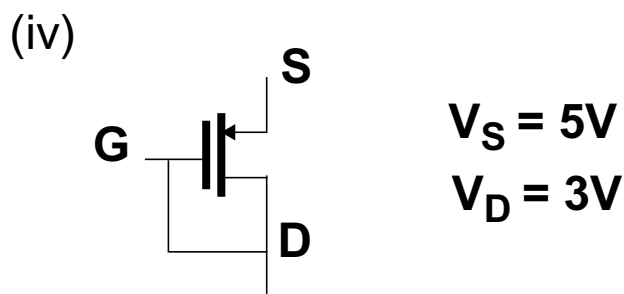
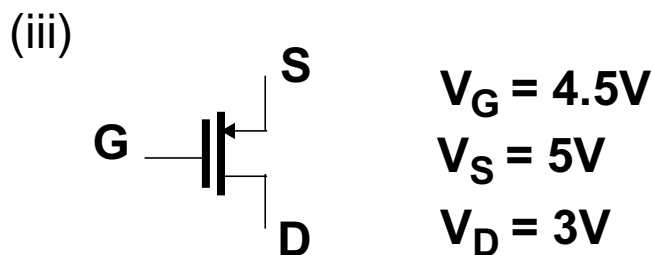
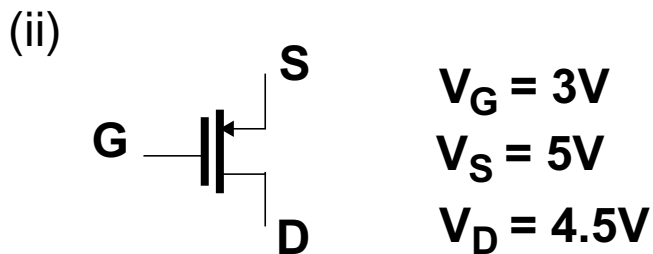
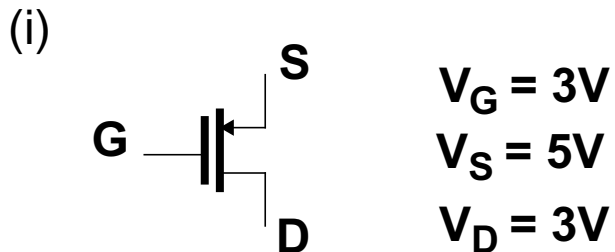


$$V_S = 0V$$

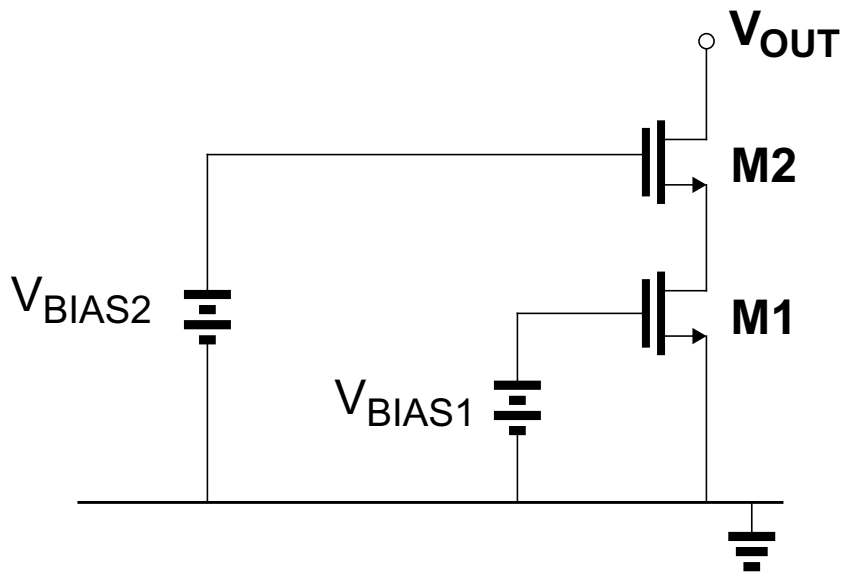
$$V_D = 2V$$

Problems P40: PMOS Operating regions

1. What is the operating region of the following pmos transistors?
Take $V_t = -1V$ and assume the bulk is tied to the source.



Problem P.55 DC Biasing (2)



The body effect may be ignored.

- (i) The circuit shown is to be biased for optimal low-voltage operation.

If

$$V_{BIAS1} = 1.2V$$

$$V_T = 0.8V$$

$$(W/L)_{M2} = (W/L)_{M1}$$

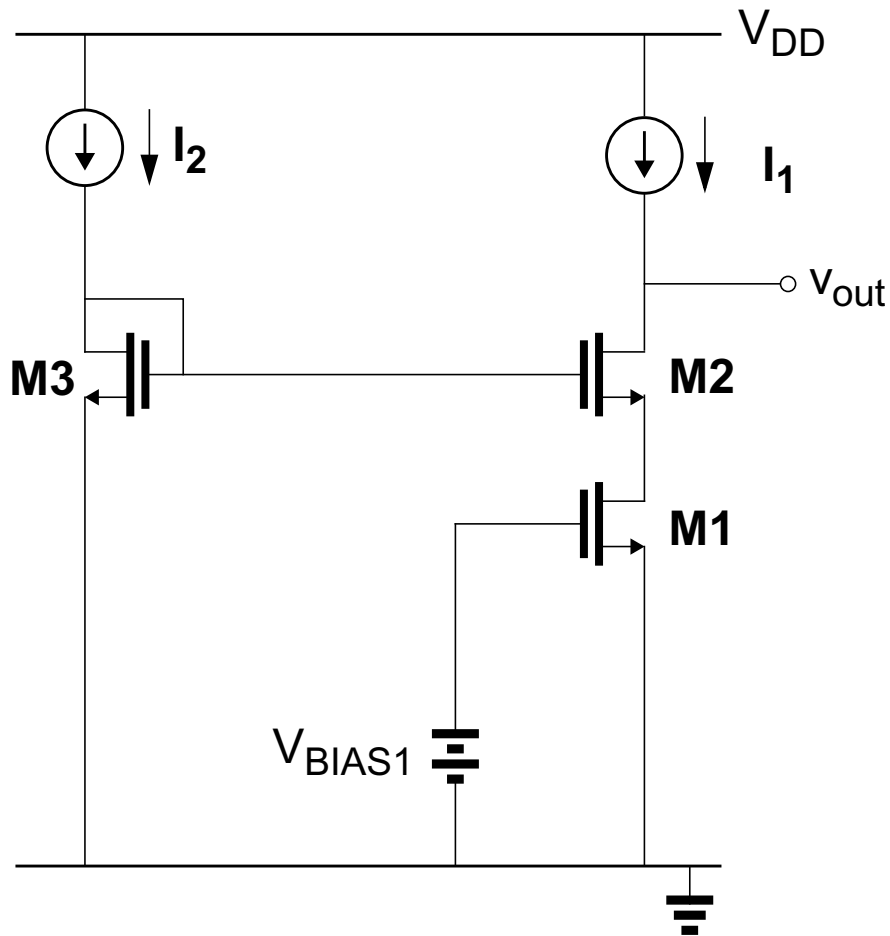
calculate the minimum value of the voltage at the output node (i.e. at the drain of M2) for both M1 and M2 to be in saturation and the value of V_{BIAS2} necessary to achieve this.

Neglect λ for this calculation.

- (ii) Repeat the calculations if the aspect ratio of M2 is four times that of M1

$$\text{i.e. } (W/L)_{M2} = 4 * (W/L)_{M1}$$

Problem P.56: DC Biasing (3)



The body effect may be ignored.

- (i) The circuit shown is to be biased for optimal low-voltage operation.

If

$$V_{BIAS1} = 1.25V, V_T = 1V, I_1 = 100\mu A$$

$$(W/L)_{M1} = (W/L)_{M2} = (W/L)_{M3} = 16\mu m / 1\mu m$$

calculate the minimum value of the voltage at the output node (i.e. at the drain of $M2$) for both $M1$ and $M2$ to be in saturation and the value of I_2 necessary to achieve this.

Neglect λ for this calculation.

- (i) For low power I_2 is changed to $40\mu A$.

What value of $(W/L)_{M3}$ is required to preserve the bias conditions of $M1$ and $M2$.

Solution (Problem P.55) DC Biasing (2)

(i) For M1 to be in saturation then

$$V_{DS1} \geq V_{GS1} - V_t$$

$$(V_{DS1})_{min} = V_{GS1} - V_t = 1.2V - 0.8V = 0.4V$$

If M2 is in saturation its drain current is given by

$$I_{D2} = \frac{K'_n W}{2 L} (V_{GS2} - V_t)^2$$

Since M2 has same drain current, W/L and V_t as M1 it will also have the same V_{GS}

$$(V_{DS2})_{min} = V_{GS2} - V_t = 0.4V$$

so minimum voltage at the output for both transistors to be in saturation is given by

$$V_{out} = (V_{DS1})_{min} + (V_{DS2})_{min} = 0.8V$$

The bias voltage V_{BIAS2} necessary to achieve this is given by

$$V_{BIAS2} = V_{GS2} + (V_{DS1})_{min} = 1.2V + 0.4V = 1.6V$$

Solution (Problem P.55) DC Biasing (2) cont.

(ii)

Since $I_{D1} = I_{D2}$ then

$$\frac{K'_n}{2} \left(\frac{W}{L} \right) (V_{GS1} - V_t)^2 = \frac{K'_n}{2} 4 \left(\frac{W}{L} \right) (V_{GS2} - V_t)^2$$

$$V_{GS2} - V_t = \frac{V_{GS1} - V_t}{2} = 0.2V$$

$$V_{GS2} = 1V$$

$$(V_{DS2})_{min} = 0.2V$$

so minimum voltage at the output for both transistors to be in saturation is given by

$$V_{out} = (V_{DS1})_{min} + (V_{DS2})_{min} = 0.6V$$

The bias voltage V_{BIAS2} necessary to achieve this is given by

$$V_{BIAS2} = V_{GS2} + (V_{DS1})_{min} = 1.0V + 0.4V = 1.4V$$

Solution (Problem P.56) DC Biasing (3)

(i) For M1 to be in saturation then

$$V_{DS1} \geq V_{GS1} - V_t$$

$$(V_{DS1})_{min} = V_{GS1} - V_t = 1.25V - 1V = 0.25V$$

If M2 is in saturation its drain current is given by

$$I_{D2} = \frac{K'_n W}{2L} (V_{GS2} - V_t)^2$$

Since M2 has same drain current, W/L and V_t as M1 it will also have the same V_{GS}

$$(V_{DS2})_{min} = V_{GS2} - V_t = 0.25V$$

so minimum voltage at the output for both transistors to be in saturation is given by

$$V_{out} = (V_{DS1})_{min} + (V_{DS2})_{min} = 0.5V$$

The bias voltage V_{GS3} necessary to achieve this is given by

$$V_{GS3} = V_{GS2} + (V_{DS1})_{min} = 1.25V + 0.25V = 1.5V$$

$$I_{D1} = \frac{K'_n \left(\frac{W}{L}\right)}{2} (V_{GS1} - V_t)^2$$

$$I_{D3} = \frac{K'_n \left(\frac{W}{L}\right)}{2} (V_{GS3} - V_t)^2$$

$$\frac{I_{D1}}{I_{D3}} = \frac{(V_{GS1} - V_t)^2}{(V_{GS3} - V_t)^2}$$

$$I_{D3} = I_{D1} \frac{(V_{GS3} - V_t)^2}{(V_{GS1} - V_t)^2} = 100\mu A \frac{(0.5)^2}{(0.25)^2} = 400\mu A$$

Solution (Problem P.56) DC Biasing (3) cont.

(ii)

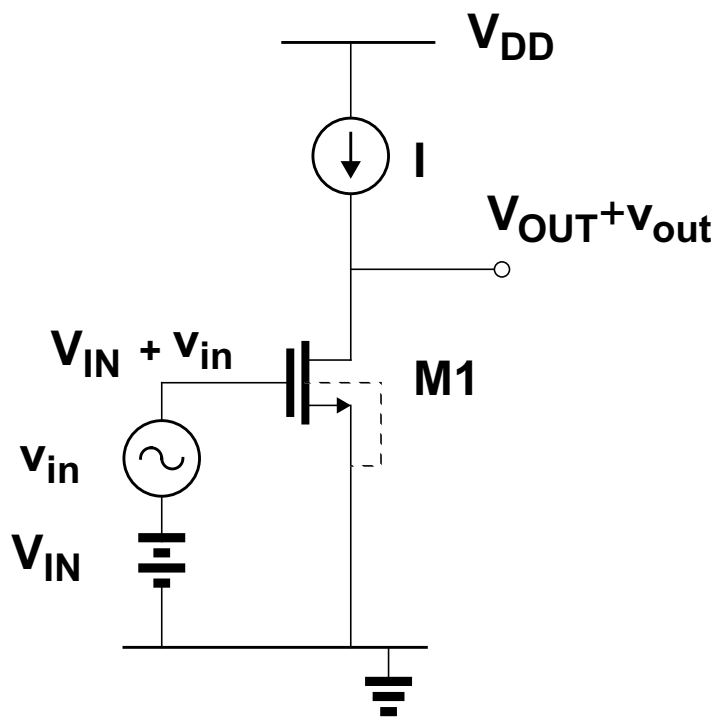
Need same $V_{GS3} - V_t$

$$I_{D3} = \frac{K'_n}{2} \left(\frac{W}{L} \right)_3 (V_{GS3} - V_t)^2$$

If I_{D3} is reduced by a factor 10, then W/L also needs to be reduced by ten

$$\left(\frac{W}{L} \right)_{M3} = 1.6$$

Problem P.72: Small-signal model



- (i) Draw the small-signal equivalent circuit
- (ii) What is the small-signal gain in terms of the small-signal parameters of M1
- (iii) Explain the result in terms of the large-signal behavior assuming M1 is in saturation
- (iv) What is the small signal gain if $I=100\mu\text{A}$, $\lambda=0.1$, $V_{GS}-V_t=200\text{mV}$

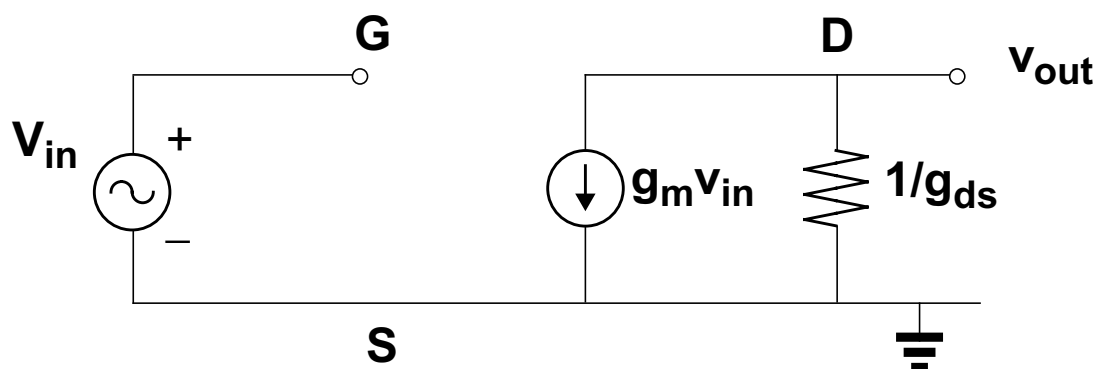
Solution Problem P.72: Small-signal model.

Body and source tied together

$$\Rightarrow v_{bs} = 0$$

\Rightarrow can ignore g_{mb}

(i) Equivalent small-signal circuit



(ii) Small-signal voltage gain

Use KCL at output node

$$g_m v_{in} + v_{out} g_{ds} = 0$$

$$\frac{v_{out}}{v_{in}} = -\frac{g_m}{g_{ds}}$$

(iii) In terms of large-signal behavior

$$I_D = \frac{K'_n W}{2L} (V_{GS} - V_t)^2 (1 + \lambda V_{DS})$$

Small increase in V_{GS}

I_D is fixed by the ideal DC current source

$\Rightarrow V_{DS}$ must decrease to restore equilibrium

Also: V_{DS} must decrease much more than the increase in V_{GS} as I_D is a weak function of V_{DS} and a strong function of V_{GS} in sat.

\Rightarrow Gain

(iv) What is the small signal gain if $I=100\mu A$, $\lambda=0.1$, $V_{GS}-V_t=200mV$

$$g_m = \frac{2I_D}{V_{GS} - V_t} = \frac{2 \times 100\mu A}{200mV} = 1mA/V$$

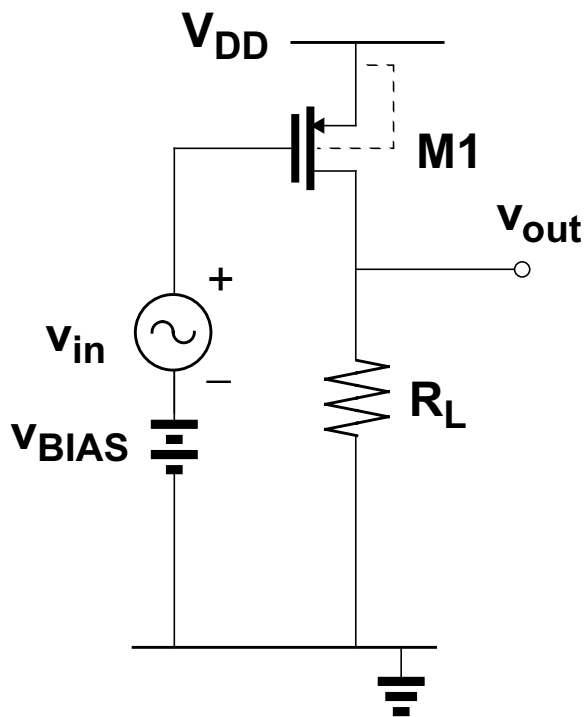
$$g_{ds} = \lambda I_D = 0.1V^{-1} 100\mu A = 10\mu A/V$$

$$\left| \frac{v_{out}}{v_{in}} \right| = \frac{1000\mu A/V}{10\mu A/V} = 100$$

Note: gain usually expressed in dB

$$A = 20\log \left| \frac{v_{out}}{v_{in}} \right| = 40dB$$

Problem: PMOS common-source stage with resistive load

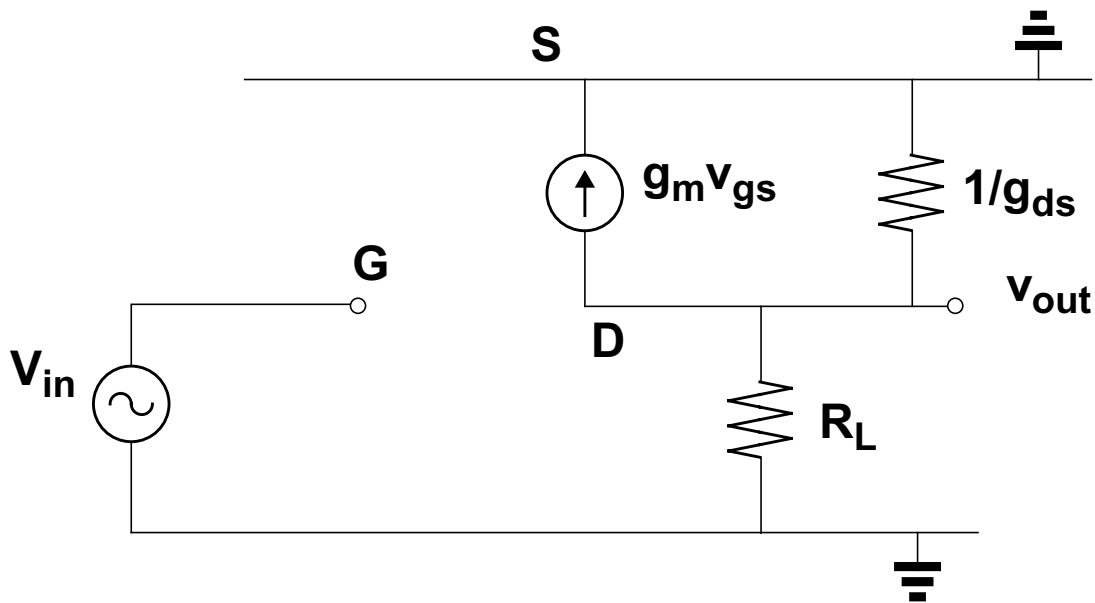


$$V_{BIAS}=3.5V, V_t=1V, \lambda=0.05V^{-1}, I_{D1}=100\mu A, V_{DD}=5V$$

- (i) Draw the small signal model for the circuit shown.
- (ii) What is the low-frequency small signal voltage gain (v_{out}/v_{in}) in terms of the small-signal parameters and R_L ?
- (iii) What is the value of g_{m1} ?
What is the value of g_{ds1} ?
- (iv) What is the largest value of R such that M1 is operating in the saturated region?
- (v) What value of R gives the largest small-signal gain?
What is the largest small-signal gain?

Solution Prob. P83 (PMOS common-source with resistive load):

(i) Equivalent small-signal circuit



(ii) Small-signal voltage gain

Use KCL at output node

$$g_m v_{gs} + \frac{v_{out}}{R_L} + v_{out} g_{ds} = 0$$

$$g_m v_{in} = -v_{out} \left(\frac{1}{R_L} + g_{ds} \right)$$

$$\frac{v_{out}}{v_{in}} = -\frac{g_m}{g_{ds} + \frac{1}{R_L}}$$

(iii) What is the value of g_{m1} ? What is the value of g_{ds1} ?

$$g_m = \frac{2I_D}{|V_{GS}| - |V_t|} = \frac{2 \times 100\mu A}{1.5V - 1V} = 400\mu A/V$$

$$g_{ds} = \lambda I_D = 0.05V^{-1} 100\mu A = 5\mu A/V$$

(iv) What is largest value of R_L such that M1 is in saturation?

$$\text{Minimum } |V_{DS}| \text{ for M1 in saturation} = |V_{GS}| - |V_t| = 0.5V$$

$$\Rightarrow \text{Maximum voltage at } v_{out} = V_{DD} - 0.5V = 4.5V$$

\Rightarrow Maximum value of R_L given by

$$R_{L(max)} = \frac{v_{out(max)}}{I_D} = \frac{4.5V}{100\mu A} = 45k\Omega$$

(v) What is the largest small-signal gain?

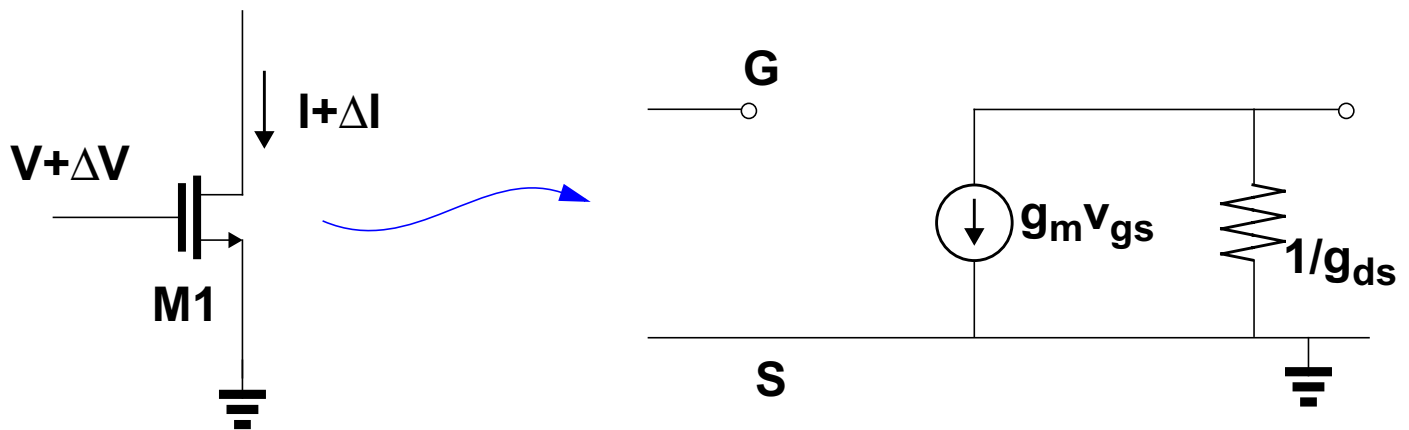
$$Gain_{max} = -\frac{g_m}{g_{ds} + \frac{1}{R_L}} = -\frac{400\mu A/V}{5\mu A/V + \frac{1}{45k\Omega}} = -14.7$$

In dB:

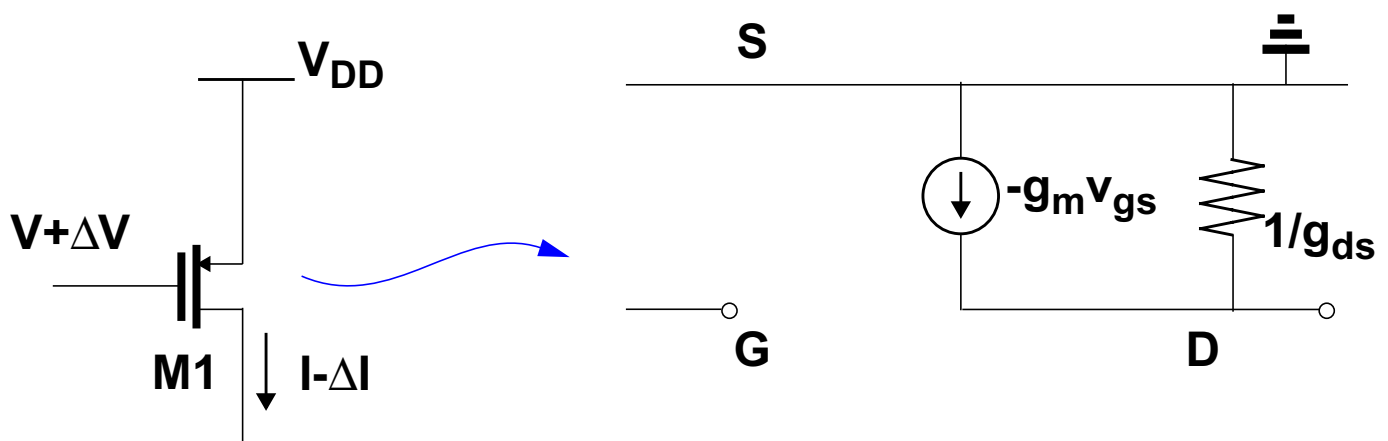
$$Gain_{max} = 20\log\left|\frac{v_{out}}{v_{in}}\right| = 23dB$$

Note on NMOS and PMOS small signal models

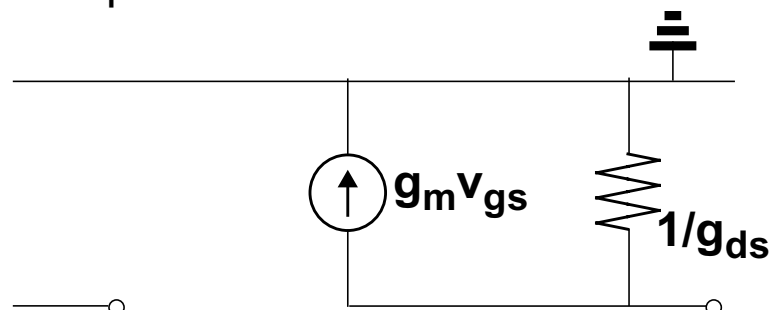
NMOS: Increase in gate voltage w.r.t. source results in positive incremental current from drain to source



PMOS: Increase in gate voltage w.r.t. source results in negative incremental current from drain to source

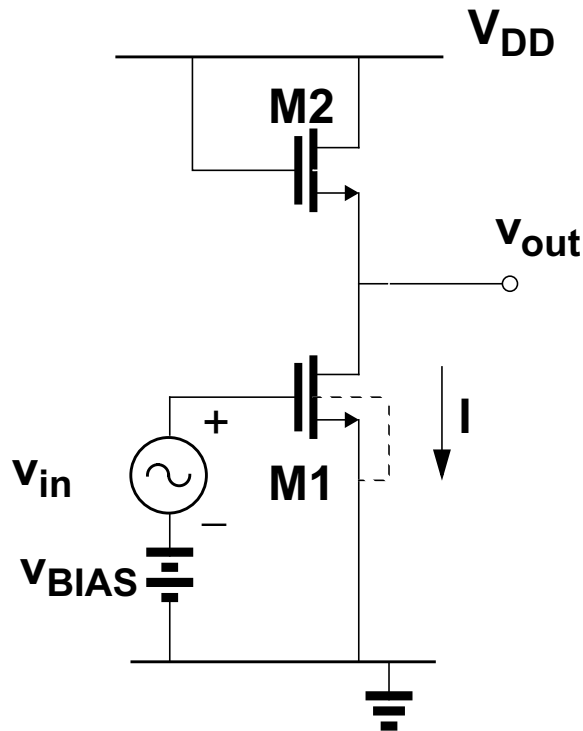


which is equivalent to



so that the direction of the small-signal current source is the same for NMOS and PMOS i.e. from drain to source.

Problem P93: - Common source stage with NMOS Diode Load



Assume M1 is biased in saturation.

- (i) Draw the small signal model for the circuit shown.
- (ii) What is the low-frequency small signal voltage gain (v_{out}/v_{in}) in terms of the small-signal parameters?

Assume that $g_{m1} \gg g_{ds1}, g_{ds2}$ and that $g_{m2} \gg g_{ds1}, g_{ds2}$

- (iii) Calculate the gain if

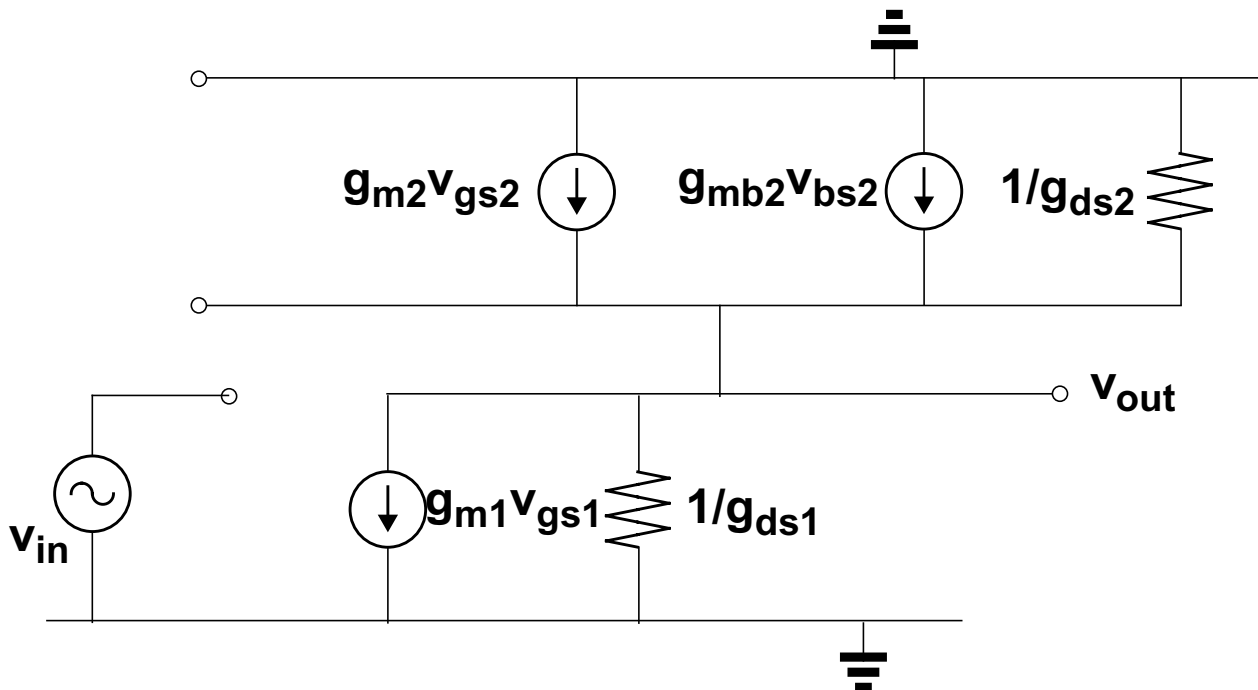
$$W1=25, L1=1$$

$$W2=1, L2=1$$

$$\eta=0.3$$

Solution Prob. P93 (NMOS common-source stage with NMOS diode load):

(i) Equivalent small-signal circuit



(ii) Small-signal voltage gain

Use KCL at output node

$$g_{m1}v_{gs1} + v_{out}g_{ds1} - g_{m2}v_{gs2} - g_{mb2}v_{bs2} + v_{out}g_{ds2} = 0$$

$$g_{m1}v_{in} + v_{out}g_{ds1} + g_{m2}v_{out} + g_{mb2}v_{out} + v_{out}g_{ds2} = 0$$

$$\frac{v_{out}}{v_{in}} = -\frac{g_{m1}}{g_{m2} + g_{mb2} + g_{ds1} + g_{ds2}} \cong -\frac{g_{m1}}{g_{m2} + g_{mb2}}$$

(iii) Calculate the gain if

$W_1=25, L_1=1$

$W_2=1, L_2=1$

$\eta=0.3$

$$\frac{v_{out}}{v_{in}} = -\frac{g_{m1}}{g_{m2} + g_{mb2}}$$

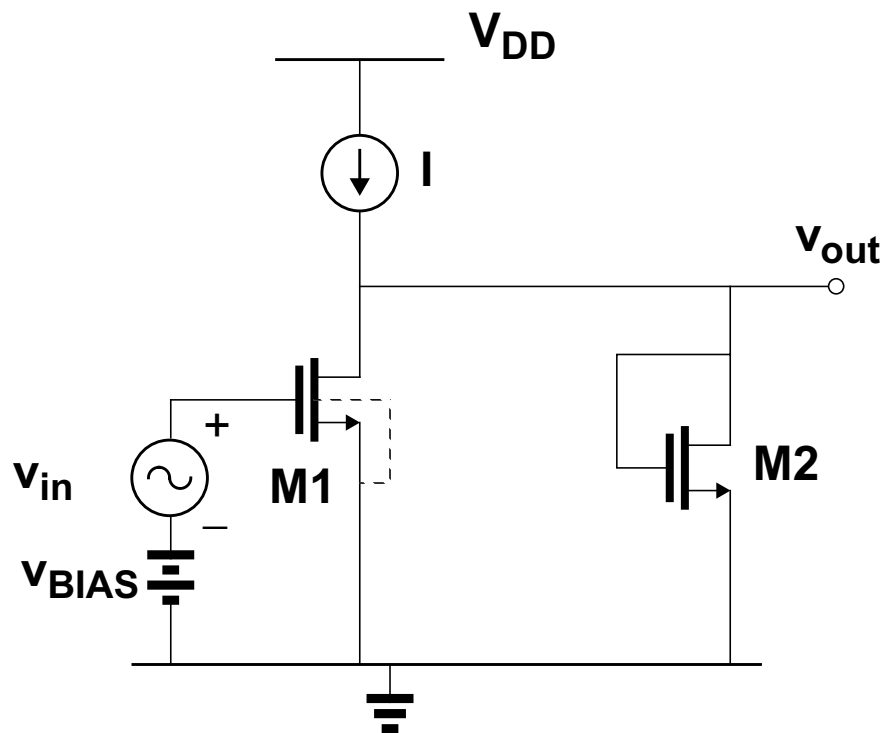
$$= -\frac{g_{m1}}{g_{m2}(1 + \eta)}$$

$$= -\frac{\sqrt{2K'_n \frac{W_1}{L_1} I_{D1}}}{\sqrt{2K'_n \frac{W_2}{L_2} I_{D2}}} \cdot \frac{1}{1 + \eta}$$

$$= -\frac{\sqrt{\frac{W_1}{L_1}}}{\sqrt{\frac{W_2}{L_2}}} \cdot \frac{1}{1 + \eta}$$

$$= -\sqrt{\frac{25}{1}} \cdot \frac{1}{1 + 0.3} = 3.8 \Leftrightarrow 11.7dB$$

To eliminate the body effect on the load transistor, use a 'folded' load.

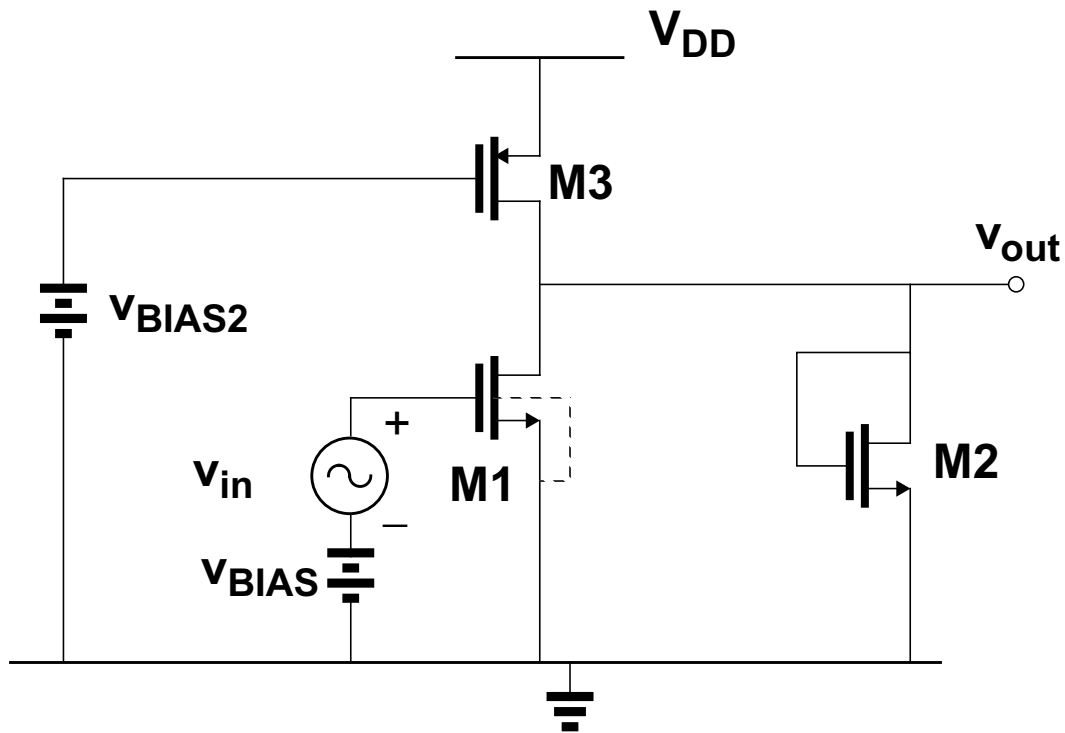


$$\frac{v_{out}}{v_{in}} = -\frac{g_{m1}}{g_{m2} + g_{ds1} + g_{ds2}} \cong -\frac{g_{m1}}{g_{m2}}$$

Looked at from another perspective:

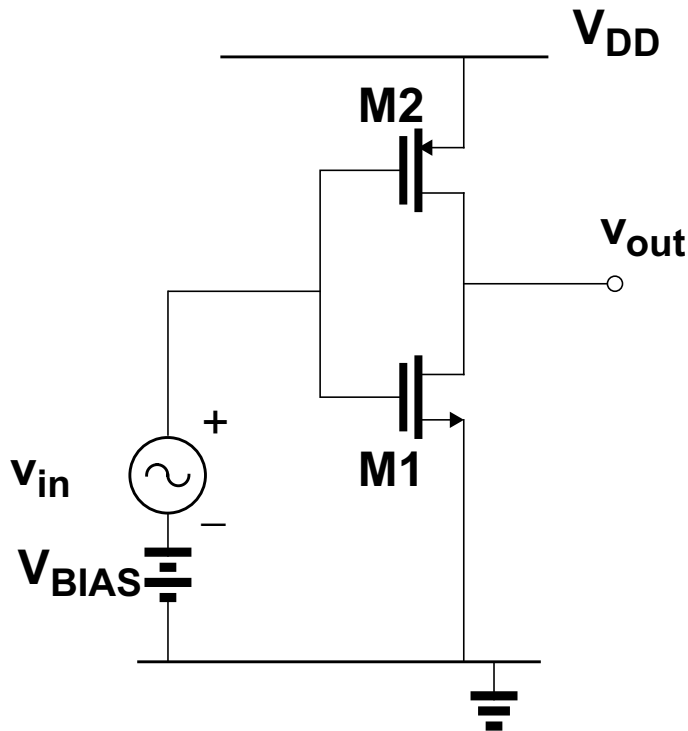
A change in input voltage causes a change in the drain current of M1. Because I is clamped this produces an equal change in M2, which is converted to a voltage by the impedance of M2

Practical implementation of the 'folded' load - PMOS supplies current



$$\frac{v_{out}}{v_{in}} = -\frac{g_{m1}}{g_{m2} + g_{ds1} + g_{ds2} + g_{ds3}} \cong -\frac{g_{m1}}{g_{m2}}$$

Problem: CS stage (CMOS Inverter)



Assume M1 and M2 are biased in saturation.

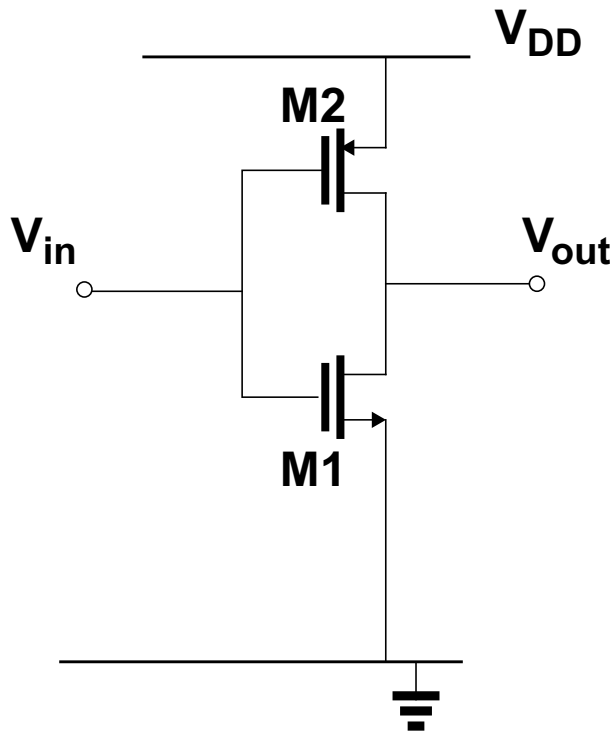
- (i) Draw the small signal model for the circuit shown.
- (ii) Derive an expression for the low-frequency small signal voltage gain (v_{out}/v_{in}) in terms of the small-signal parameters?

Assume that $g_{m1} \gg g_{ds1}, g_{ds2}$ and that $g_{m2} \gg g_{ds1}, g_{ds2}$

- (iii) Calculate the gain if

$$\begin{aligned} V_{DD} &= 3, V_{BIAS} = 1.5, |V_t| = 1 \\ I_D &= 100 \mu A, \lambda_p = \lambda_n = 0.05 V^{-1} \\ W_1 &= 10, L_1 = 1 \\ W_2 &= 40, L_2 = 1 \end{aligned}$$

Problem P104 CS stage (CMOS Inverter)



How does this stage work?

Assume both devices are in saturation, and so obey the equation

$$|I_D| = \frac{K'}{2} \frac{W}{L} (|V_{GS}| - |V_t|)^2 (1 + \lambda |V_{DS}|)$$

Small increase in $V_{in} \Rightarrow V_{GS}$ M1 increases

\Rightarrow M1 'wants' more drain current from M2

$\Rightarrow V_{out}$ goes down to pull more current from M2 (by increasing $|V_{DS2}|$)

At the same time $|V_{GS}|$ M2 decreases

\Rightarrow M2 'wants' less drain current from M1

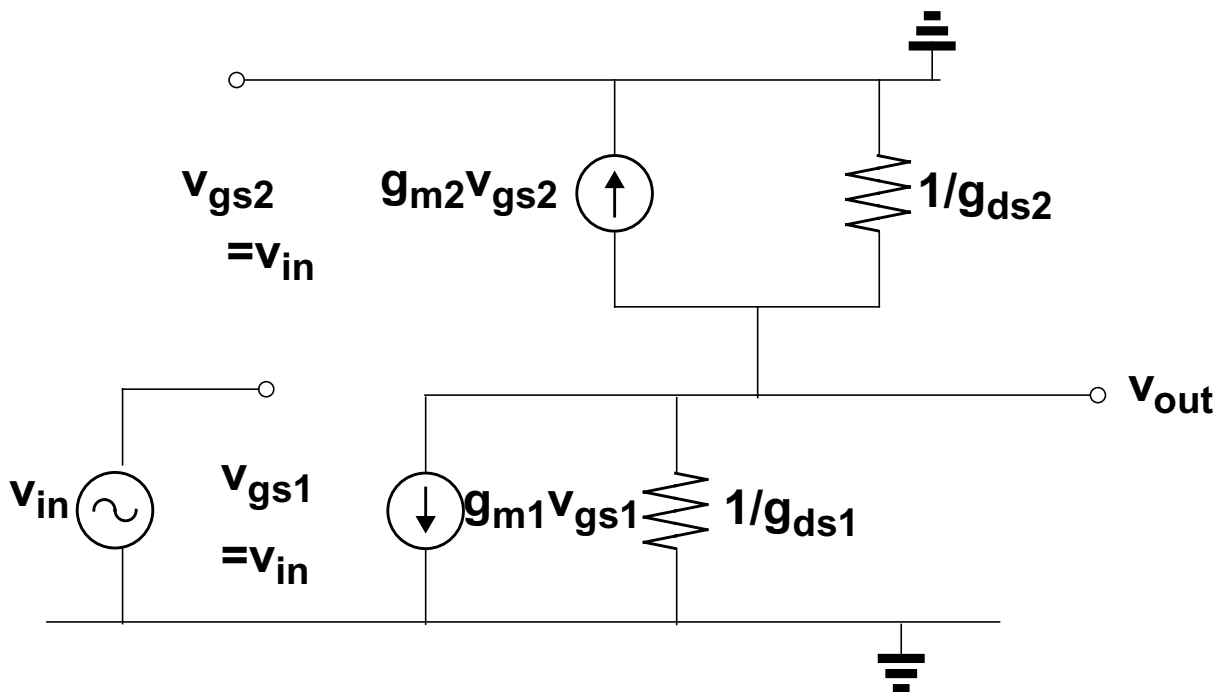
$\Rightarrow V_{out}$ goes down to cut off current from M1 (by decreasing $|V_{DS1}|$)

V_{out} drops until equilibrium is restored.

Note: gain is higher than circuit on P.98 because M2 contributes.

Solution

(i) Draw the small signal model for the circuit shown.



(ii) Derive an expression for the low-frequency small signal voltage gain (v_{out}/v_{in}) in terms of the small-signal parameters?

Sum current at output node

$$g_{m1}v_{gs1} + g_{m2}v_{gs2} + v_{out}g_{ds1} + v_{out}g_{ds2} = 0$$

$$g_{m1}v_{in} + g_{m2}v_{in} + v_{out}g_{ds1} + v_{out}g_{ds2} = 0$$

$$\frac{v_{out}}{v_{in}} = -\frac{g_{m1} + g_{m2}}{g_{ds1} + g_{ds2}}$$

(iii) Calculate the gain if

$$\begin{aligned}V_{DD} &= 3, V_{BIAS} = 1.5, |V_t| = 1 \\I_D &= 100\mu A, \lambda_p = \lambda_n = 0.05V^{-1} \\W_1 &= 10, L_1 = 1 \\W_2 &= 40, L_2 = 1\end{aligned}$$

$$I_{D1} = I_{D2} = 100\mu A,$$

$$V_{GS1} - V_{t1} = |V_{GS2}| - |V_{t2}| = 0.5V$$

$$g_{m1} = g_{m2} = \frac{2I_D}{V_{GS} - V_t} = \frac{2 \times 100\mu A}{0.5V} = 400\mu A/V$$

$$\lambda_1 = \lambda_2 = 0.05V^{-1}$$

$$g_{ds1} = g_{ds2} = \lambda I_D = 0.05V^{-1} \times 100\mu A = 5\mu A/V$$

$$Gain = \frac{v_{out}}{v_{in}} = -\frac{g_{m1} + g_{m2}}{g_{ds1} + g_{ds2}} = -\frac{800}{10} = 80$$

$$dBGain = 20\log\left|\frac{v_{out}}{v_{in}}\right| = 38dB$$

y-parameters summary

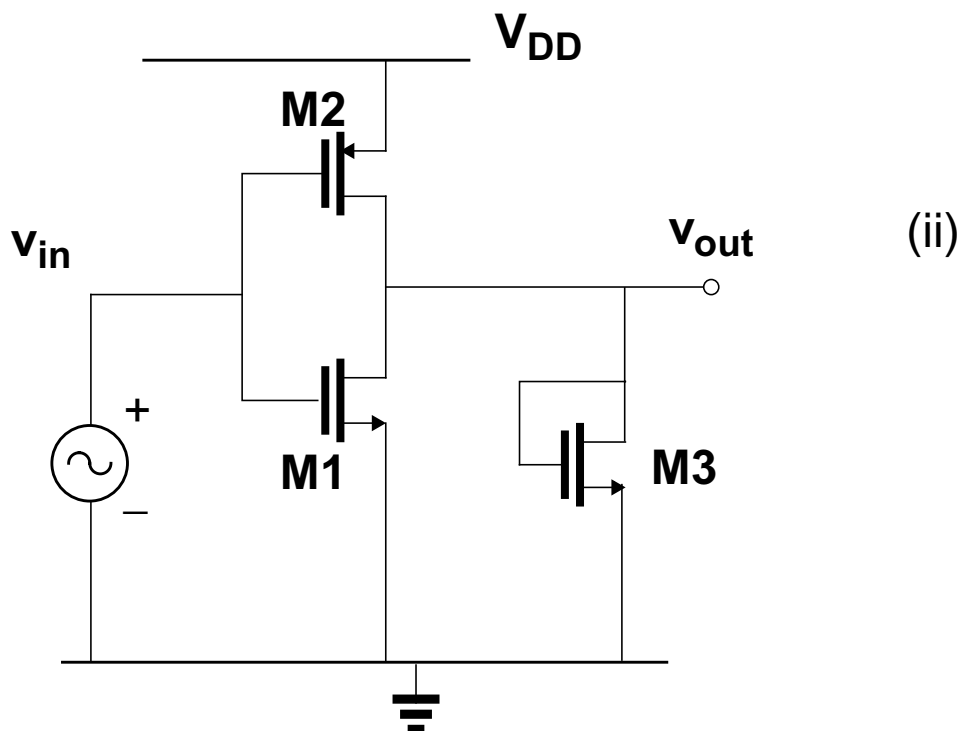
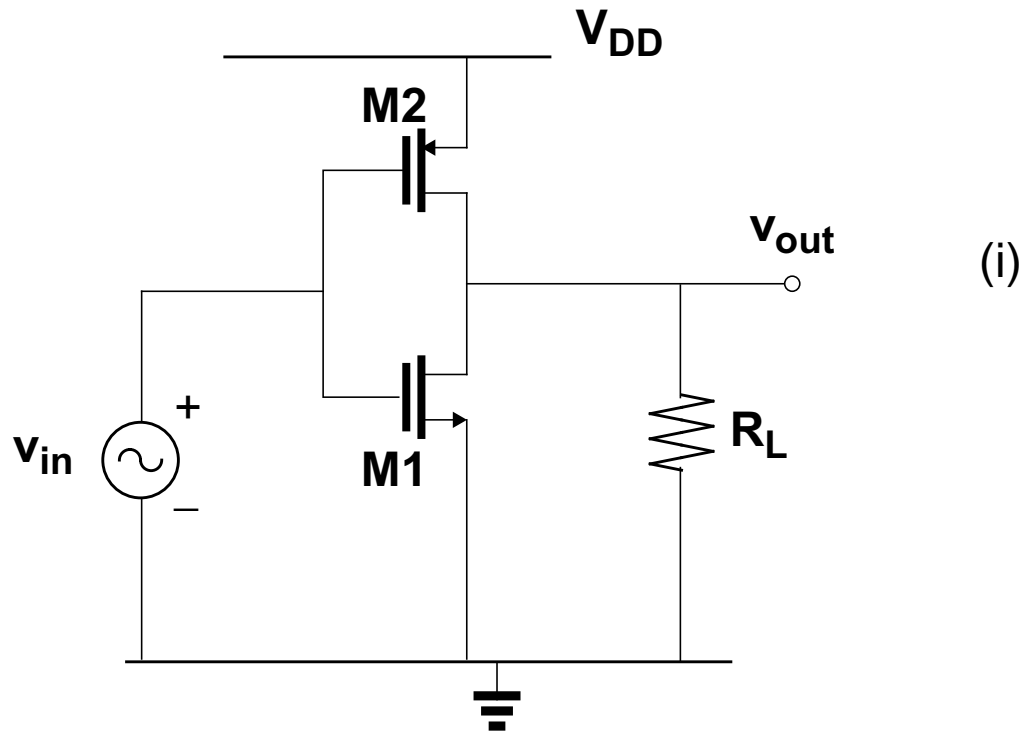
Razavi Chap. 3

Lemma: *In a linear circuit, the voltage gain is equal to $-G_m R_{out}$, where G_m denotes the transconductance of the circuit when the output is shorted to ground, and R_{out} represents the output resistance of the circuit when the input voltage is set to zero.*

In the notes we more often use G_{out} . When a load with conductance G_L is added we simply add its conductance to G_{out} , so the voltage gain is equal to $-G_m/(G_{out}+G_L)$ or **transconductance of the circuit divided by the total conductance at the output node**.

This is a very useful concept in circuits where it is easy to determine G_m and G_{out} by inspection e.g. common-source stage, cascode stage, differential pair.

Problem P109: CMOS Inverter & y-parameters



Use y-parameters to calculate the small-signal gain of a CMOS inverter (both devices are in saturation) with

- (i) resistive load
- (ii) nmos diode load

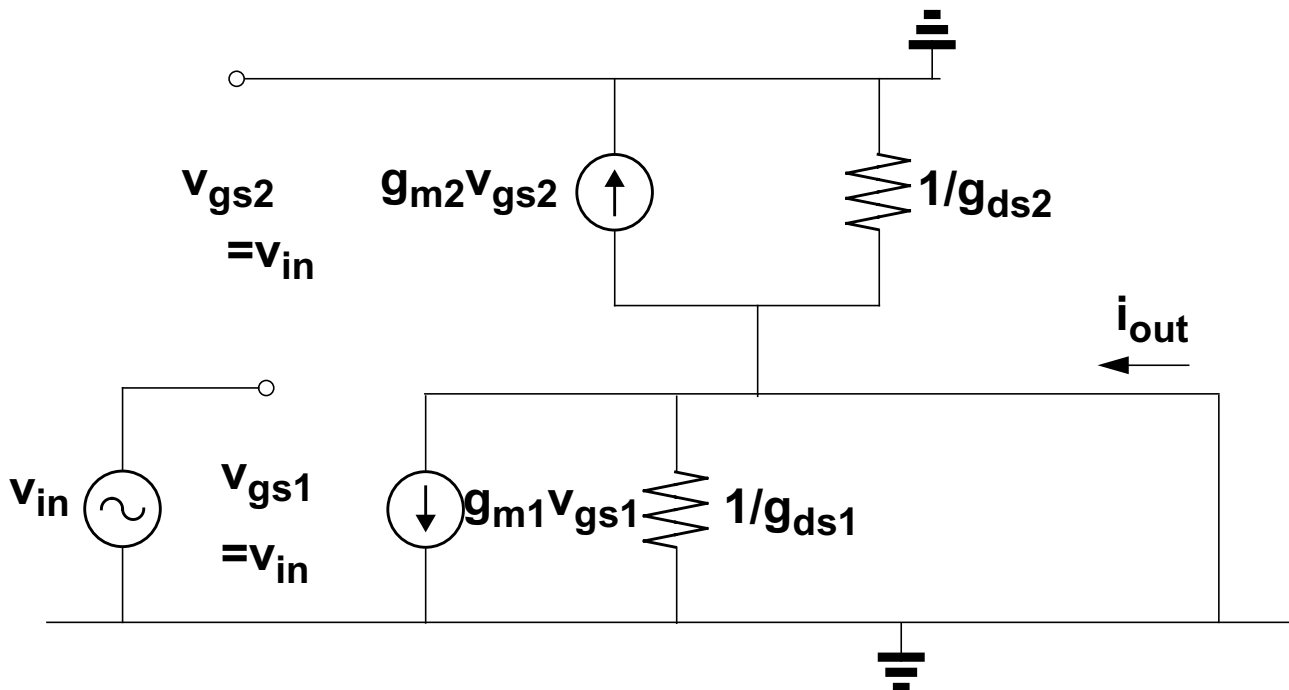
Problem P. 109 CMOS Inverter & y-parameters.

First derive expressions for G_m and R_{out}/G_{out} .

G_m

For G_m , small-signal circuit as previously, with output shorted to ground.

Calculate i_{out}/v_{in} .



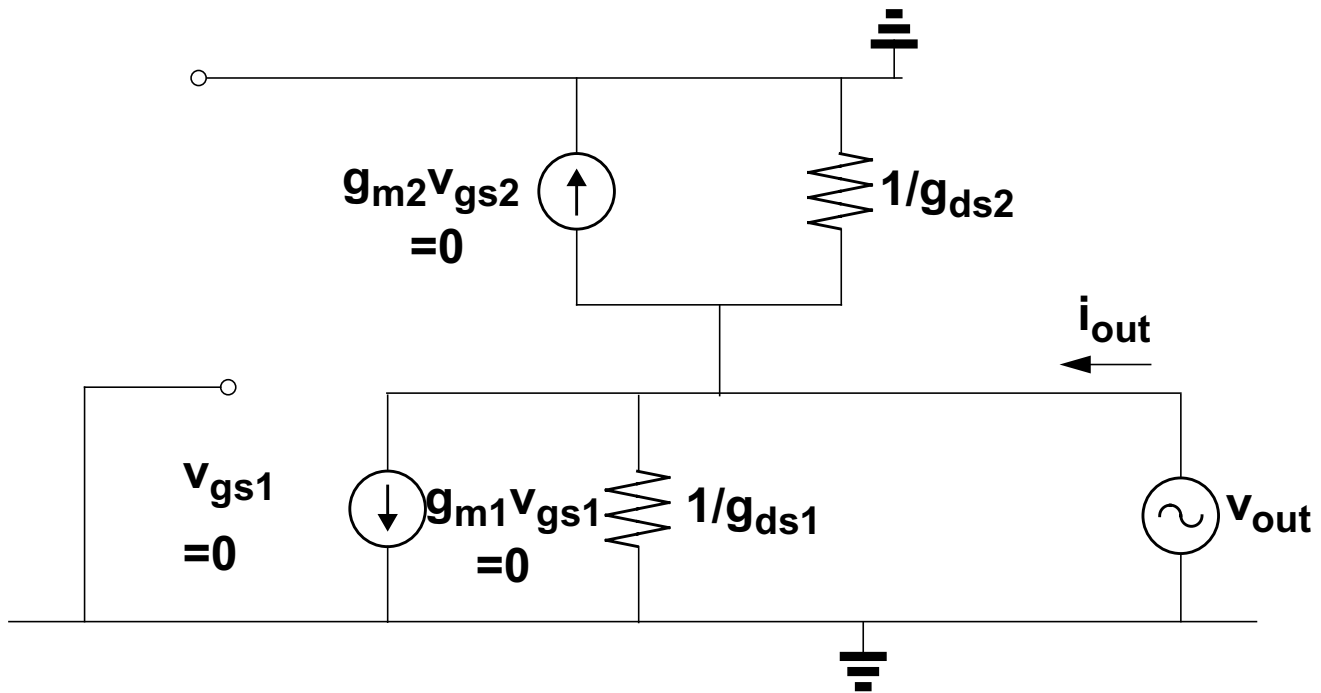
$$i_{out} = g_{m1}v_{in} + g_{m2}v_{in}$$

$$G_m \equiv \frac{i_{out}}{v_{in}} = g_{m1} + g_{m2}$$

G_{out}

For G_{out} , short input to ground.

Apply voltage at output and calculate i_{out}/v_{in}



$$i_{out} = v_{out}g_{ds1} + v_{out}g_{ds2}$$

$$G_{out} \equiv \frac{i_{out}}{v_{out}} = g_{ds1} + g_{ds2}$$

$$Gain_{unloaded} \equiv \frac{G_m}{G_{out}} = \frac{g_{m1} + g_{m2}}{g_{ds1} + g_{ds2}}$$

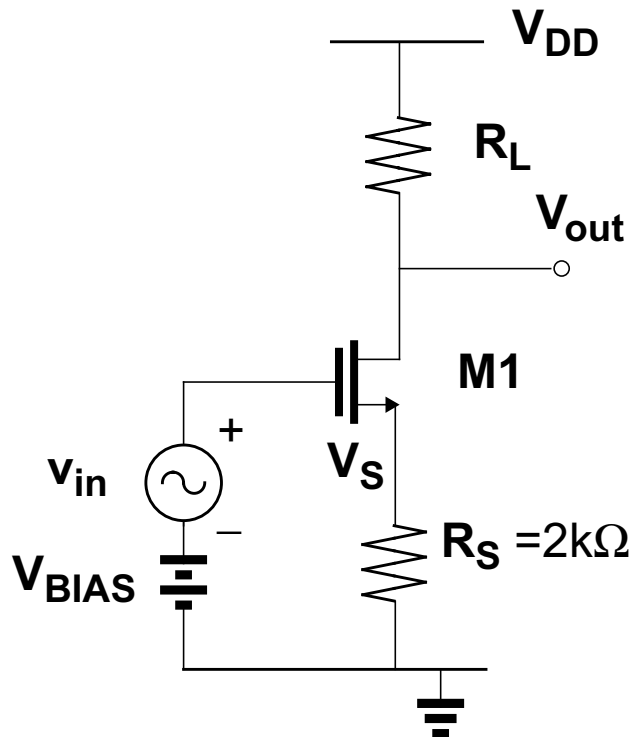
(i) With R_L connected:

$$Gain_{R_L} \equiv \frac{G_m}{G_{out} + G_L} = \frac{g_{m1} + g_{m2}}{g_{ds1} + g_{ds2} + \frac{1}{R_L}}$$

(ii) With nmos diode connected:

$$Gain_{nd} \equiv \frac{G_m}{G_{out} + G_L} = \frac{g_{m1} + g_{m2}}{g_{ds1} + g_{ds2} + g_{m3}}$$

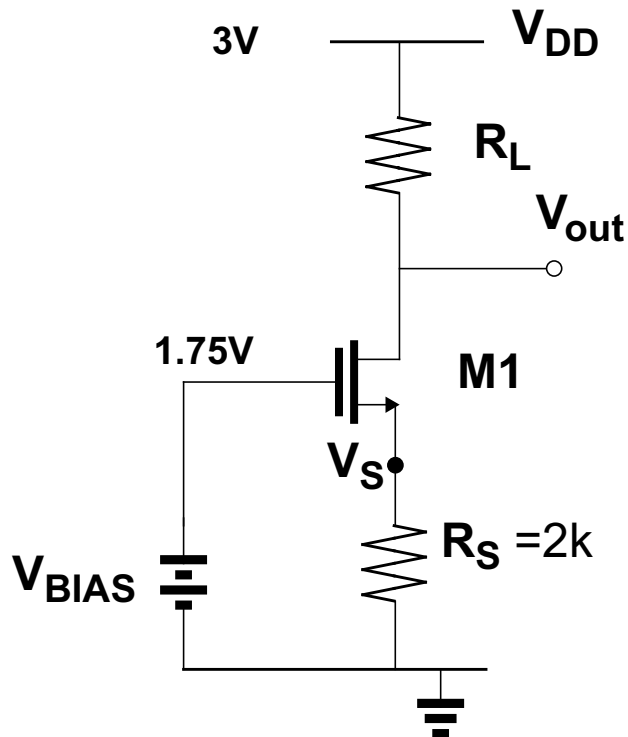
Problem: CS stage with resistive degeneration



Assume M1 is in saturation, ignore the body effect, take $g_m \gg g_{ds}$
Assume the stage is biased such that $g_m R_S = 2$
 $V_{\text{DD}} = 3\text{V}$, $V_{\text{BIAS}} = 1.75\text{V}$, $V_t = 1\text{V}$.

- (i) Calculate the value of the stage transconductance G_m
- (ii) What is the largest value of R_L such that M1 is in saturation
(Take $\lambda = 0$ for this calculation)
- (iii) What is the value of the small-signal gain for this R_L ?

Solution Problem P120 Resistive degeneration



(i)
$$G_m = \frac{g_m}{1 + g_m R_s}$$

$$g_m = \frac{2I_D}{V_{GS} - V_t}$$

Need to find values for I_D , $V_{GS} - V_t$

$$g_m R_s = \frac{2I_D R_s}{V_{GS} - V_t} = 2 \Rightarrow V_{GS} - V_t = I_D R_s$$

i.e. overdrive voltage of M1 = voltage across R_s

$$V_{BIAS} = V_t + (V_{GS} - V_t) + I_D R_s$$

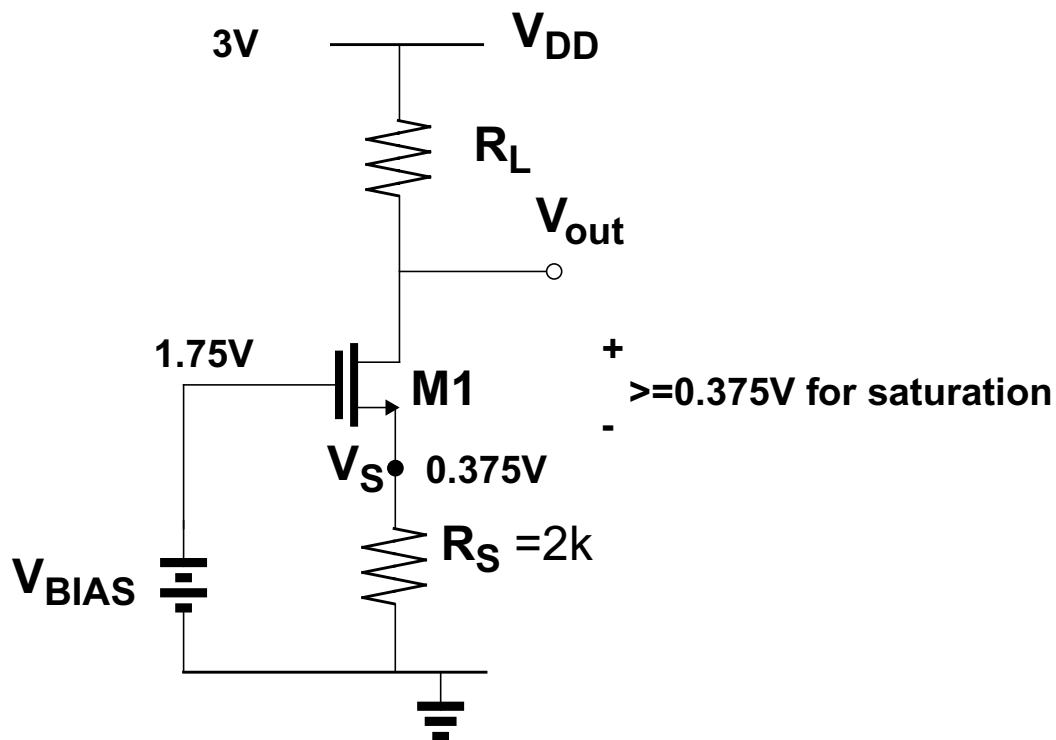
$$V_{BIAS} - V_t = 2(V_{GS} - V_t)$$

$$V_{GS} - V_t = \frac{1.75 - 1}{2} = 0.375V$$

$$I_D R_s = 0.375V \Rightarrow I_D = \frac{0.375V}{2k\Omega} = 187.5\mu A$$

$$g_m = \frac{2I_D}{V_{GS} - V_t} = \frac{2 \times 187.5 \mu A}{0.375 V} = 1 mA/V$$

$$G_m = \frac{g_m}{1 + g_m R_s} = \frac{1 mA/V}{1 + 2} = 333 \mu A/V$$



(ii) For M1 to be in saturation

$$V_{DS} \geq V_{GS} - V_t \Rightarrow V_{DS} \geq 0.375V \Rightarrow V_{out} \geq 0.75V$$

$$V_{DD} - I_D R_L \geq 0.75V$$

$$R_L \leq \frac{3 - 0.75V}{187.5\mu A}$$

$$R_L \leq 12k\Omega \quad \Rightarrow \quad R_{Lmax} = 12k\Omega$$

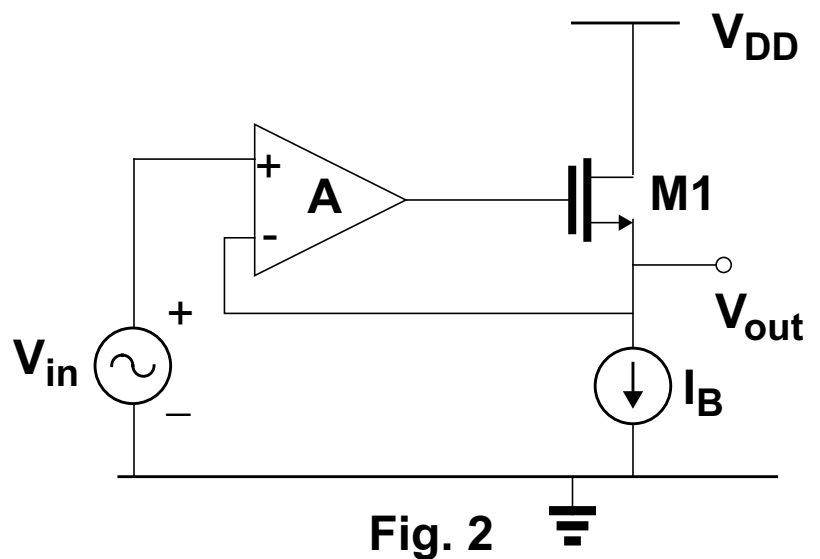
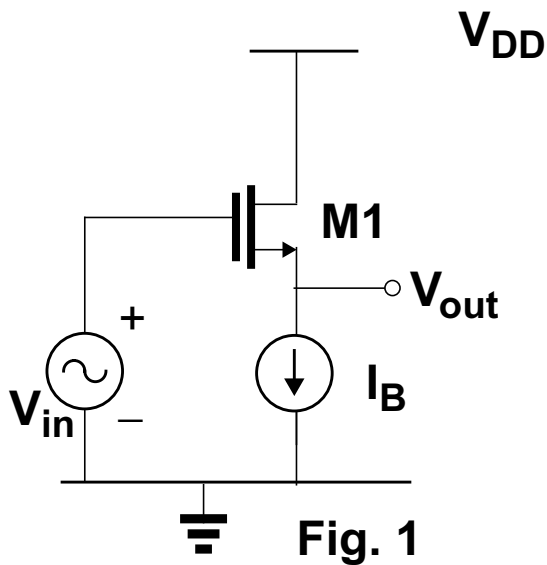
(iii)

$$\begin{aligned} Gain_{max} &= -G_m R_L = -\frac{g_m R_L}{1 + g_m R_S} \\ &= -\frac{1mA/V \times 12k\Omega}{1 + 2} = -4 \end{aligned}$$

In dB

$$Gain = 12dB$$

Problem - Source follower

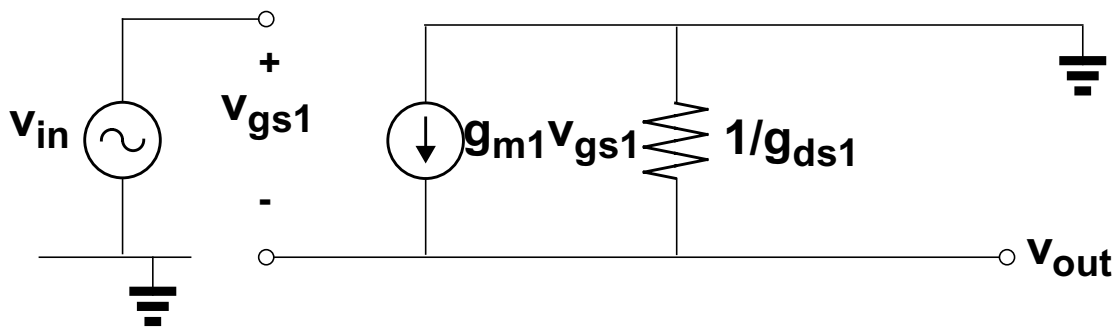


Assume M1 is in saturation, ignore the body effect

- (i) Draw the small signal model.
 - (ii) What is the small-signal low-frequency gain of the circuit in terms of g_m and g_{ds} ?
 - (iii) If $I_B = 200\mu A$, $V_{GS} = 1.5V$, $V_t = 1V$, calculate the small-signal low-frequency gain. Take $\lambda = 0.02V^{-1}$
 - (iv) What is the conductance/resistance at the output node?
 - (v) In Fig.2 an ideal amplifier has been added to reduce the output resistance. Draw the small signal model.
 - (vi) What is the impedance at the output node in terms of A, g_m and g_{ds} ?
- (To simplify the analysis assume $g_m \gg g_{ds}$)

Solution Problem P. 128: Source Follower

(i) Draw the small-signal model for the circuit shown in Fig.1.



(ii) What is the small-signal low-frequency gain of the circuit in terms of g_m and g_{ds} ?

Sum current at output node

$$g_{m1}v_{gs1} - v_{out}g_{ds1} = 0$$

$$g_{m1}(v_{in} - v_{out}) = v_{out}g_{ds1}$$

$$\frac{v_{out}}{v_{in}} = \frac{g_{m1}}{g_{m1} + g_{ds1}} \approx 1$$

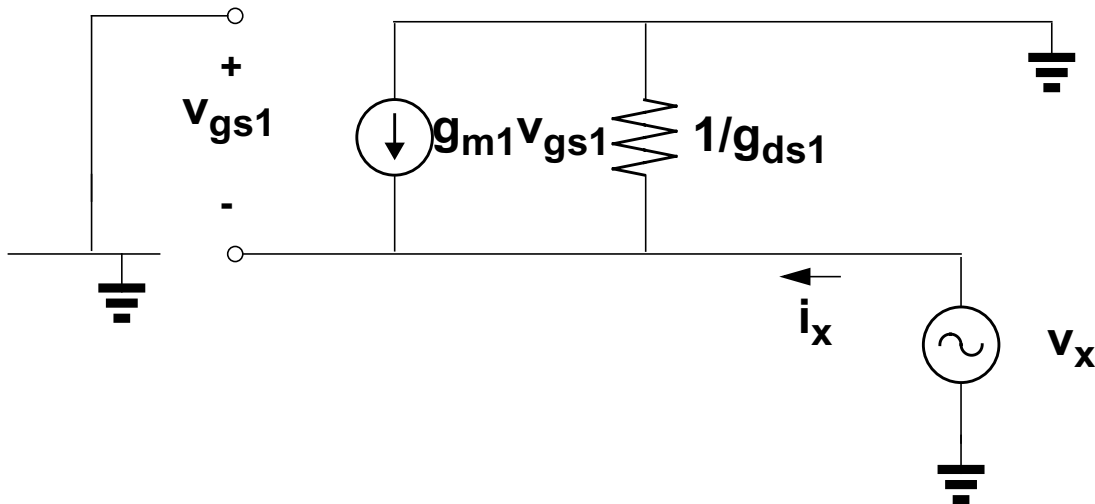
(iii) If $I_B = 200\mu A$, $V_{GS} = 1.5V$, $V_t = 1V$, calculate the small-signal low-frequency gain. Take $\lambda = 0.02V^{-1}$.

$$g_{m1} = \frac{2I_B}{V_{GS} - V_t} = \frac{2 \times 200\mu A}{0.5V} = 800\mu A/V$$

$$g_{ds1} = \lambda I_B = 0.02V^{-1} \times 200\mu A = 4\mu A/V$$

$$Gain = \frac{v_{out}}{v_{in}} = \frac{g_{m1}}{g_{m1} + g_{ds1}} = \frac{800}{800 + 4} \approx 1$$

(iv) What is the conductance/resistance at the output node?
To measure the small-signal output resistance:
Short the input.
Apply a test voltage at the output.
Measure the current through the test voltage.
Calculate ratio of voltage to current



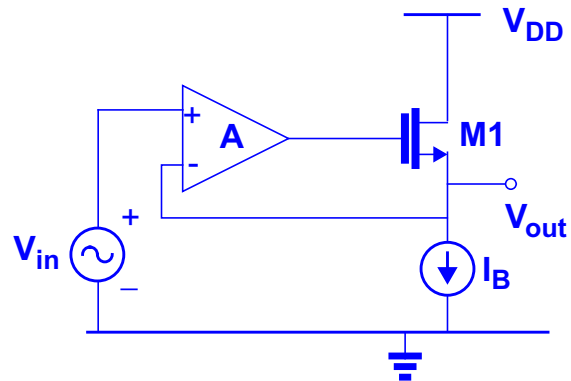
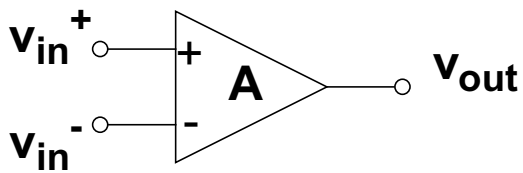
$$i_x = v_x g_{ds1} - g_{m1} v_{gs1}$$

$$= v_x g_{ds1} + g_{m1} v_x$$

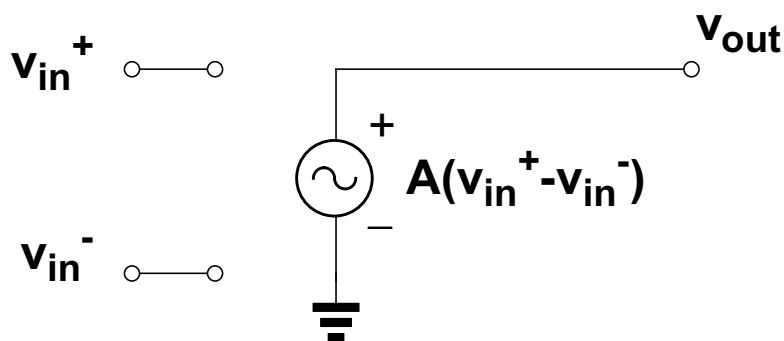
$$r_{out} = \frac{v_x}{i_x} = \frac{1}{g_{m1} + g_{ds1}} \approx \frac{1}{g_{m1}}$$

(v) In Fig.2 an ideal amplifier has been added to reduce the output resistance. Draw the small-signal model.

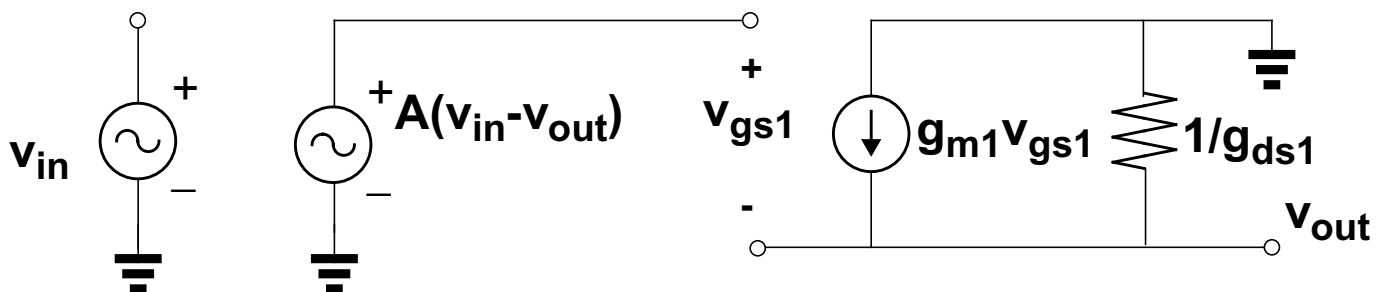
Differential-to-single-ended opamp



Small-signal model of opamp:



Small-signal model of Fig. 2:



Gain:

$$g_{m1}v_{gs1} - v_{out}g_{ds1} = 0$$

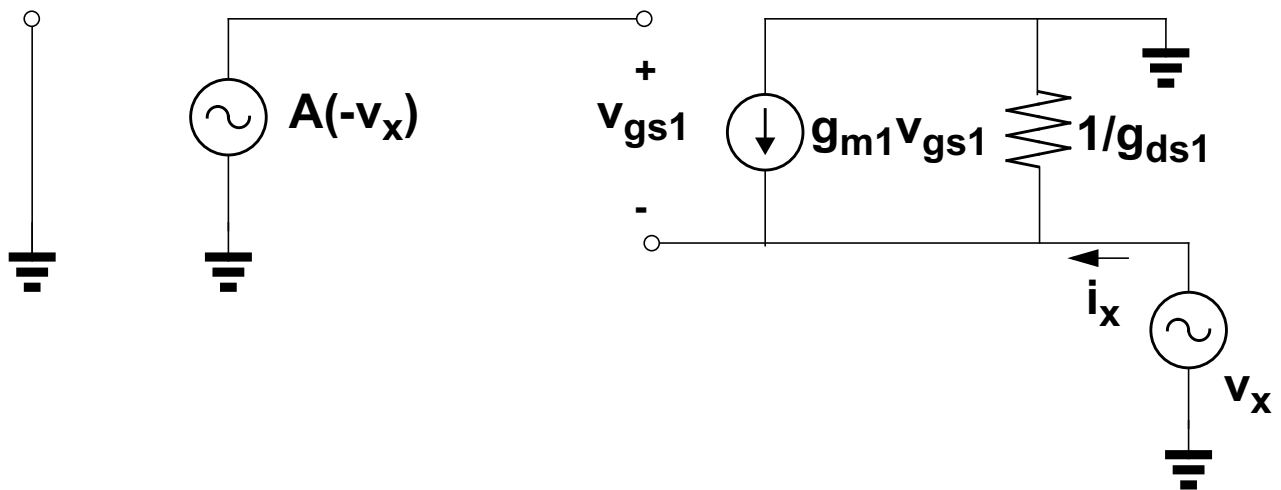
$$g_{m1}(A(v_{in} - v_{out}) - v_{out}) - v_{out}g_{ds1} = 0$$

$$g_{m1}Av_{in} = g_{m1}Av_{out} + g_{m1}v_{out} + v_{out}g_{ds1}$$

$$\frac{v_{out}}{v_{in}} = \frac{Ag_{m1}}{Ag_{m1} + g_{m1} + g_{ds1}} \approx 1$$

(vi) What is the impedance at the output node in terms of A , g_m and g_{ds} ?
 (To simplify the analysis assume $g_m \gg g_{ds}$)

Short input, apply test voltage at output and measure current into circuit

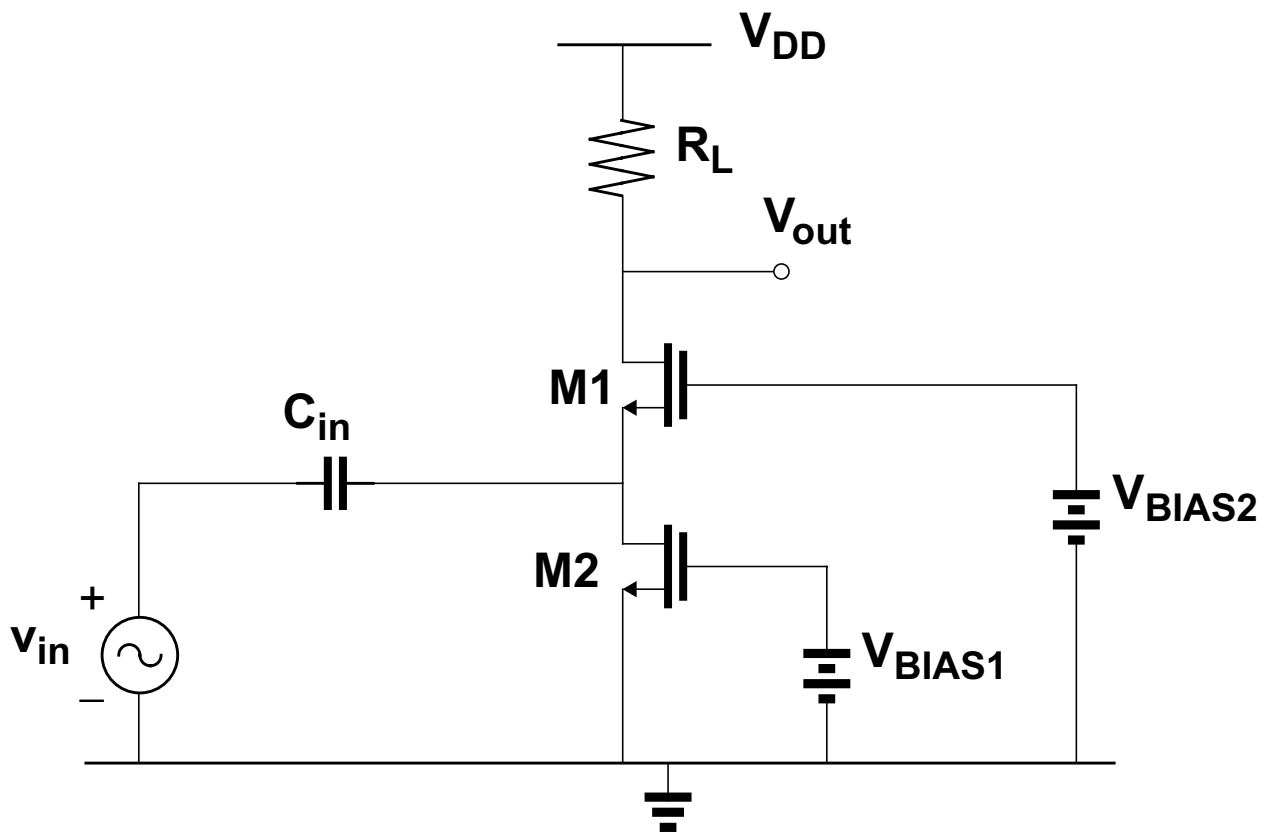


$$i_x = v_x g_{ds1} - g_{m1} v_{gs1}$$

$$= v_x g_{ds1} - g_{m1} (-A v_x - v_x)$$

$$r_{out} = \frac{v_x}{i_x} = \frac{1}{A g_{m1} + g_{m1} + g_{ds1}} \approx \frac{1}{(A + 1) g_{m1}}$$

Problem: Common-gate stage



$V_{DD}=3.3V$, $V_t=0.6V$, $I_{D1}=1mA$

It is required for an input stage to a system to have an input resistance of $200\Omega \pm 10\%$ and a gain of about 20dB.

Assume the input signal couples through C_{in} without loss.

- (i) Suggest values for g_{m1} and R_L to meet this specification.
- (ii) Assuming M1 and M2 have the same W/L and M2 is just in saturation, what is the range of allowed voltages for V_{BIAS2} ?

Solution Common-gate stage problem

(i)

Assume body effect can be ignored.

From analysis in notes:

$$R_{in} = \frac{v_x}{i_x} \approx \frac{1}{g_m} + \frac{R_L}{\frac{g_m}{g_{ds}}}$$

Assume $1/g_m$ term dominates

$$R_{in} = \frac{v_x}{i_x} \approx \frac{1}{g_m} \Rightarrow g_m = \frac{1}{R_{in}} = \frac{1}{200\Omega}$$

$$Gain \approx g_m R_L = 10 \Rightarrow R_L = \frac{10}{g_m} = 2k\Omega$$

Note that this implies that $g_m/g_{ds} > 100$ in order to meet the spec of $R_{in}=200\Omega \pm 10\%$.

May want to increase g_m , reduce R_L to meet spec more comfortably, target $R_{in} = 200\Omega$.

=> design iteration

Solution

(ii)

What $V_{GS}-V_t$ is required for each transistor?

For M1:

$$g_m = \frac{2I_D}{V_{GS} - V_t} \Rightarrow V_{GS} - V_t = \frac{2I_D}{g_m} = 2 \times 1mA \times 200\Omega = 400mV$$

M1 and M2 have same $V_{GS}-V_t$

For M2 to be in saturation

$$V_{BIAS2} \geq V_{GS1} + (V_{GS2} - V_t)$$

$$V_{BIAS2} \geq V_t + (V_{GS1} - V_t) + (V_{GS2} - V_t)$$

$$V_{BIAS2} \geq 0.6V + 0.4V + 0.4V = 1.4V$$

For M1 to be in saturation

$$V_{out} \geq V_{BIAS2} - V_t \Rightarrow V_{BIAS2} \leq V_{out} + V_t$$

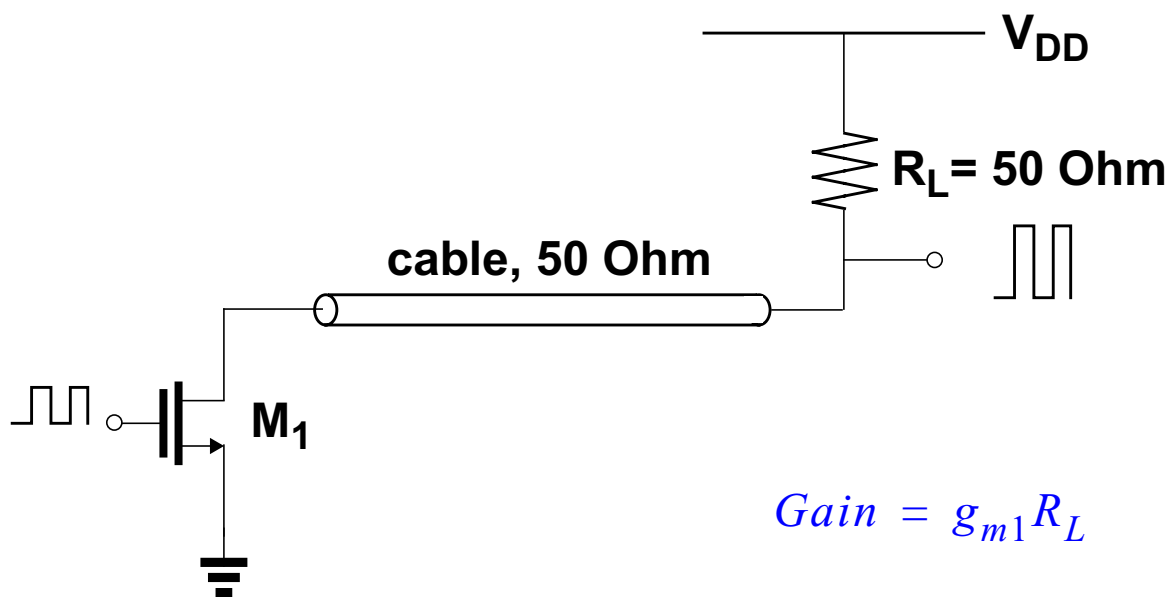
$$V_{out} = V_{DD} - I_D R_L = 3.3 - 1mA \times 2k\Omega = 1.3V$$

$$V_{BIAS2} \leq 1.3V + 0.6V = 1.9V$$

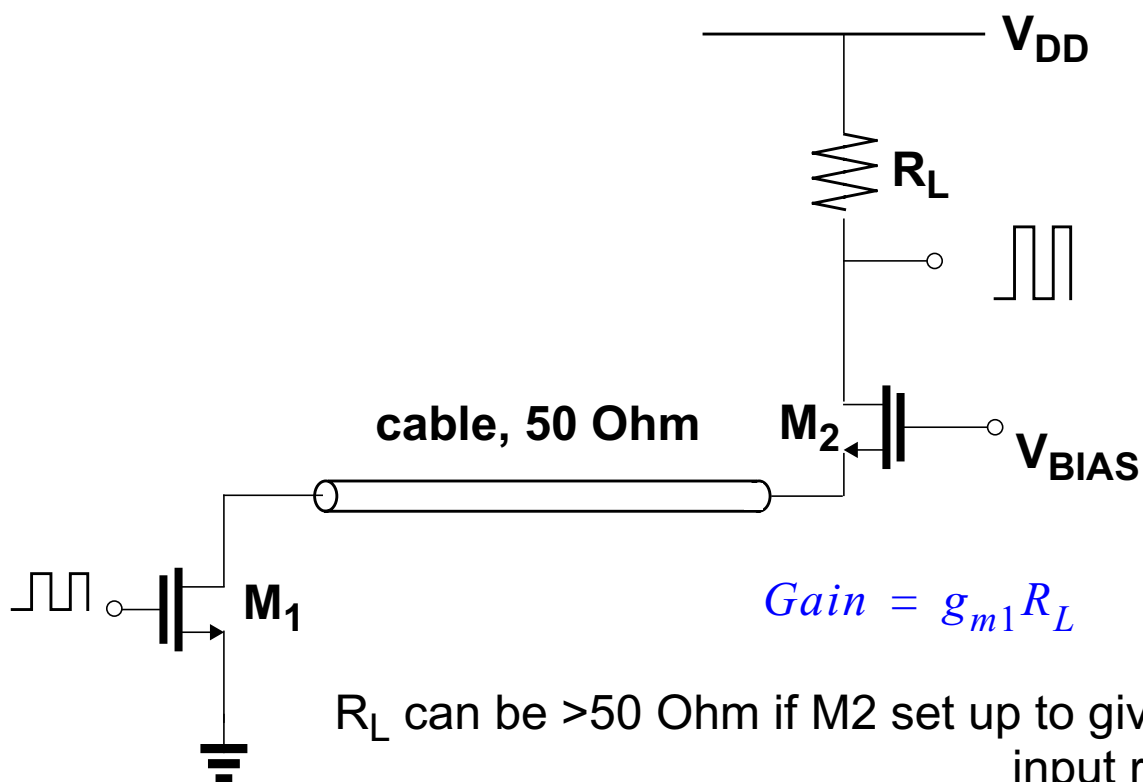
$$1.4V \leq V_{BIAS2} \leq 1.9V$$

So the optimum voltage for V_{BIAS2} is around 1.65V.
A small signal of up to 250mV could then be handled

Example from Razavi



R_L must be $\sim 50 \text{ Ohm}$ to prevent reflections



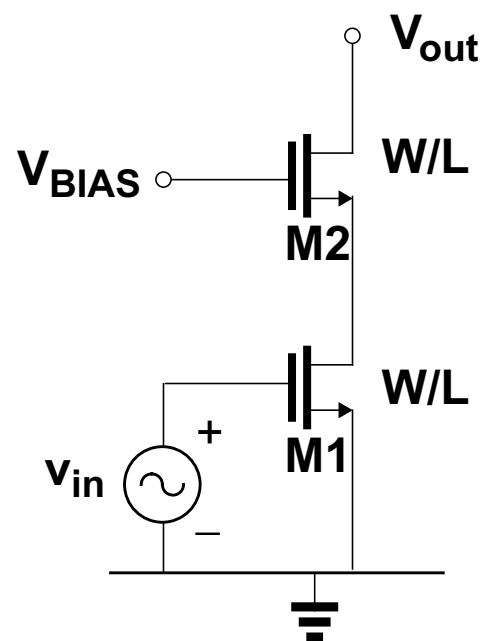
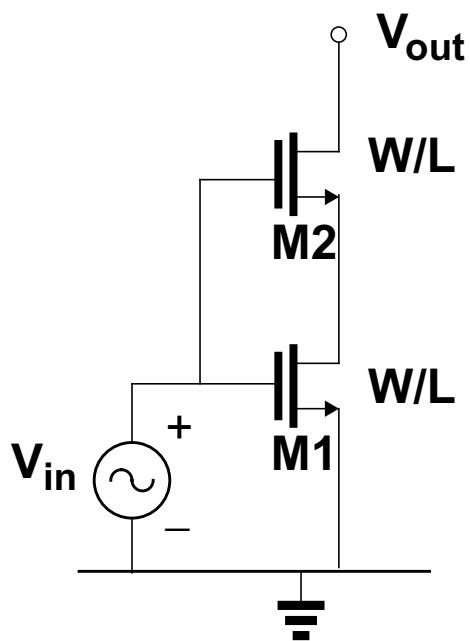
R_L can be $> 50 \text{ Ohm}$ if M_2 set up to give 50 Ohm input resistance

Problem - Cascode stage output resistance, voltage headroom:

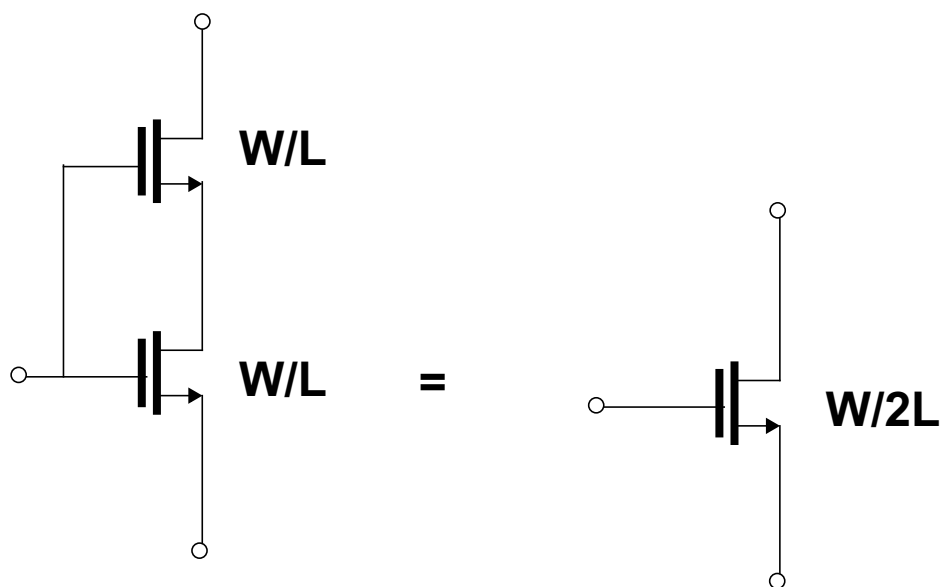
Compare the two stages shown in terms of

- (i) output resistance
- (ii) gain
- (iii) voltage headroom required

Assume both stages have same bias current. Ignore body effect.

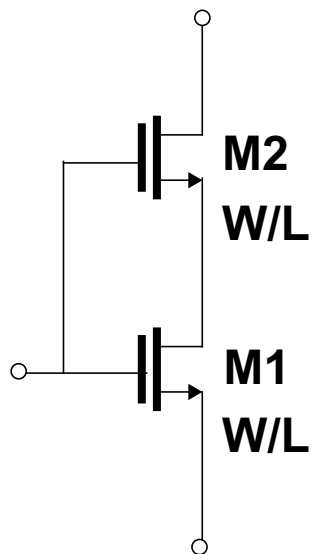


Note:

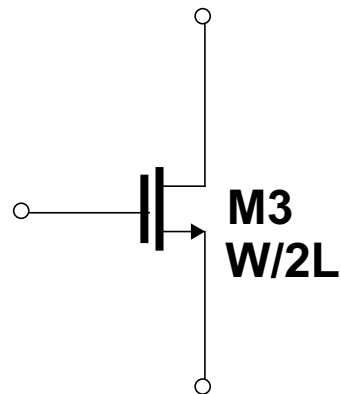


Problem P.141 : Cascode v. common source

Redraw



as



(i) Compare output resistances

Cascode:

$$r_{outcas} = \frac{g_{m2}}{g_{ds2}} \cdot \frac{1}{g_{ds1}}$$

Common source: $r_{outcs} = \frac{1}{g_{ds3}}$

Given that $g_{ds} = \lambda I_D$ and $\lambda \propto \frac{1}{L}$

then $g_{ds3} = \frac{g_{ds1}}{2}$

and $r_{outcs} = \frac{2}{g_{ds1}}$

=> Common source:

$$r_{outcs} = 2 \frac{1}{g_{ds1}}$$

Since $\frac{g_{m2}}{g_{ds2}} \gg 2$ the r_{out} of the cascode is much higher.

(ii) Compare gains

Cascode: $Gain_{cas} = -g_{m1} r_{outcas} = -g_{m1} \cdot \frac{g_{m2}}{g_{ds2}} \cdot \frac{1}{g_{ds1}} = \frac{g_{m1}}{g_{ds1}} \cdot \frac{g_{m2}}{g_{ds2}}$

Common source: $Gain_{cs} = -g_{m3} r_{out3}$

Given that $g_{m3} = \sqrt{2K'_n \frac{W}{2L} I_D}$

then $g_{m3} = \frac{g_{m1}}{\sqrt{2}}$

=> Common source: $Gain_{cs} = -\frac{g_{m1}}{\sqrt{2}} \frac{2}{g_{ds1}} = -\frac{2}{\sqrt{2}} \frac{g_{m1}}{g_{ds1}}$

Since $\frac{g_{m2}}{g_{ds2}} \gg \frac{2}{\sqrt{2}}$ the gain of cascode is much higher

(iii) Compare required voltage headroom

Cascode:

The minimum output voltage if the cascode is optimally biased is

$$V_{outcas} \geq 2V_{GT1}$$

$$\text{where } V_{GT} \equiv V_{GS} - V_t$$

Common source:

$$V_{outcs} \geq V_{GT3}$$

$$\text{Since } I_D = \frac{K_n'}{2} \frac{W}{L} (V_{GT3})^2$$

$$\text{then } V_{GT3} = \sqrt{\frac{2I_D}{K_n' \frac{W}{L}}} = \sqrt{2} \sqrt{\frac{2I_D}{K_n' \frac{W}{L}}}$$

$$V_{outcs} \geq V_{GT3} = \sqrt{2} V_{GT1}$$

=> common source stage requires less headroom

Note: It can be argued that a fairer comparison would be if we were to dimension M3 to have the same voltage headroom requirement as the cascode stage, i.e. by making $M3=W/4L$.

Then for the common source stage:

$$r_{outcs} = \frac{4}{g_{ds1}}$$

$$Gain_{cs} = -2 \frac{g_{m1}}{g_{ds1}}$$

i.e. still much lower gain than cascode

Of course the cascode needs extra biasing circuitry (and current, area) to set up the cascode voltage.

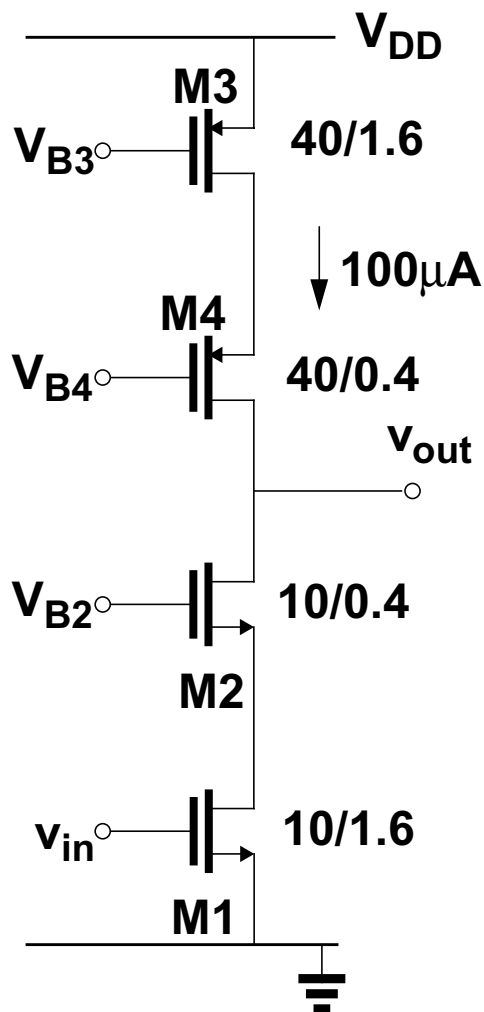
Also the cascode introduces extra nodes in the circuitry

=> extra poles

=> possible stability issues in negative feedback

So there are cases in which extra L will be a better option.

Problem P. 144 Cascode gain stage with cascode load



From P.134:
$$Gain = -\frac{g_{m1}}{\frac{g_{ds1}}{g_{m2}/g_{ds2}} + \frac{g_{ds3}}{g_{m4}/g_{ds4}}}$$

Given: $K_n', K_p', \lambda_n, \lambda_p, I$

Use:
$$g_{mn} = \sqrt{2K_n' \frac{W}{L} I} \quad g_{dsn} = \lambda_n I$$

$$g_{mp} = \sqrt{2K_p' \frac{W}{L} I} \quad g_{dsp} = \lambda_p I$$

$$g_{m1} = \sqrt{2 \cdot 200\mu A/V^2 \cdot \frac{10}{1.6} \cdot 100\mu A} = 500\mu A/V$$

$$g_{m2} = \sqrt{2 \cdot 200\mu A/V^2 \cdot \frac{10}{0.4} \cdot 100\mu A} = 1mA/V$$

$$g_{m3} = \sqrt{2 \cdot 50\mu A/V^2 \cdot \frac{40}{1.6} \cdot 100\mu A} = 500\mu A/V$$

$$g_{m4} = \sqrt{2 \cdot 50\mu A/V^2 \cdot \frac{40}{0.4} \cdot 100\mu A} = 1mA/V$$

$$g_{ds1} = \frac{0.04V^{-1}}{1.6} \cdot 100\mu A = 2.5\mu A/V$$

$$g_{ds2} = \frac{0.04V^{-1}}{0.4} \cdot 100\mu A = 10\mu A/V$$

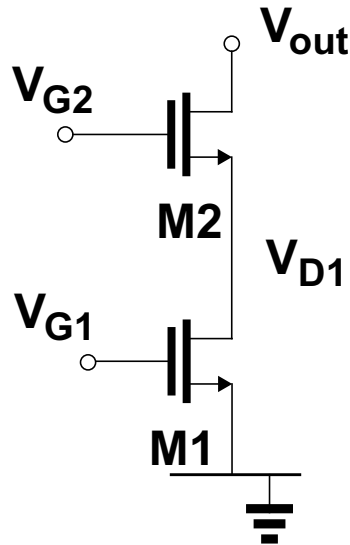
$$g_{ds3} = \frac{0.04V^{-1}}{1.6} \cdot 100\mu A = 2.5\mu A/V$$

$$g_{ds4} = \frac{0.04V^{-1}}{0.4} \cdot 100\mu A = 10\mu A/V$$

$$\begin{aligned} Gain &= -\frac{g_{m1}}{\frac{g_{ds1}}{g_{m2}/g_{ds2}} + \frac{g_{ds3}}{g_{m4}/g_{ds4}}} = -\frac{500}{\frac{2.5}{1000/10} + \frac{2.5}{1000/10}} \\ &= -10000 \end{aligned}$$

$$\text{In dB: } Gain = 80dB$$

Cascode output resistance - DC point of view



The cascode provides extra gain by increasing the output resistance of the common source stage i.e. the change in output current for a given change in output voltage is reduced.

Looked at from the DC point of view: if the DC voltage at the output increases, then the output current will increase due to the finite output conductance of the transistors.

This current will be provided by M1.

As M1 obeys the equation

$$I_D = \frac{K_n'}{2} \frac{W}{L} (V_{GS} - V_t)^2 (1 + \lambda V_{DS})$$

and its V_{GS} is fixed, then V_{D1} will increase.

The increase in V_{D1} reduces V_{GS} of M2, so that M2 will obey the current equation with a relatively large increase in its V_{DS} .

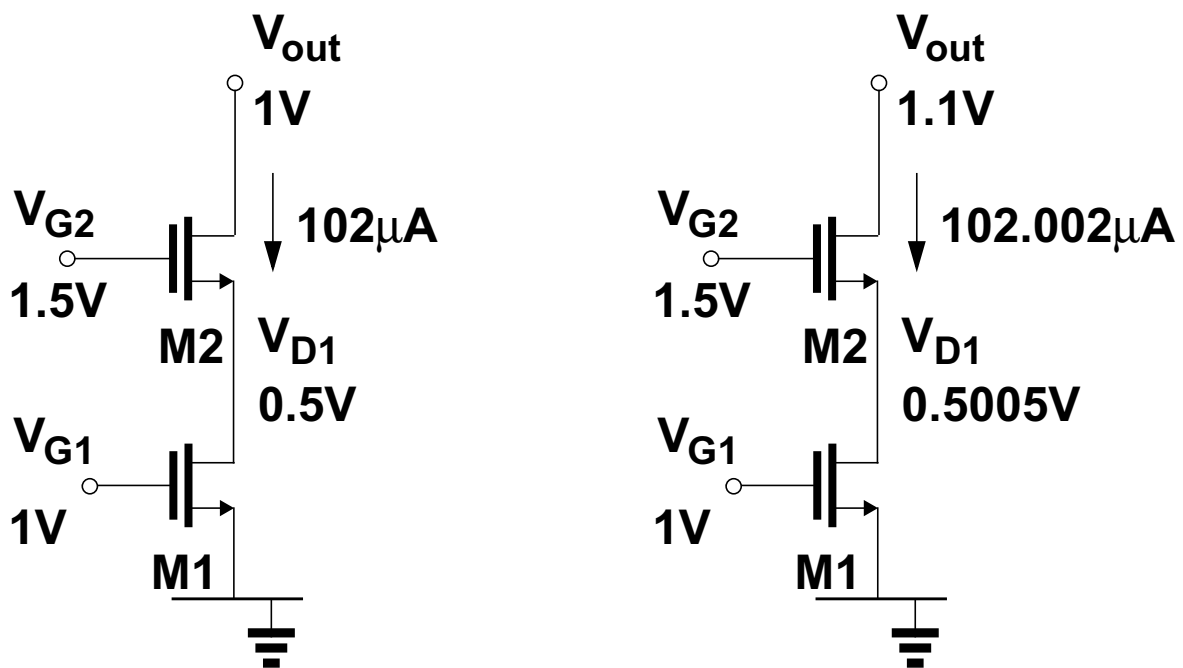
The overall result is that the increase in V_{out} falls largely over M2, and only a small proportion of the increase falls over M1.

So the current out of M1 increases much less than would be the case without the cascode (basically a factor defined by the ratio of the transconductance of M2 to its output conductance).

Simulation results are given below for 2 output voltages of 1V and 1.1V using the model

$$I_D = \frac{K_n'}{2} \frac{W}{L} (V_{GS} - V_t)^2 (1 + \lambda V_{DS})$$

with $K_n' = 200 \mu\text{A}/\text{V}^2$, $W/L = 16/1$, $V_t = 0.75\text{V}$, $\lambda = 0.04$.



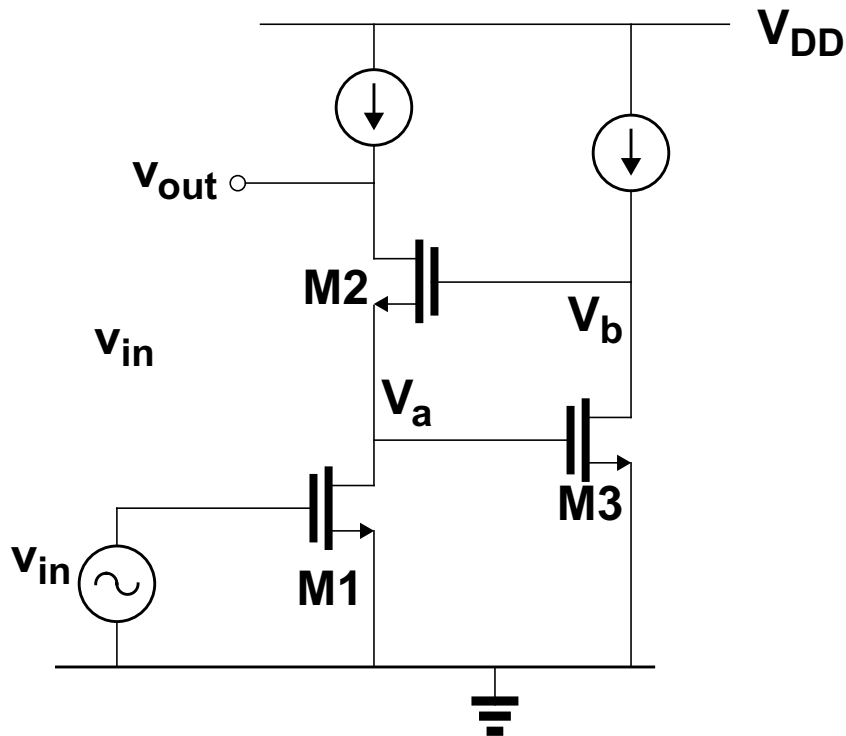
It can be seen that the voltage at the drain of M1 increases by 0.5mV, and the output current by just 2nA. Without the cascode this would have been 0.4μA.

Problem P150: regulated cascode:

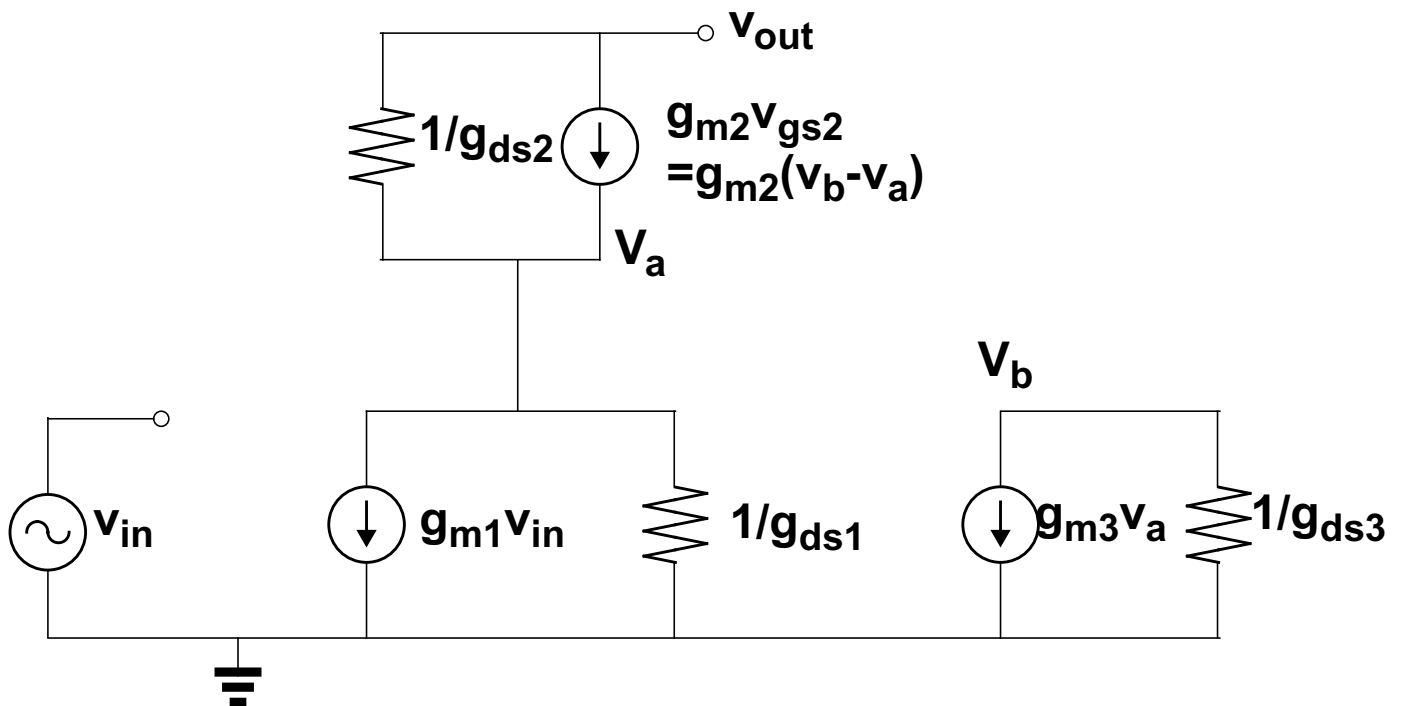
What is voltage gain of stage shown below?

Assume all transistors are biased in saturation.

Ignore body effect.?



Small-signal model



Small-signal voltage gain

KCL at output node (drain of M2):

$$(v_{out} - v_a)g_{ds2} + g_{m2}(v_b - v_a) = 0 \quad [1]$$

i.e. because there is no current flowing into v_{out} (biased by ideal DC current source), then the two currents must be equal

KCL at node v_a (source of M2):

$$(v_{out} - v_a)g_{ds2} + g_{m2}(v_b - v_a) = g_{m1}v_{in} + v_ag_{ds1}$$

$$0 = g_{m1}v_{in} + v_ag_{ds1}$$

$$v_a = -\frac{g_{m1}}{g_{ds1}}v_{in}$$

KCL at node v_b (gate of M2):

$$g_{m3}v_a = -v_bg_{ds3}$$

$$v_b = -\frac{g_{m3}}{g_{ds3}}v_a$$

$$v_b = \frac{g_{m3}g_{m1}}{g_{ds3}g_{ds1}}v_{in}$$

Substitute for v_b, v_a in [1]

$$v_{out}g_{ds2} + \frac{g_{m1}}{g_{ds1}}g_{ds2}v_{in} + g_{m2}\left(\frac{g_{m3}g_{m1}}{g_{ds3}g_{ds1}}\right)v_{in} + g_{m2}\left(\frac{g_{m1}}{g_{ds1}}\right)v_{in} = 0$$

$$\frac{v_{out}}{v_{in}} = -\frac{1}{g_{ds2}}\left(g_{m2}\left(\frac{g_{m3}g_{m1}}{g_{ds3}g_{ds1}}\right) + g_{m2}\left(\frac{g_{m1}}{g_{ds1}}\right) + g_{ds2}\frac{g_{m1}}{g_{ds1}}\right)$$

$$\frac{v_{out}}{v_{in}} = -\left(\frac{g_{m3}g_{m2}g_{m1}}{g_{ds3}g_{ds2}g_{ds1}} + \frac{g_{m2}g_{m1}}{g_{ds2}g_{ds1}} + \frac{g_{m1}}{g_{ds1}}\right) \approx -\frac{g_{m2}g_{m3}g_{m1}}{g_{ds2}g_{ds3}g_{ds1}}$$

This technique is known as 'gain-boosting'

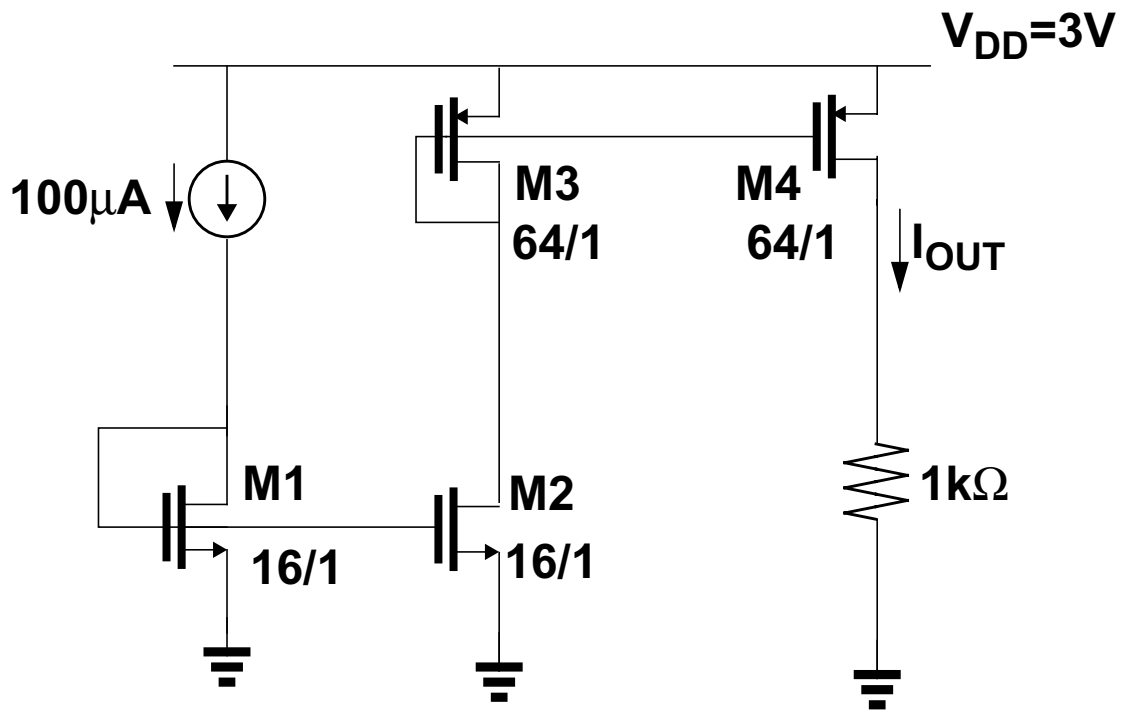
Problem P174: Current source inaccuracy due to V_t mismatch

Estimate the nominal value and the 3σ spread of the current I_{OUT} in the circuit below.

$$A_{V_t} = 10 \text{ mV}/\mu\text{m}$$

$$K_n' = 200 \mu\text{A}/\text{V}^2, K_p' = 50 \mu\text{A}/\text{V}^2, V_t = 0.75 \text{ V}$$

Assume all errors have a normal distribution and are uncorrelated.



Problem P.174 Current mirror spread

Taking $\lambda = 0$ initially

For nmos mirror

$$\sigma_{V_{tn}} = \frac{A_{V_{tn}}}{\sqrt{WL}} = \frac{10mV\mu m}{\sqrt{16\mu m \cdot 1\mu m}} = 2.5mV$$

$$V_{GS1} - V_{tn} = \sqrt{\frac{2I_D}{K'_n \frac{W}{L}}} = \sqrt{\frac{2 \cdot 100\mu A}{200\mu A/V^2 \frac{16}{1}}} = 0.25V$$

$$g_{mn} = \frac{2I_D}{V_{GS} - V_{tn}} = \frac{2 \times 100\mu A}{0.25V} = 800\mu A/V$$

$$\sigma_{I_{Dn}} = g_{mn} \sigma_{V_{tn}} = 800\mu A/V \times 2.5mV = 2\mu A$$

For pmos mirror

$$\sigma_{V_{tp}} = \frac{A_{V_{tp}}}{\sqrt{WL}} = \frac{10mV\mu m}{\sqrt{64\mu m \cdot 1\mu m}} = 1.25mV$$

$$|V_{GS3} - V_{tp}| = \sqrt{\frac{2I_D}{K'_n \frac{W}{L}}} = \sqrt{\frac{2 \cdot 100\mu A}{50\mu A/V^2 \frac{64}{1}}} = 0.25V$$

$$g_{mp} = \frac{2I_D}{V_{GS} - V_{tp}} = \frac{2 \times 100\mu A}{0.25V} = 800\mu A/V$$

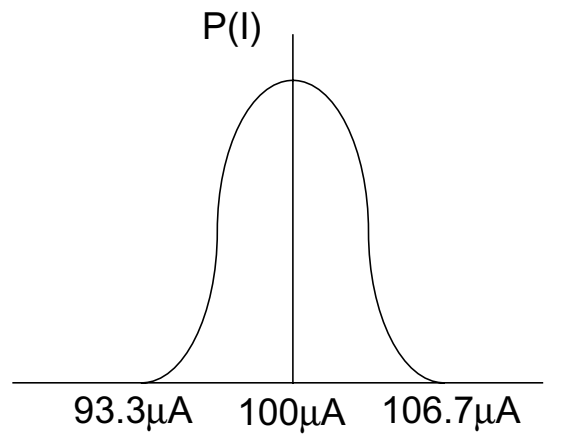
$$\sigma_{I_{Dp}} = g_{mp} \sigma_{V_{tp}} = 800\mu A/V \times 1.25mV = 1\mu A$$

$$\sigma_{I_{OUT}} = \sqrt{\sigma_{I_{Dn}}^2 + \sigma_{I_{Dp}}^2}$$

$$\sigma_{I_{OUT}} = \sqrt{2^2 + 1^2} = 2.236\mu A$$

This is the total 1σ sigma mismatch between I_{IN} and I_{OUT}

If we specify for 3σ sigma mismatch then we specify $100\mu A \pm 6.7\mu A$



The above analysis ignored the static error.

To calculate the mean output current, the finite output conductance must be taken into account

Taking $\lambda = 0.04V^{-1}$

$$V_{GS1} = V_{DS1} = 1.0V$$

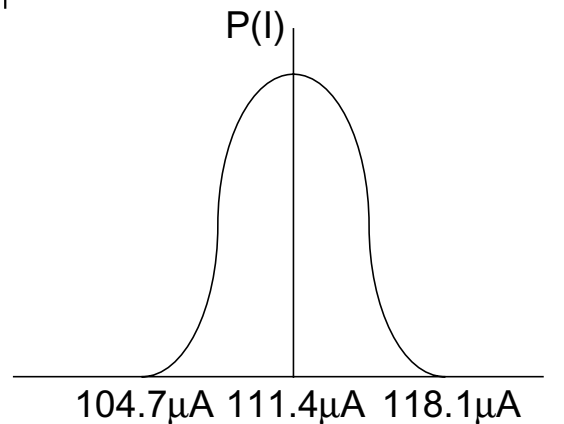
$$|V_{GS3}| = |V_{DS3}| = 1.0V$$

$$V_{DS2} = V_{DD} - |V_{GS3}| = 2V$$

$$\frac{I_{D2}}{I_{D1}} = \frac{1 + \lambda V_{DS2}}{1 + \lambda V_{DS1}} = \frac{1 + 0.04 \times 2}{1 + 0.04 \times 1} \Rightarrow I_{D2} = 103.8\mu A$$

$$V_{DS4} = V_{DD} - I_{OUT} \times 1k\Omega \approx 2.9V$$

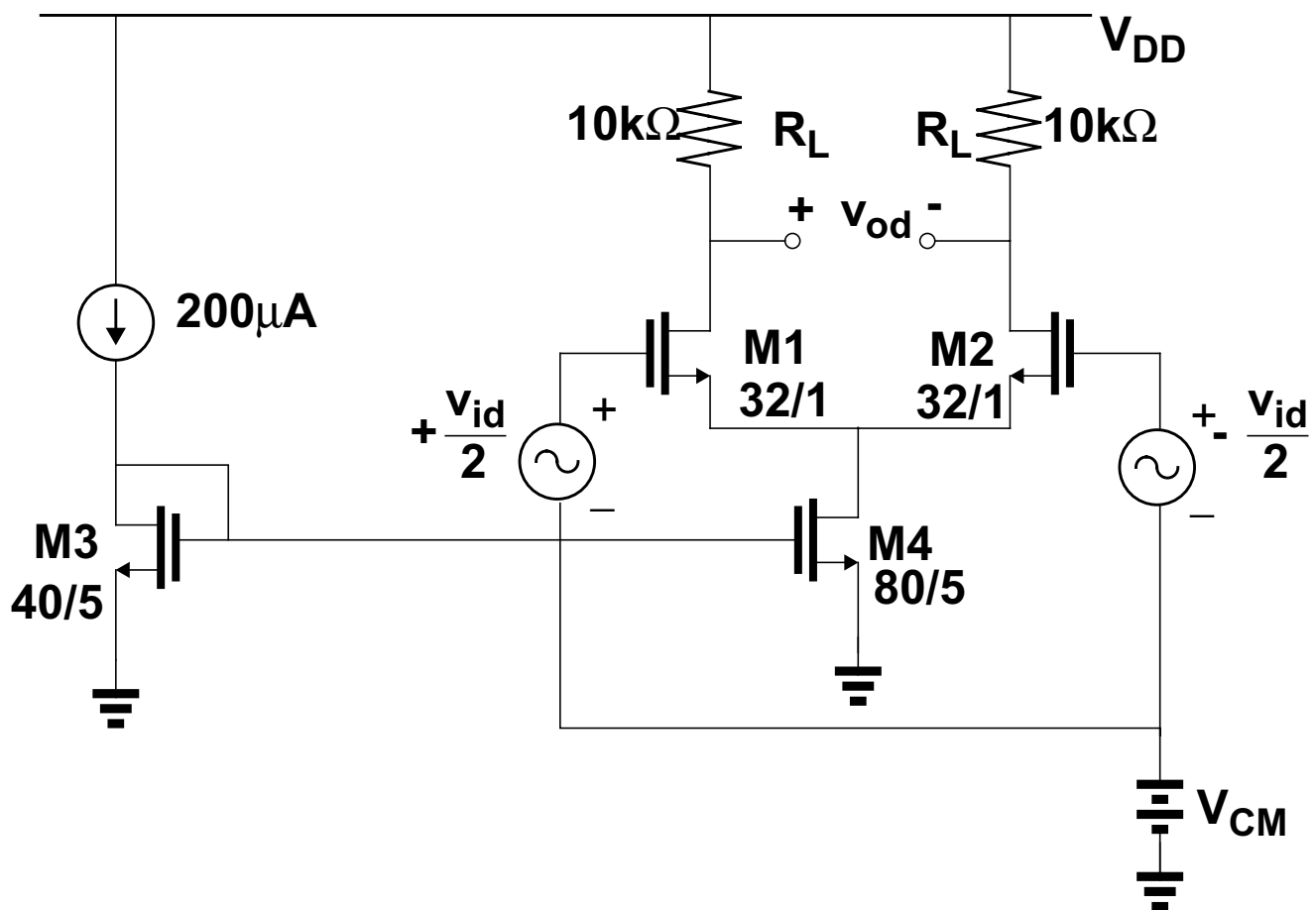
$$\frac{I_{D4}}{I_{D3}} = \frac{1 + \lambda |V_{DS4}|}{1 + \lambda |V_{DS3}|} = \frac{1 + 0.04 \times 2.9}{1 + 0.04 \times 1} \Rightarrow I_{D4} = 1.07 I_{D3} = 111.4\mu A$$



Note: there are still a number of approximations in this answer.

For fully accurate yield prediction, use Monte Carlo simulations

Problem P193 - Diff. amp. common-mode input range, CMRR



- What is the allowed range of the common-mode input voltage (i.e. the range in the quiescent state such that all transistors remain in saturation)?
- What is the value of the differential gain?
- What is the value of the common-mode gain?
- What is the CMRR?

$$V_{DD} = 3.3V$$

$$V_t = 1V, \lambda_n = 0.04/L \text{ V}^{-1}$$

$$K_n' = 200\mu A/V$$

Problem P. 193 (Common-Mode Input Range)

(i) Common-mode input voltage range

1. Lower limit on V_{CM} :

The common-mode voltage is bound on the lower side by the voltage at the common-source node falling with the common-mode voltage and pushing M4 out of saturation.

$$\text{M4: } V_{GS4} - V_t = \sqrt{\frac{2 \cdot 400\mu A}{200\mu A/V \cdot \frac{80}{5}}} = 500mV$$

=> Voltage at drain of M4 (V_{DS4}) must be greater than 0.5V.

$$\text{M1: } V_{GS1} - V_t = \sqrt{\frac{2 \cdot 200\mu A}{200\mu A/V \cdot \frac{32}{1}}} = 250mV$$

$$V_{GS1} = 250mV + V_t = 1.25V$$

So minimum common-mode voltage given by

$$V_{CMmin} = V_{DS4min} + V_{GS1}$$

$$V_{CMmin} = 0.5V + 1.25V = 1.75V$$

2. Upper limit on V_{CM} :

The common-mode voltage is bound on the upper side by the voltage at the common-source node rising with the common-mode voltage and pushing M1,M2 out of saturation.

$$V_{D1} = V_{DD} - I_D R_L = 3.3V - 200\mu A \times 10k\Omega = 1.3V$$

$$V_{DS1} \geq V_{GS1} - V_t$$

$$V_{S1} \leq V_{D1} - (V_{GS1} - V_t)$$

$$V_{S1} \leq 1.3V - 0.25V = 1.05V$$

So maximum common-mode voltage given by

$$V_{CM} \leq V_{S1min} + V_{GS1}$$

$$V_{CM} \leq 1.05V + 1.25V = 2.3V$$

$$V_{CMmax} = 2.3V$$

Common-mode input range given by

$$V_{CMmin} \leq V_{CM} \leq V_{CMmax}$$

$$1.75V \leq V_{CM} \leq 2.3V$$

(ii) Differential Gain

$$A_{dm} = -\frac{g_{m1}}{g_{ds1} + \frac{1}{R_L}}$$

$$g_{m1} = \sqrt{2K'_n \frac{W_1}{L_1} I_{D1}} = \sqrt{2 \times 200 \mu A/V \times \frac{32}{1} \times 200 \mu A} = 1.6 mA/V$$

$$g_{ds1} = \lambda I_{D1} = \frac{0.04}{1} \times 200 \mu A = 8 \mu A/V$$

$$\frac{1}{g_{ds1}} = 125 k\Omega \Rightarrow \frac{1}{g_{ds1}} \gg R_L$$

$$A_{dm} \approx -g_{m1} R_L = 1.6 mA/V \times 10 k\Omega = -16 \equiv 24 dB$$

(iii) Common-mode Gain

$$A_{cm} = -\frac{R_L}{2R_{cur}}$$

R_{cur} is output resistance of M4

$$g_{ds4} = \lambda I_{D4} = \frac{0.04}{5} \times 400 \mu A = 3.2 \mu A/V$$

$$\frac{1}{g_{ds4}} = 312.5 k\Omega \equiv R_{cur}$$

$$A_{cm} = -\frac{10 k\Omega}{2 \times 312.5 k\Omega} = -16 e^{-3} \equiv -36 dB$$

(iv) Common-mode rejection ratio

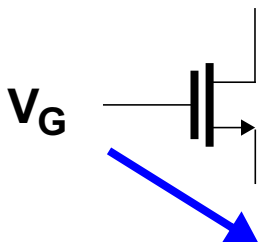
$$CMRR = \left| \frac{A_{dm}}{A_{cm}} \right| = \left| \frac{-16}{-16 e^{-3}} \right| = 1000 \equiv 60 dB$$

Note: Relationship between gate and drain voltage for saturation.

The voltage at the gate defines the voltage at the source (i.e. the source voltage is equal to the gate voltage less the V_{GS} drop).

The voltage at the source then defines the minimum voltage needed at the drain for saturation (i.e. the source voltage plus $V_{GS}-V_t$)

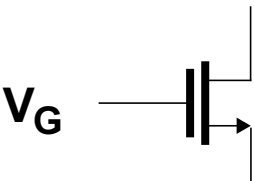
For saturation: $V_{DS} > V_{GS} - V_t$

$$\Rightarrow V_D > V_S + V_{GS} - V_t$$
$$\Rightarrow V_D > V_G - (V_{GS} - V_t) - V_t + (V_{GS} - V_t)$$
$$\Rightarrow V_D > V_G - V_t$$

$$V_S = V_G - V_{GS}$$
$$\Rightarrow V_S = V_G - (V_{GS} - V_t) - V_t$$

Summary (NMOS):

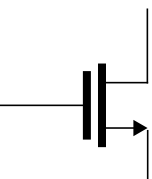
If you know the voltage at the gate, this defines the minimum voltage at the drain

For saturation:

$$V_D > V_G - V_t$$


Alternatively, if you know the voltage at the drain, this defines the maximum voltage at the gate:

For saturation:

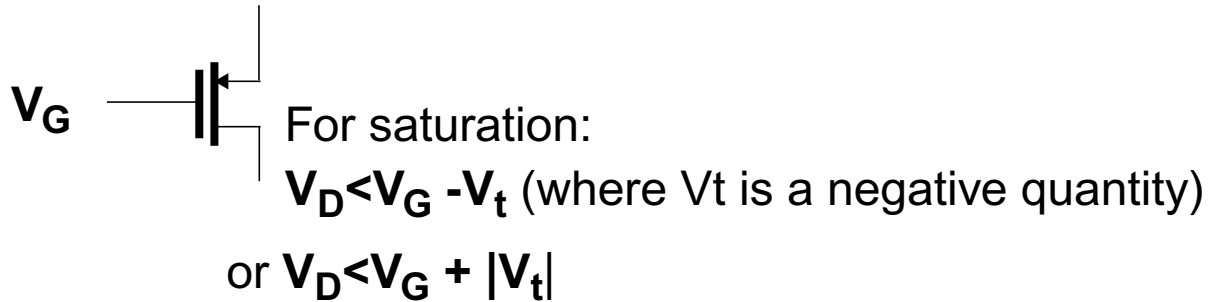
$$V_G < V_D + V_t$$


So in the previous example, once the drain voltage is calculated as 1.3V, then you know the max. gate voltage is 2.3V

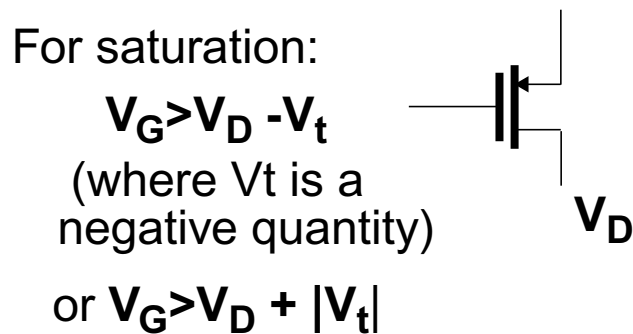
Same applies for PMOS

Summary (PMOS):

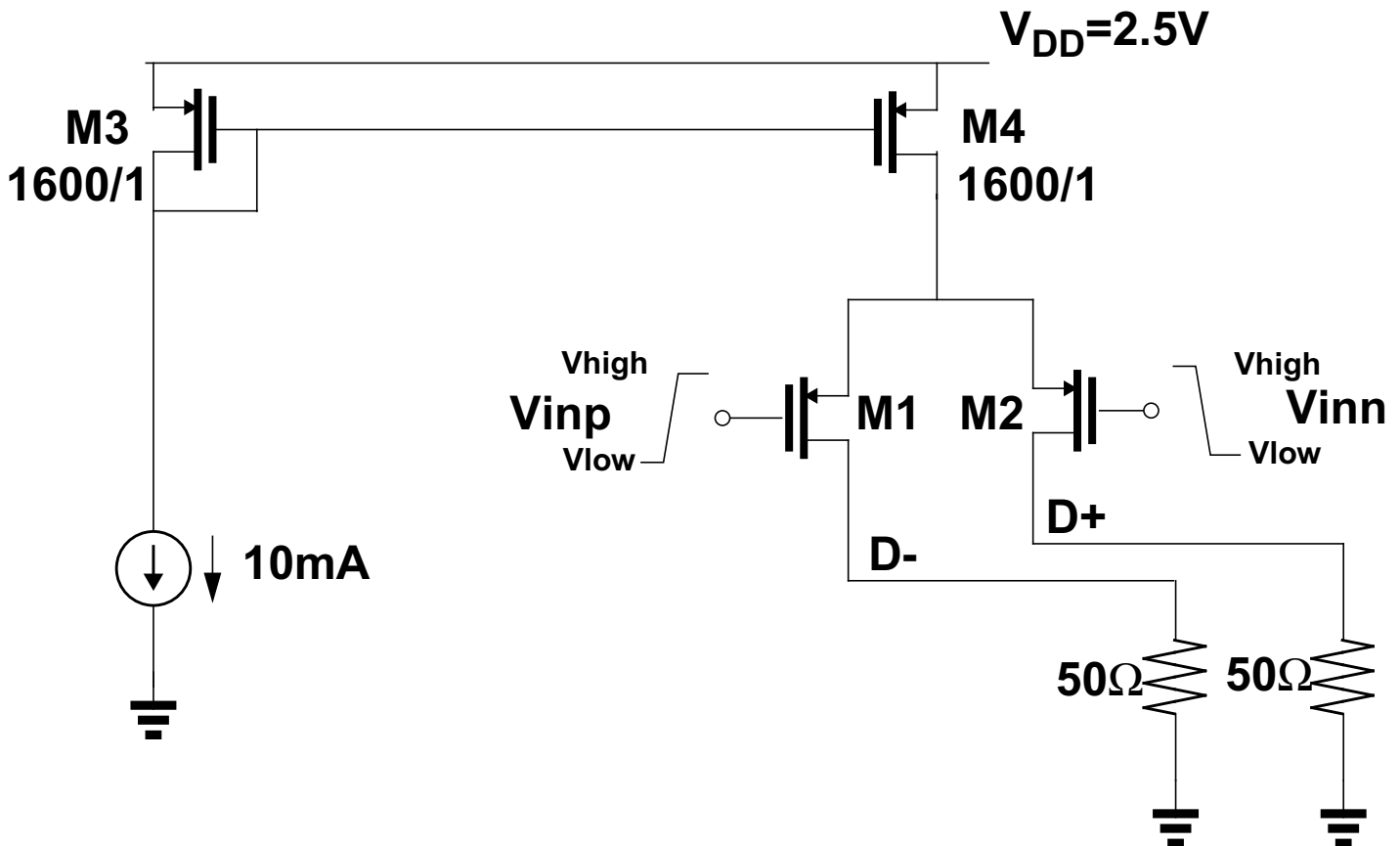
If you know the voltage at the gate, this defines the maximum voltage at the drain



Alternatively (if you know the voltage at the drain, this defines the minimum voltage at the gate):



Problem: (supplement to P 177) SKIPPED



For an interconnectivity application a differential signal current is sourced into a differential cable (D+, D-) terminated in 50Ω . The signal current is set up by the mirror M3:M4, and is switched into the positive or negative output lines by the switches M1,M2 which are driven by differential logic signals V_{inp} and V_{inn} . The low logic level (V_{low}) is 0V.

Take $K_p' = 50\mu A/V^2$, $V_{tp} = -0.75V$.

- (i) What are the dimensions of the switches for optimal mirroring accuracy?
- (ii) What is the minimum logic high level (V_{high}) such that the 'off' switch is completely turned off?

Problem Solution: (supplement to P 177) SKIPPED

(i) What are the dimensions of the switches for optimal mirroring accuracy?

$$\text{M3: } |V_{GS3}| - |V_t| = \sqrt{\frac{2 \cdot 10mA}{50\mu A/V \cdot \frac{1600}{1}}} = 500mV$$

$$|V_{GS3}| = 500mV + |V_{tp}| = 500mV + 750mV = 1.25V$$

$$V_{D3} = V_{DD} - |V_{GS3}| = 2.5V - 1.25V = 1.25V$$

For optimal mirroring accuracy the drain of M4 should be at 1.25V

Voltage at drain of M4 is set by V_{GS} across M1 or M2

For example if M1 on:

$$V_{D4} = V_{low} + V_{GS1} = 1.25V \Rightarrow V_{GS1} = 1.25V$$

So W/L of M1,M2 should be same as M3,M4 i.e. 1600/1.

(ii) What is the minimum logic high level (V_{high}) such that the 'off' switch is completely turned off?

For all current to be flowing in M1 or in M2 then

$$\sqrt{\frac{2I_S}{K'_p \frac{W}{L}}} < v_{id} < -\sqrt{\frac{2I_S}{K'_p \frac{W}{L}}}$$

$$\sqrt{\frac{2 \cdot 10mA}{50\mu A/V \cdot \frac{1600}{1}}} < V_{inp} - V_{inn} < -\sqrt{\frac{2 \cdot 10mA}{50\mu A/V \cdot \frac{1600}{1}}}$$

$$500mV < V_{inp} - V_{inn} < -500mV$$

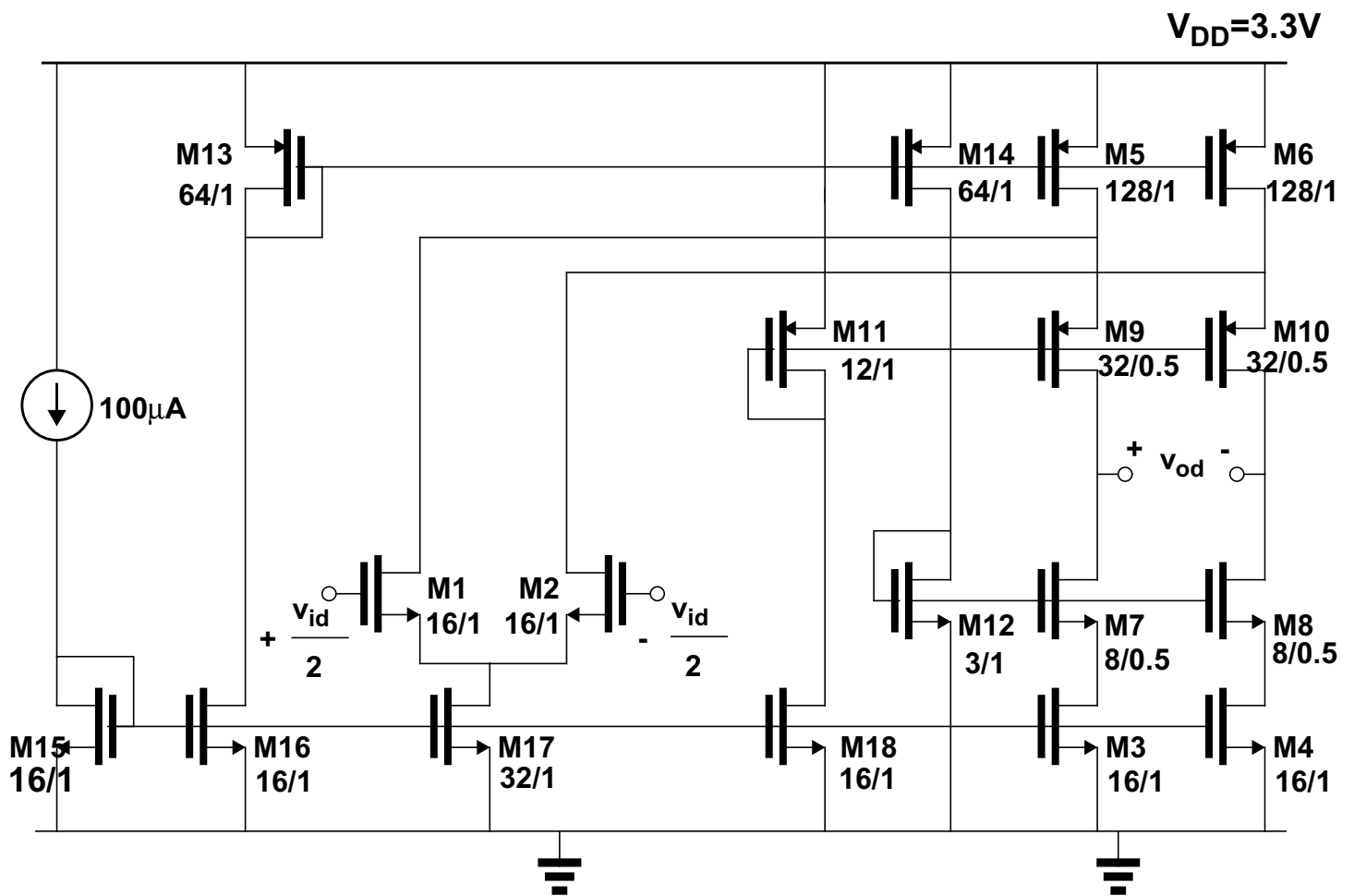
For example if all current to be flowing in M1 then

$$V_{inp} - V_{inn} < -500mV$$

$$V_{low} - V_{high} < -500mV$$

$$V_{high} > 500mV$$

Problem P208: Folded Cascode differential amplifier.



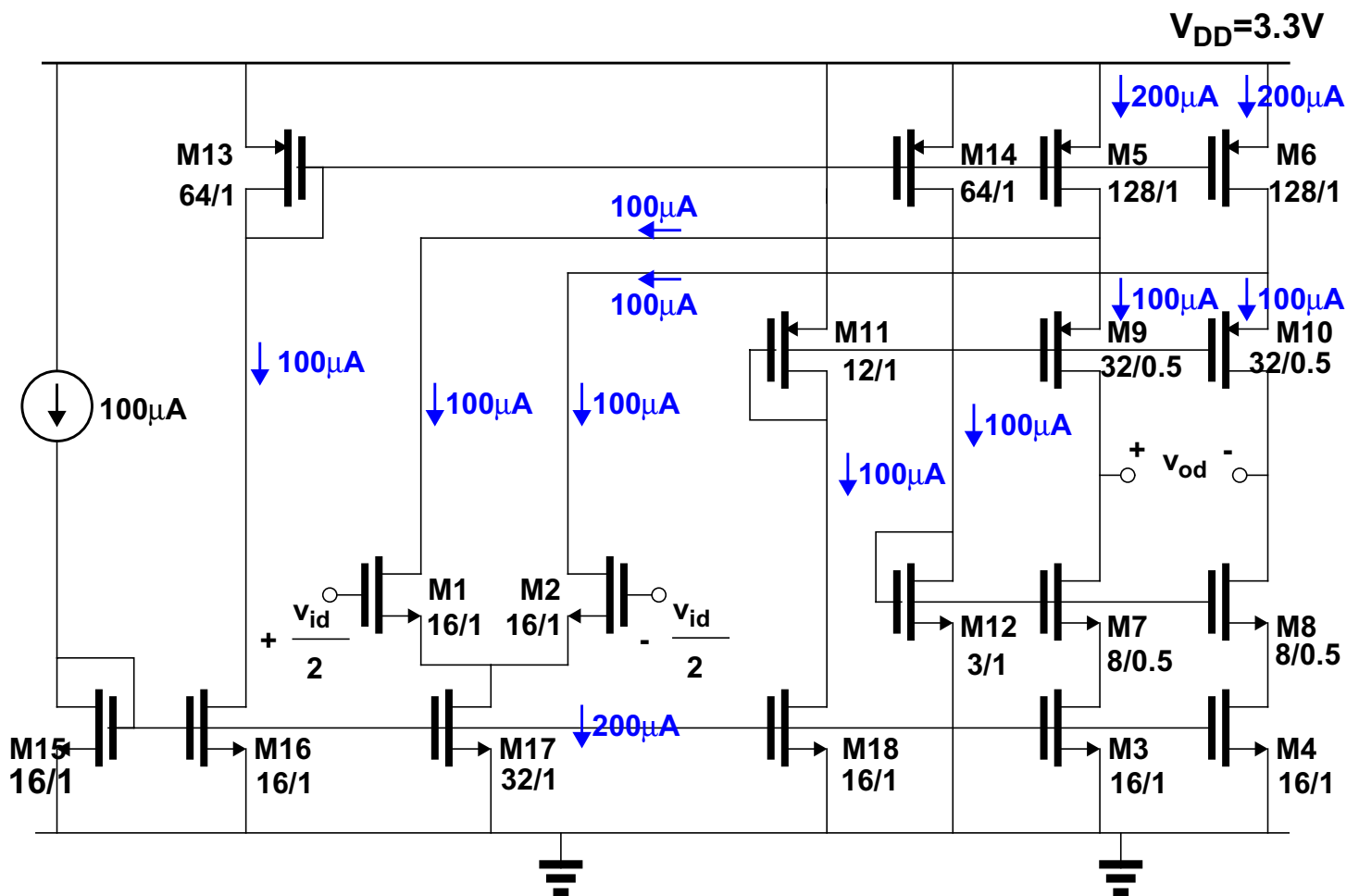
Calculate the small-signal gain of the folded-cascode amplifier shown.

Dimensions are as shown.

Assume all transistors are in saturation.

$$K_n' = 200\mu A/V^2, K_p' = 50\mu A/V^2, V_t = 0.75V, \lambda = 0.04/L V^{-1}$$

Branch Currents



The input bias current is mirrored via M15 to the p-side mirror (through M16), to the differential pair (through M17), to the output stage (through M3, M4), and to the p cascode generation diode (through M18).

The p-bias current from M16 is mirrored via M13 to the output stage (through M5, M6) and to the n cascode generation diode (through M14).

Voltage requirements

All transistors except M11,M12 are dimensioned for $V_{GS}-V_t=250mV$,
i.e. $V_{GS}=1V$

$$M3,M4: V_{GS} - V_t = \sqrt{\frac{2I_D}{K'_n \frac{W}{L}}} = \sqrt{\frac{2 \cdot 100\mu A}{200\mu A/V^2 \frac{16}{1}}} = 250mV$$

$$M9,M10: |V_{GS}| - |V_t| = \sqrt{\frac{2I_D}{K'_p \frac{W}{L}}} = \sqrt{\frac{2 \cdot 100\mu A}{50\mu A/V^2 \frac{32}{0.5}}} = 250mV$$

$$M5,M6: |V_{GS}| - |V_t| = \sqrt{\frac{2I_D}{K'_p \frac{W}{L}}} = \sqrt{\frac{2 \cdot 200\mu A}{50\mu A/V^2 \frac{128}{1}}} = 250mV$$

M12 sets up the cascode voltage on the NMOS output side.
From the notes the W/L needs to be at least 4/1.
A safety margin is taken here and 3/1 is used.

$$M12: V_{GS} - V_t = \sqrt{\frac{2I_D}{K'_n \frac{W}{L}}} = \sqrt{\frac{2 \cdot 100\mu A}{100\mu A/V^2 \frac{3}{1}}} = 577mV$$

The voltage at the source of M7 is

$$V_{S7} = (V_t + 577mV) - (V_t + 250mV) = 327mV$$

i.e. 77mV above the minimum required.

Similarly M11 sets up the cascode voltage on the PMOS output side. From the notes the W/L needs to be at least 16/1. A safety margin is taken here and 12/1 is used.

$$\text{M12: } |V_{GS}| - |V_t| = \sqrt{\frac{2I_D}{K'_p \frac{W}{L}}} = \sqrt{\frac{2 \cdot 100\mu A}{50\mu A/V^2 \frac{12}{1}}} = 577mV$$

The voltage at the source of M9 is

$$V_{S9} = V_{DD} - ((|V_t| + 577mV) + (|V_t| + 250mV))$$

$$V_{S9} = V_{DD} - 327mV$$

i.e. 77mV above the minimum required.

The common-mode input voltage needs to be greater than 1.25V so that M17 is in saturation.

The maximum common mode input voltage is given by the requirement that the input pair is in saturation i.e.

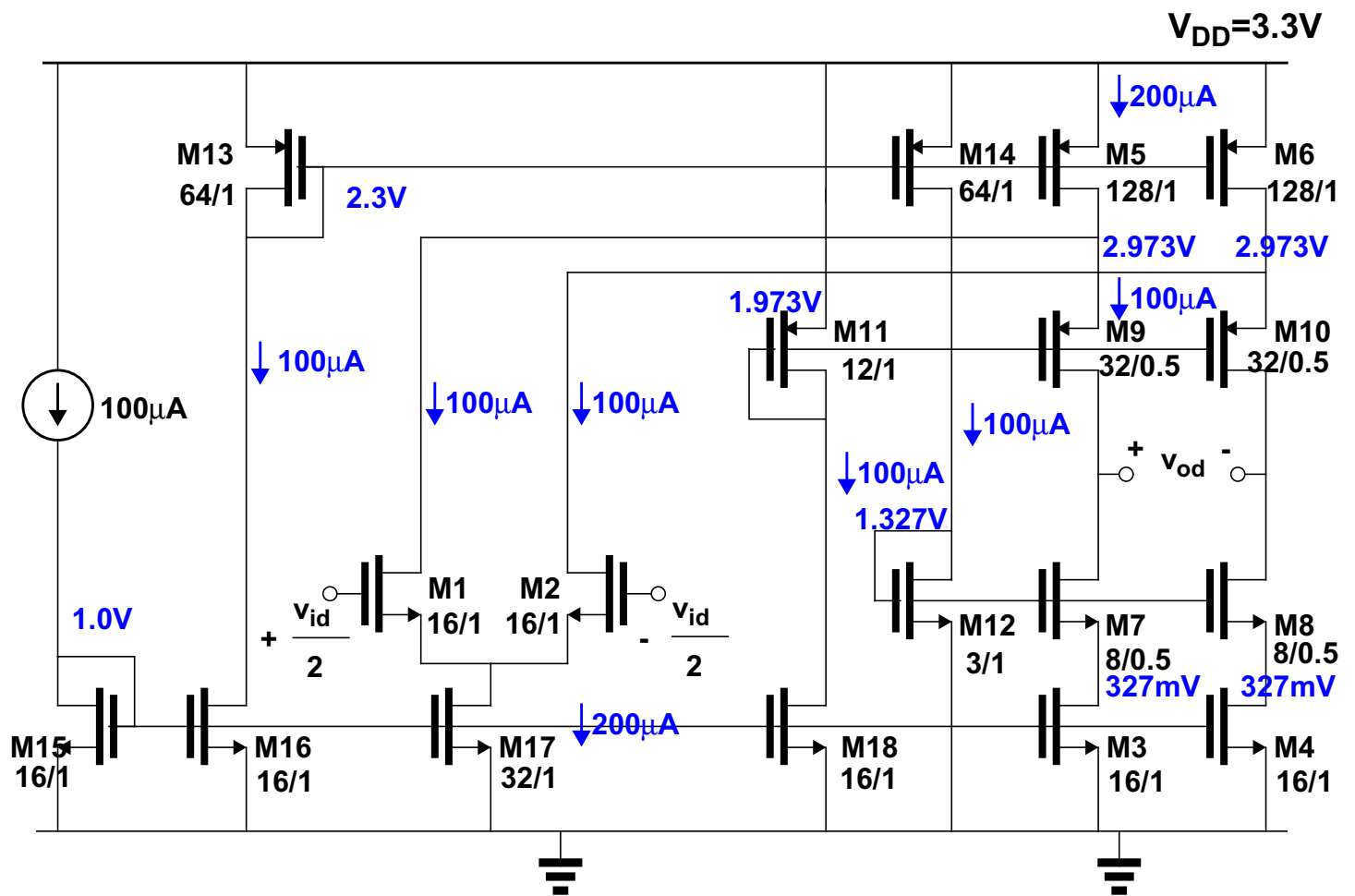
$$V_{CM} - |V_t| < V_{DD} - 327mV$$

$$V_{CM} < V_{DD} - 327mV + |V_t|$$

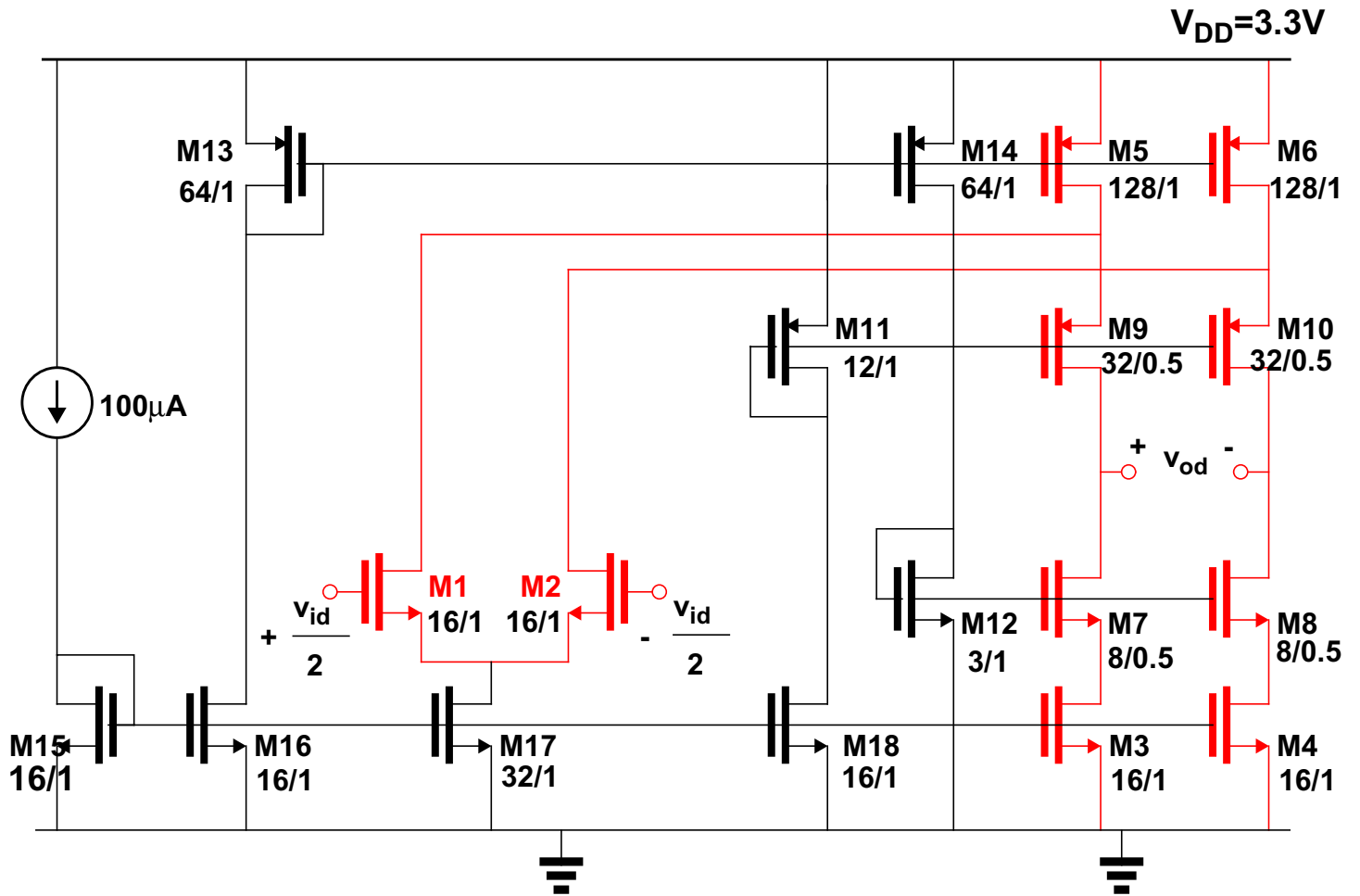
$$V_{CM} < 3.3V - 327mV + 0.75V$$

$$V_{CM} < 3.723V$$

DC Bias Voltages



Signal path



Gain

$$\frac{v_{od}}{v_{id}} = - \frac{g_{m1}}{\frac{g_{ds3}}{g_{m7}/g_{ds7}} + \frac{g_{ds1} + g_{ds5}}{g_{m9}/g_{ds9}}}$$

Use: $g_{mn} = \sqrt{2K'_n \frac{W}{L} I}$

$$g_{dsn} = \lambda_n I$$

$$g_{mp} = \sqrt{2K'_p \frac{W}{L} I}$$

$$g_{dsp} = \lambda_p I$$

$$g_{m1} = \sqrt{2 \cdot 200\mu A/V^2 \cdot \frac{16}{1} \cdot 100\mu A} = 800\mu A/V$$

$$g_{m7} = \sqrt{2 \cdot 200\mu A/V^2 \cdot \frac{8}{0.5} \cdot 100\mu A} = 800\mu A/V$$

$$g_{m9} = \sqrt{2 \cdot 50\mu A/V^2 \cdot \frac{32}{0.5} \cdot 100\mu A} = 800\mu A/V$$

$$g_{ds1} = \frac{0.04V^{-1}}{1} \cdot 100\mu A = 4\mu A/V$$

$$g_{ds3} = \frac{0.04V^{-1}}{1} \cdot 100\mu A = 4\mu A/V$$

$$g_{ds5} = \frac{0.04V^{-1}}{1} \cdot 200\mu A = 8\mu A/V$$

$$g_{ds7} = \frac{0.04V^{-1}}{0.5} \cdot 100\mu A = 8\mu A/V$$

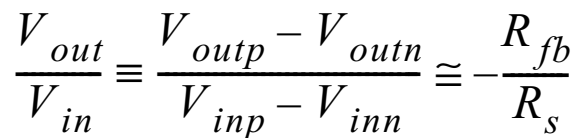
$$g_{ds9} = \frac{0.04V^{-1}}{0.5} \cdot 100\mu A = 8\mu A/V$$

$$Gain = -\frac{g_{m1}}{\frac{g_{ds3}}{g_{m7}/g_{ds7}} + \frac{g_{ds1} + g_{ds5}}{g_{m9}/g_{ds9}}} = -\frac{800}{\frac{4}{800/8} + \frac{4+8}{800/8}}$$

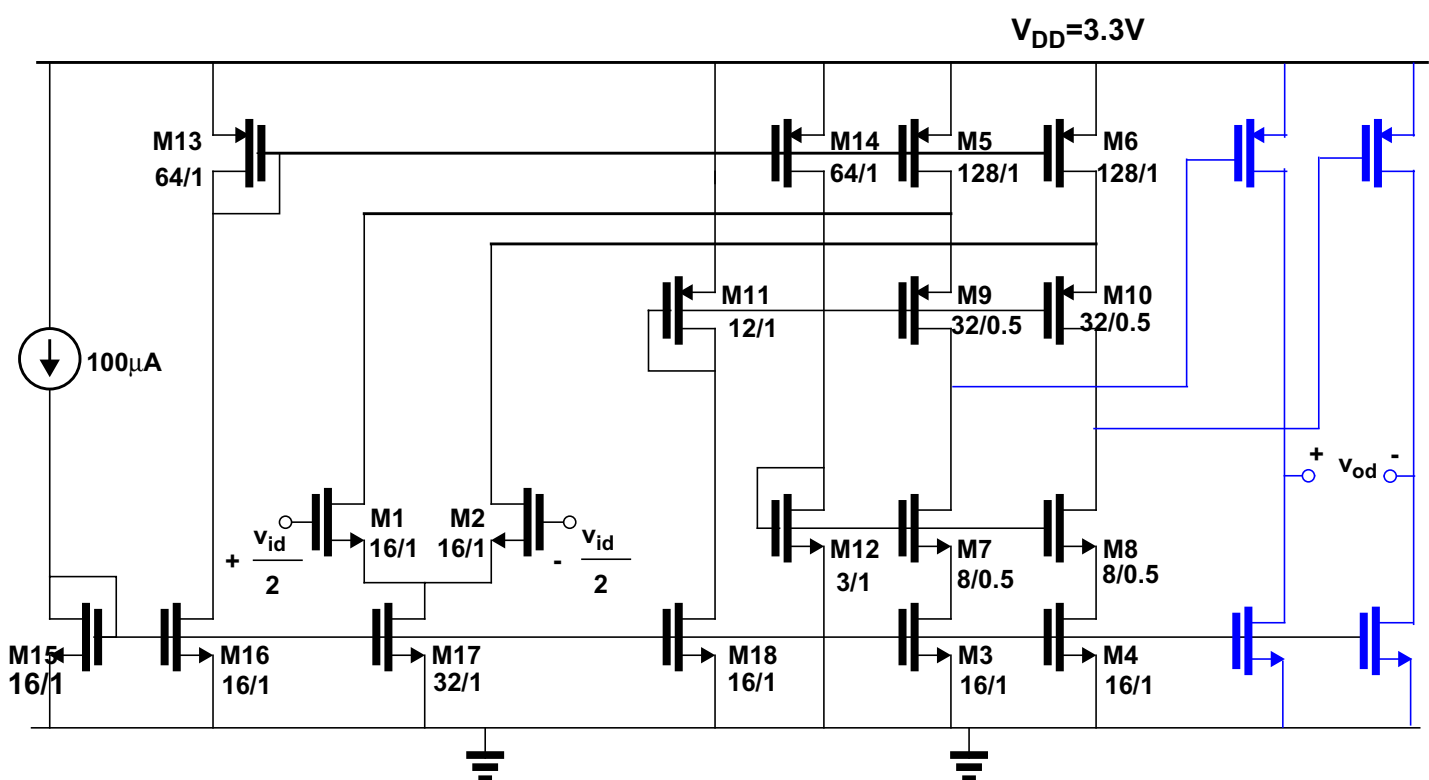
$$= -5000$$

$$\text{In dB: } Gain = 74dB$$

Many opamp applications require driving a resistive load e.g. gain stages, filters.



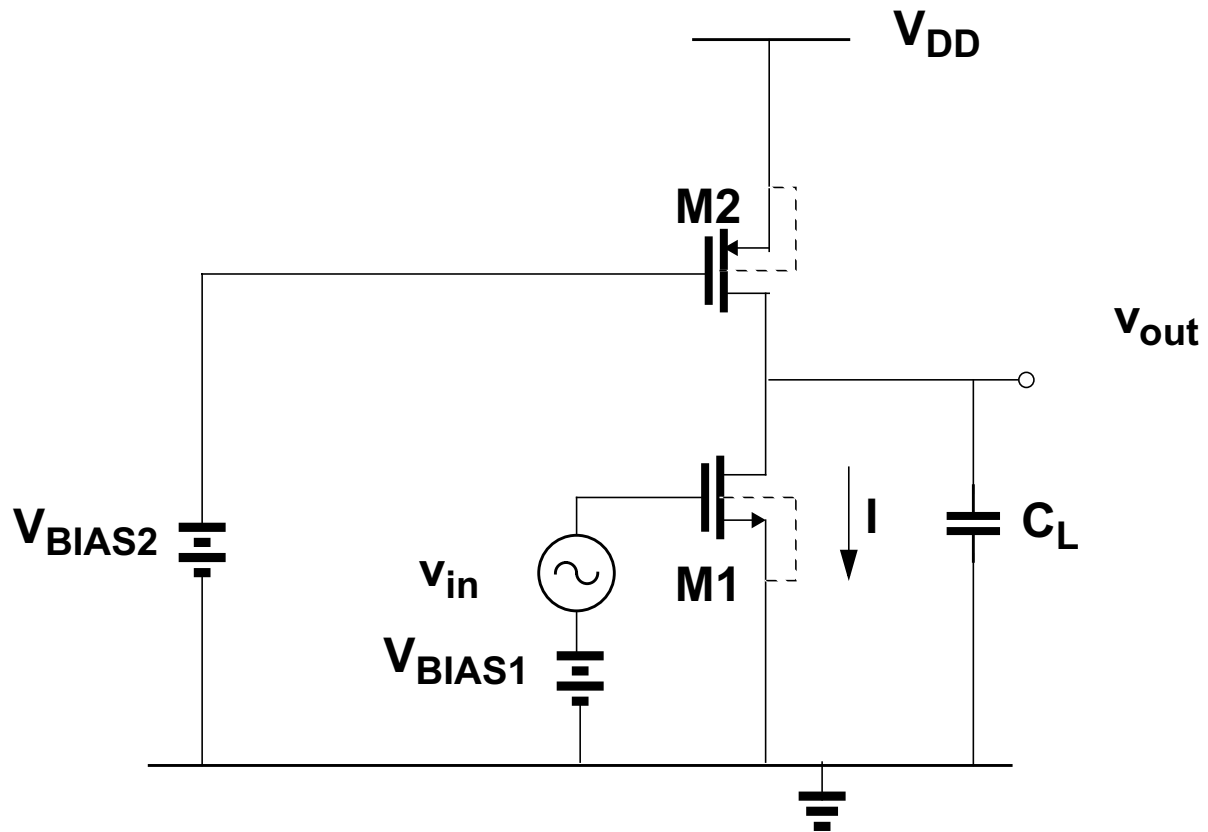
If the previous opamp were used in this configuration its gain would reduce to $\sim g_{m1} R_{fb}$. An extra buffer stage (e.g. common-source stage) is required to drive the resistive load:



Compensation for stability not shown.

Opamp as drawn has positive gain

Problem P237. CS stage with active load, h.f. analysis



$$V_{BIAS1}=1.3, V_{BIAS2}=1.7, V_{DD}=3$$

$$V_{tn}=0.8V, V_{tp}=-0.8V,$$

$$\lambda_p=0.04/L \text{ V}^{-1}, \lambda_n=0.04/L \text{ V}^{-1}$$

$$K_n'=160\mu\text{A/V}, K_p'=40\mu\text{A/V}$$

$$W_1=10, L_1=1, W_2=40, L_2=1$$

$$C_L=1\text{pF}$$

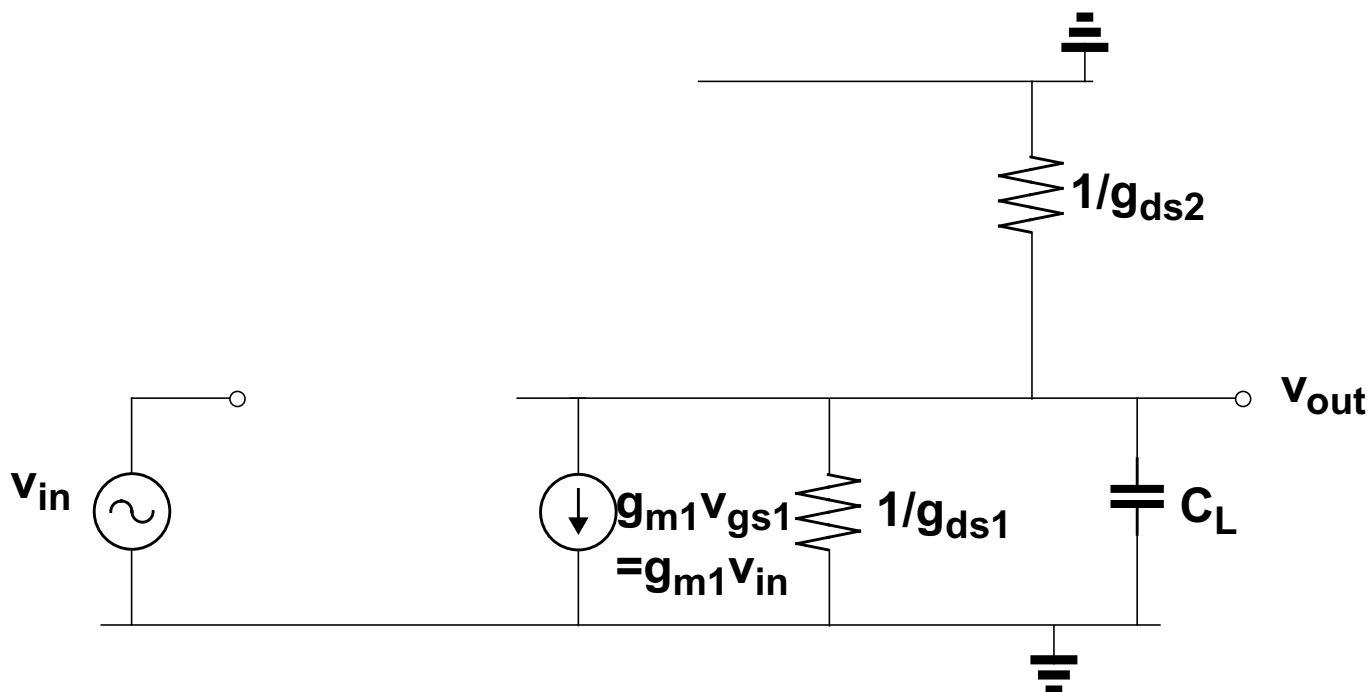
Assume all transistors are in saturation.

Ignore all capacitances except C_L

- (i) Draw the small-signal model
- (ii) Derive an expression for the gain in terms of the small-signal parameters and the load capacitance
- (iii) What is the pole frequency?
- (iv) What is the GBW?
- (v) What is the effect on the gain, pole frequency and GBW if the bias current is doubled?

Solution Common Source HF Problem P237

(i) Draw the small-signal model



(ii) Derive an expression for the gain in terms of the small-signal parameters and the load capacitance

KCL at output node

$$g_{m1}v_{in} + v_{out}g_{ds1} + v_{out}g_{ds2} + v_{out}sC_L = 0$$

$$g_{m1}v_{in} = -(g_{ds1} + g_{ds2} + sC_L)v_{out}$$

$$\frac{v_{out}}{v_{in}} = -\frac{g_{m1}}{g_{ds1} + g_{ds2} + sC_L}$$

$$\frac{v_{out}}{v_{in}} = -\frac{g_{m1}}{g_{ds1} + g_{ds2}} \cdot \frac{1}{\left(1 + \frac{sC_L}{g_{ds1} + g_{ds2}}\right)}$$

(iii) What is the pole frequency?

$$|\omega_p| = \frac{g_{ds1} + g_{ds2}}{C_L}$$

$$g_{ds1} = \lambda_n I_D$$

$$I_{D1} = \frac{K'_n W}{2L} (V_{GS1} - V_t)^2 = \frac{160 \mu A/V^2}{2} \frac{10}{1} (1.3 - 0.8)^2 = 200 \mu A$$

$$g_{ds1} = \lambda_n I_D = 0.04 V^{-1} \times 200 \mu A = 8 \mu A/V$$

$$g_{ds2} = \lambda_p I_D = 0.04 V^{-1} \times 200 \mu A = 8 \mu A/V$$

$$|\omega_p| = \frac{g_{ds1} + g_{ds2}}{C_L} = \frac{8 \mu A/V + 8 \mu A/V}{1 pF} = 16 Mrad/s$$

(iv) What is the GBW

$$GBW = A_o |\omega_p|$$

$$A_o = \frac{g_{m1}}{g_{ds1} + g_{ds2}}$$

$$|\omega_p| = \frac{g_{ds1} + g_{ds2}}{C_L}$$

$$GBW = A_o |\omega_p| = \frac{g_{m1}}{g_{ds1} + g_{ds2}} \cdot \frac{g_{ds1} + g_{ds2}}{C_L} = \frac{g_{m1}}{C_L}$$

$$g_{m1} = \sqrt{2K'_n \frac{W}{L} I_D} = \sqrt{2 \times 160 \mu A/V \times \frac{10}{1} \times 200 \mu A} = 800 \mu A/V$$

Alternatively

$$g_{m1} = \frac{2I_D}{(V_{GS1} - V_{tn})} = \frac{2 \times 100 \mu A}{0.25} = 800 \mu A/V$$

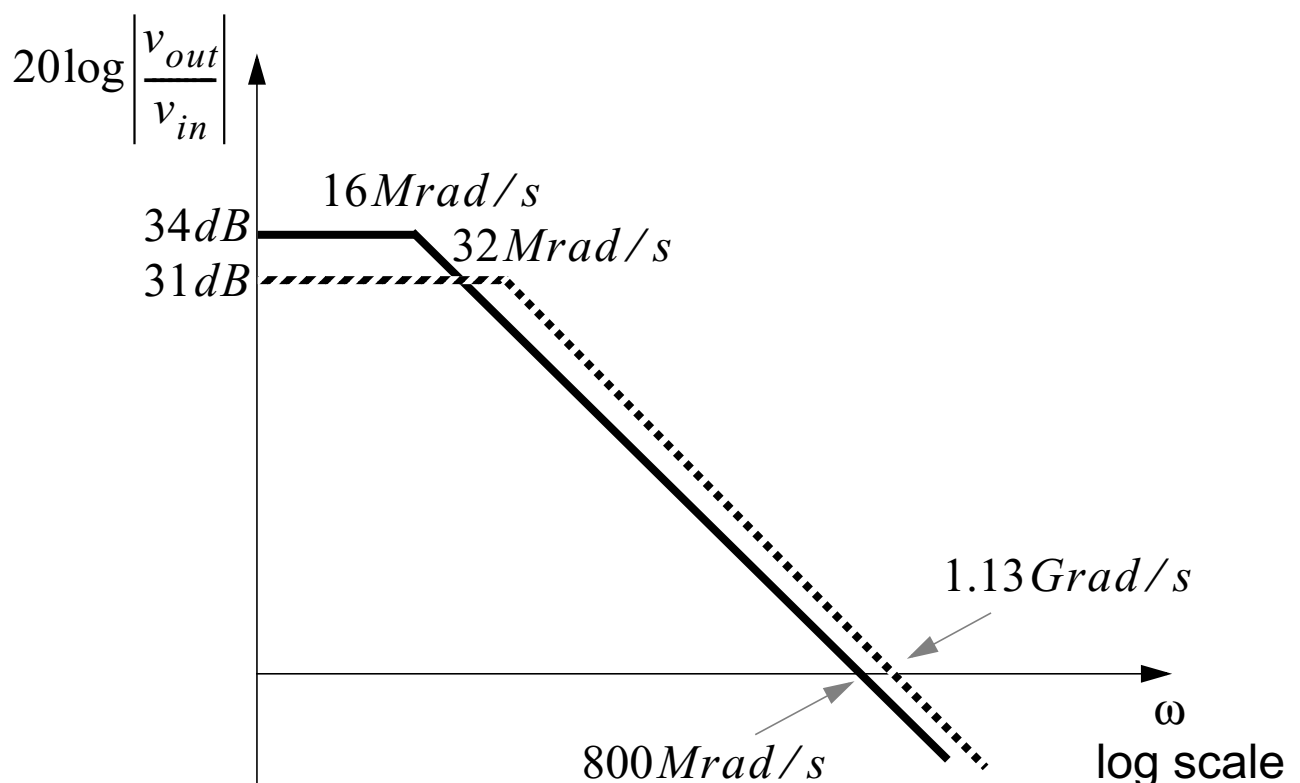
$$GBW = \frac{g_{m1}}{C_L} = \frac{800 \mu A/V}{1 pF} = 800 Mrad/s$$

(v) What is the effect on the gain, pole frequency and GBW if the bias current is doubled?

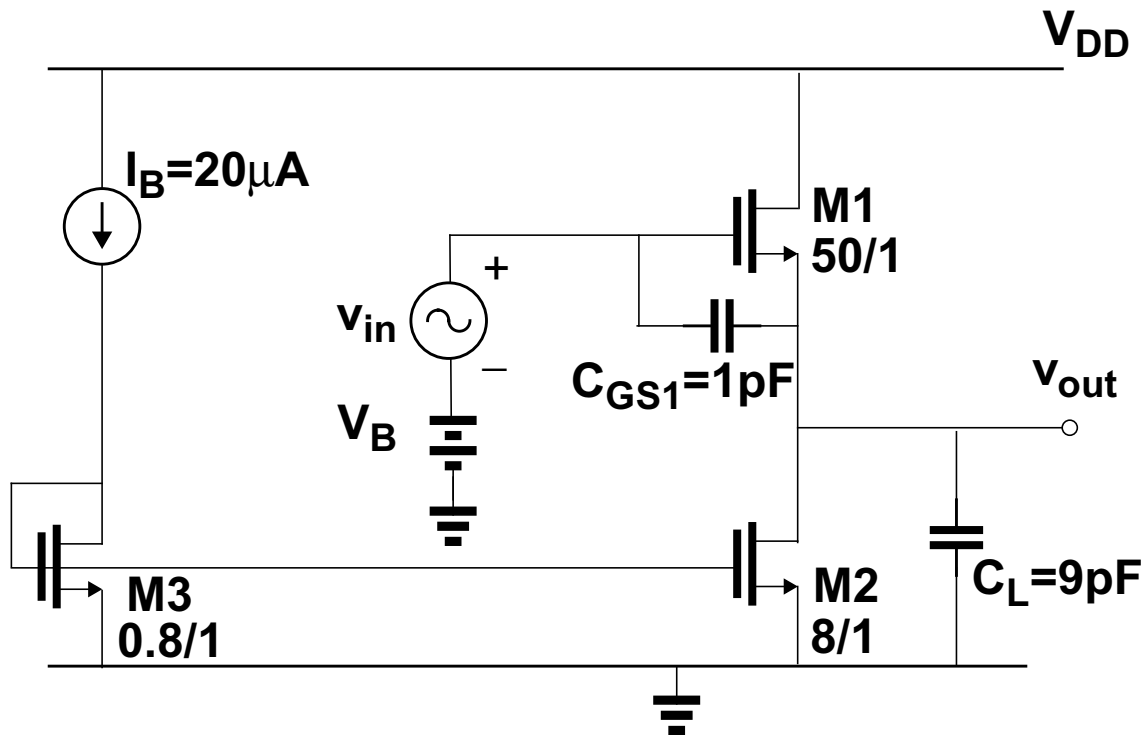
$$A_o = \frac{g_{m1}}{g_{ds1} + g_{ds2}} \quad \left. \begin{array}{l} g_{m1} \propto \sqrt{I_D} \\ g_{ds} \propto I_D \end{array} \right\} \Rightarrow A_o \propto \frac{1}{\sqrt{I_D}} \quad \text{i.e goes down by } \sqrt{2}$$

$$|\omega_p| = \frac{g_{ds1} + g_{ds2}}{C_L} \Rightarrow \omega_p \propto I_D \quad \text{i.e goes up by } 2$$

$$GBW = \frac{g_{m1}}{C_L} \Rightarrow GBW \propto \sqrt{I_D} \quad \text{i.e goes up by } \sqrt{2}$$



Problem P238: Source follower stage, h.f. analysis



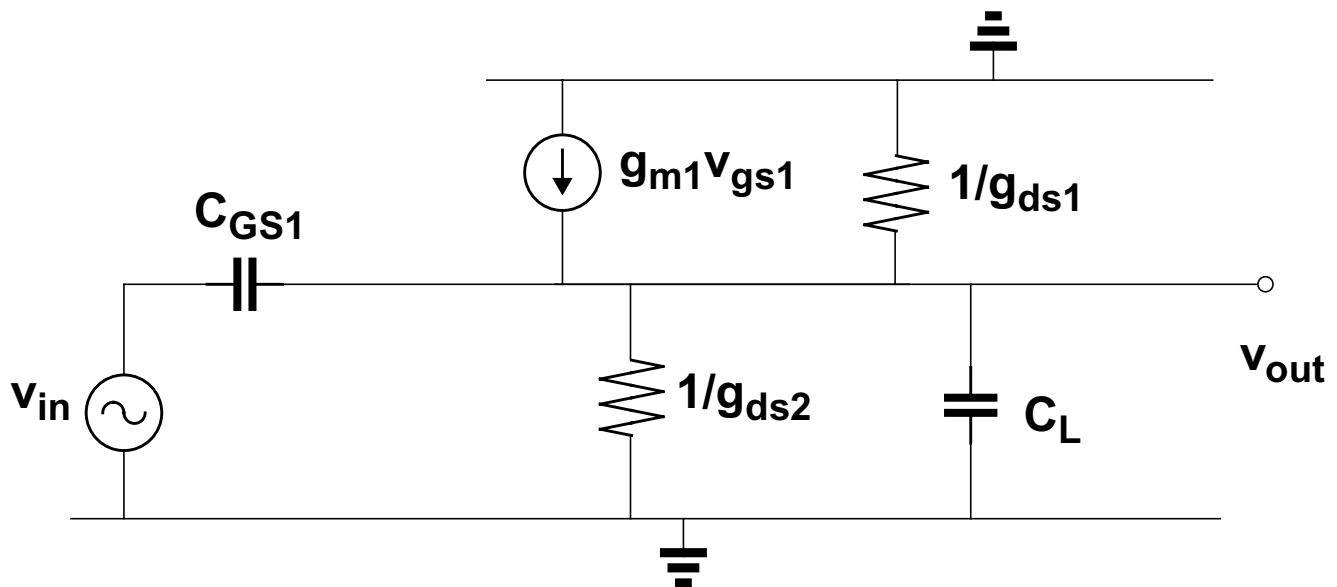
Take $K_n' = 200\mu A/V^2$.

Assume all transistors are in saturation and $g_{m1}, g_{m2} \gg g_{ds1}, g_{ds2}$.

- Draw the small-signal equivalent circuit for the source follower stage shown.
- Derive an expression for the high-frequency transfer function.
- Calculate the dc gain in dB, and the break frequencies (i.e. pole and/or zero frequencies).
- Draw a Bode diagram of the gain response.

What is the value of gain at frequencies well above the break frequencies?

- (i) Draw the small-signal equivalent circuit for the source follower stage shown in Figure 3.



- (ii) Derive an expression for the high frequency transfer function.

$$v_{gs1} = v_{in} - v_{out}$$

KCL at output node

$$(v_{in} - v_{out})sC_{gs1} + g_{m1}(v_{in} - v_{out}) - (v_{out}g_{ds1}) - (v_{out}g_{ds2}) - v_{out}sC_L = 0$$

$$(g_{m1} + sC_{gs1})v_{in} = (g_{m1} + g_{ds1} + g_{ds2} + sC_{gs1} + sC_L)v_{out}$$

$$\frac{v_{out}}{v_{in}} = \frac{g_{m1} + sC_{gs1}}{g_{m1} + g_{ds1} + g_{ds2} + sC_{gs1} + sC_L}$$

$$\frac{v_{out}}{v_{in}} = \frac{g_{m1}}{g_{m1} + g_{ds1} + g_{ds2}} \frac{\left(1 + \frac{sC_{gs1}}{g_{m1}}\right)}{\left(1 + \frac{s(C_{gs1} + C_L)}{g_{m1} + g_{ds1} + g_{ds2}}\right)}$$

(iii) Calculate the dc gain in dB, and the break frequencies (i.e. pole and/or zero frequencies).

DC gain given by

$$\frac{v_{out}}{v_{in}} = \frac{g_{m1}}{g_{m1} + g_{ds1} + g_{ds2}} \approx 1 = \underline{\underline{0dB}}$$

Pole frequency given by

$$|\omega_p| = \frac{g_{m1} + g_{ds1} + g_{ds2}}{(C_{gs1} + C_L)} \approx \frac{g_{m1}}{(C_{gs1} + C_L)}$$

$$W_3/L_3 = 10W_2/L_2 \Rightarrow I_{D2} = 10I_{D1}$$

$$g_{m1} = \sqrt{2K'_p \frac{W}{L} I_D} = \sqrt{2 \times 200\mu A/V \times \frac{50}{1} \times 200\mu A} = 2000\mu A/V$$

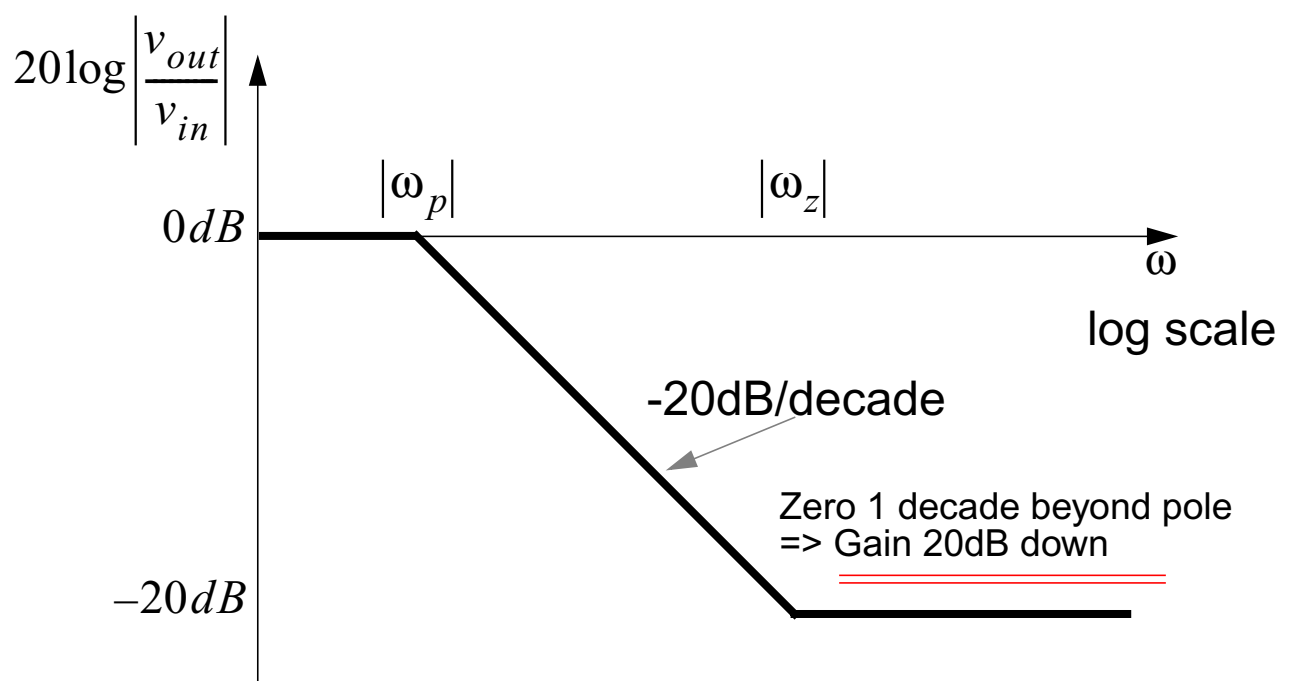
$$|\omega_p| \approx \frac{2000\mu A/V}{1pF + 9pF} = \underline{\underline{200Mrad/s}}$$

Zero frequency given by

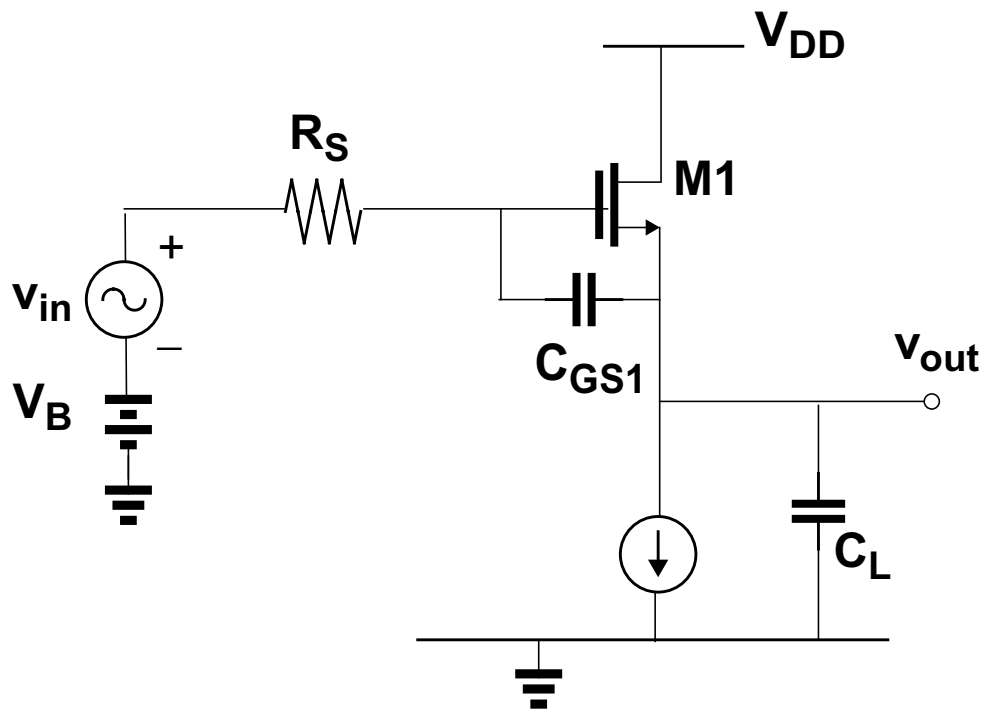
$$|\omega_z| = \frac{g_{m1}}{C_{gs1}} = \frac{2000\mu A/V}{1pF} = \underline{\underline{2Grad/s}}$$

(iv) Draw a Bode diagram of the gain response.

What is the value of gain at frequencies well above the break frequencies?



Note on high-frequency behaviour of source follower when driven from a source resistance



At low frequencies the impedance looking back into the source follower is $1/g_{m1}$

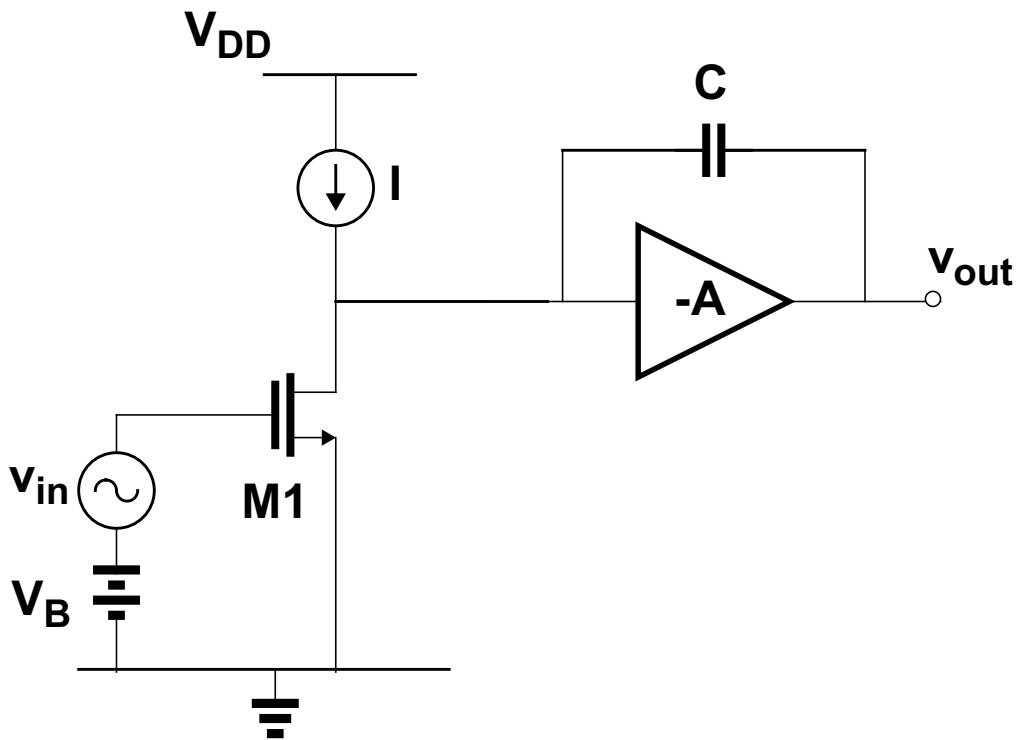
At high frequencies the impedance looking back into the source follower tends towards R_S (C_{GS} tends towards a short).

If $R_S > 1/g_m$ then the impedance increases with frequency

=> inductive

=> get ringing on step response

Problem P242: Miller capacitance.



A gain stage is cascaded with an ideal amplifier with gain $-A$. Assume M1 is in saturation.

- Write an expression for the small-signal low-frequency voltage gain (v_{out}/v_{in}) of this circuit.
- Write an expression for the frequency of the dominant pole
- Calculate the small-signal voltage gain, and the pole frequency if
 W/L of M1 = 25/1, $V_B = 1V$, $V_{tn} = 0.75V$, $K_n' = 200\mu A/V^2$, $\lambda_n = 0.04V^{-1}$
 $A = -100$, $C = 1pF$.

Problem: Miller capacitance.

- (i) Write an expression for the small-signal low-frequency voltage gain (v_{out}/v_{in}) of this circuit.

Gain is the product of the gain of the common-source stage and the gain of the ideal amplifier

$$Gain = -\frac{g_{m1}}{g_{ds1}} \cdot -A = A \frac{g_{m1}}{g_{ds1}}$$

- (ii) Write an expression for the frequency of the dominant pole

Assuming an ideal amplifier (i.e. with low output impedance), the dominant pole is at the output of the common-mode stage

The pole frequency is given by conductance at the output of the gain stage divided by the capacitance seen at this node.

The conductance is equal to g_{ds1}

The capacitance seen at this node is $(1 + A)C$

(from the Miller approximation)

The pole frequency is then given by

$$|\omega_p| = \frac{g_{ds1}}{(1 + A)C_1}$$

(iii) Calculate the small-signal voltage gain, and the pole frequency if

W/L of $M1 = 25/1$, $V_B = 1V$, $V_{tn} = 0.75V$, $K_n' = 200\mu A/V^2$, $\lambda_n = 0.04V^{-1}$
 $A = -100$, $C = 1pF$.

$$I_{D1} = \frac{K_n' W}{2L} (V_{GS1} - V_t)^2 = \frac{200\mu A/V^2}{2} \frac{25}{1} (1 - 0.75)^2 = 156\mu A$$

$$g_{m1} = \frac{2I_{D1}}{(V_{GS1} - V_{tn})} = \frac{2 \times 156\mu A}{1 - 0.75} = 1250\mu A/V$$

$$g_{ds1} = \lambda I_{D1} = 0.04V^{-1} \times 156\mu A = 6.25\mu A/V$$

Low-frequency gain given by

$$\frac{v_{out}}{v_{in}} \cong A \frac{g_{m1}}{g_{ds1}} = 100 \frac{1248\mu A/V}{6.2\mu A/V} = 20^3 = 86dB$$

Pole frequency given by

$$|\omega_p| = \frac{g_{ds1}}{(1 + A)C_1} = \frac{6.25\mu A/V}{(1 + 100)100pF} = 619rad/s$$

Problem P. 264 - Stability and feedback factor

An amplifier has the following 3 pole transfer function

$$A(s) = \frac{A_o}{\left(1 - \frac{s}{\omega_{p1}}\right)\left(1 - \frac{s}{\omega_{p2}}\right)\left(1 - \frac{s}{\omega_{p3}}\right)}$$

$$A_o = 10^4 \text{ (80dB)}$$

$$\omega_{p1} = 1 \text{ Mrad/s}$$

$$\omega_{p2} = 100 \text{ Mrad/s}$$

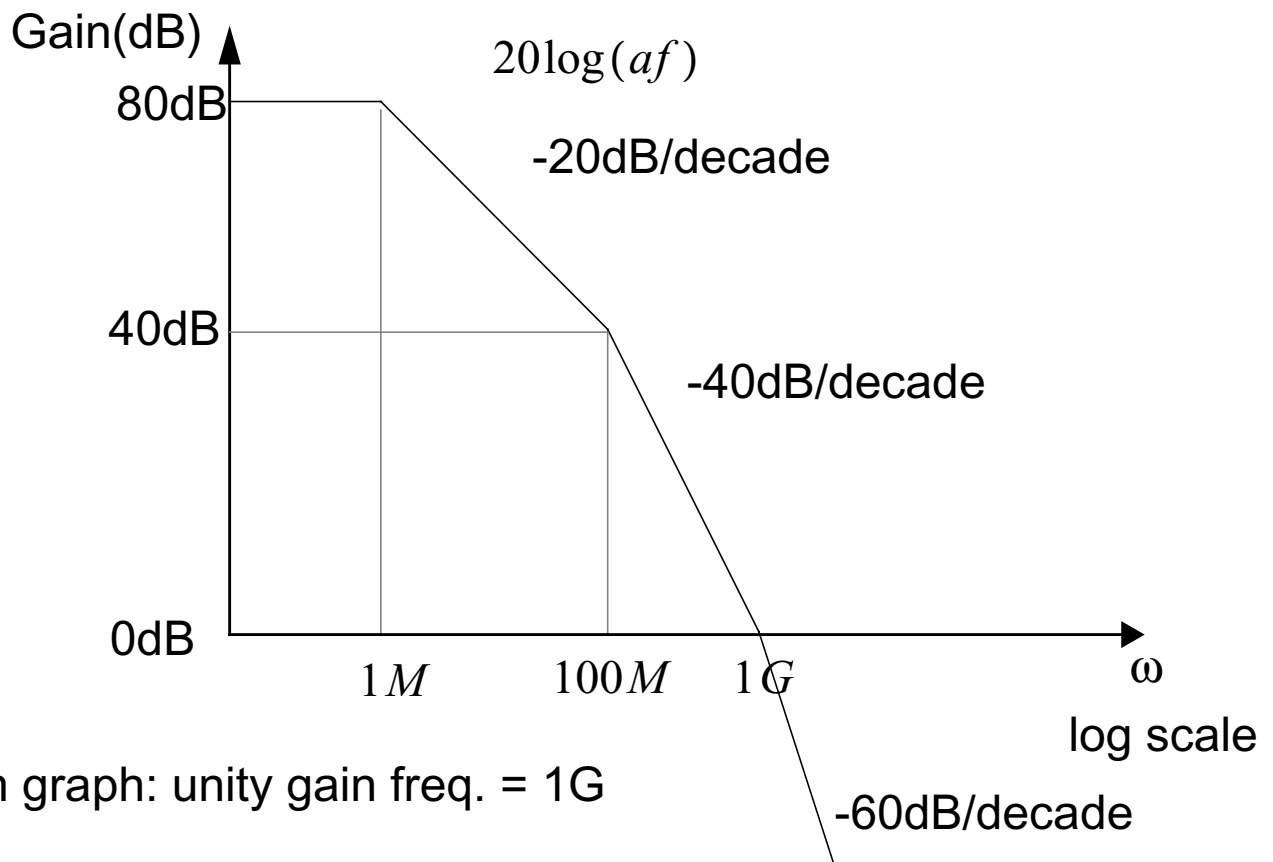
$$\omega_{p3} = 1 \text{ Grad/s}$$

- (i) Draw the Bode diagram for the gain
- (ii) If this amplifier is used in a unity gain feedback configuration, what is the phase margin?
- (iii) If the feedback factor is reduced to 0.1 what is the phase margin?

Problem P. 264 Feedback and stability

(i) Bode diagram for the gain

If feedback factor $f=1$ then loop gain = open loop gain



From graph: unity gain freq. = 1G

(ii) If this amplifier is used in a unity gain feedback configuration, what is the phase margin?

If feedback factor $f=1$ then loop gain = open loop gain

Phase Margin:

Difference between the phase shift at unity gain frequency and 180°

$$Phase_{\omega = \omega_u} = -\operatorname{atan}\left(\frac{\omega_u}{\omega_{p1}}\right) - \operatorname{atan}\left(\frac{\omega_u}{\omega_{p2}}\right) - \operatorname{atan}\left(\frac{\omega_u}{\omega_{p3}}\right)$$

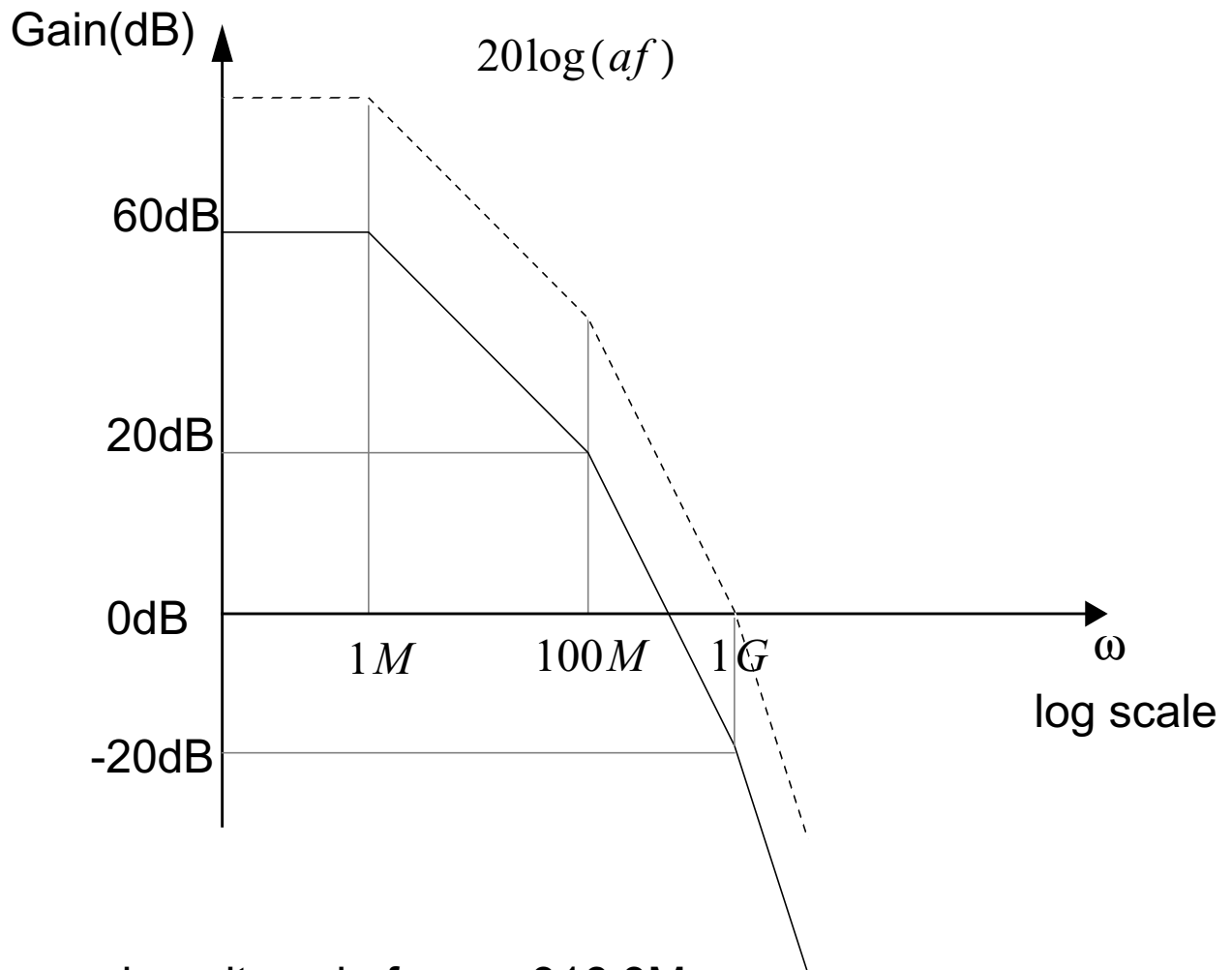
$$Phase_{\omega = \omega_u} = -\operatorname{atan}\left(\frac{1G}{1M}\right) - \operatorname{atan}\left(\frac{1G}{100M}\right) - \operatorname{atan}\left(\frac{1G}{1G}\right)$$

$$Phase_{\omega = \omega_u} = -90 - 84 - 45 = -219$$

$$PM = -39 \quad \Rightarrow \text{Unstable}$$

(iii) If the feedback factor is reduced to 0.1 what is the phase margin?

Reduce feedback factor to 0.1 i.e. move af down 20dB



From graph: unity gain freq. = $316.3M$

$$Phase_{\omega = \omega_u} = -\text{atan}\left(\frac{316M}{1M}\right) - \text{atan}\left(\frac{316M}{100M}\right) - \text{atan}\left(\frac{316M}{1G}\right)$$

$$Phase_{\omega = \omega_u} = -90 - 72.5 - 17.5 = 0 - 180$$

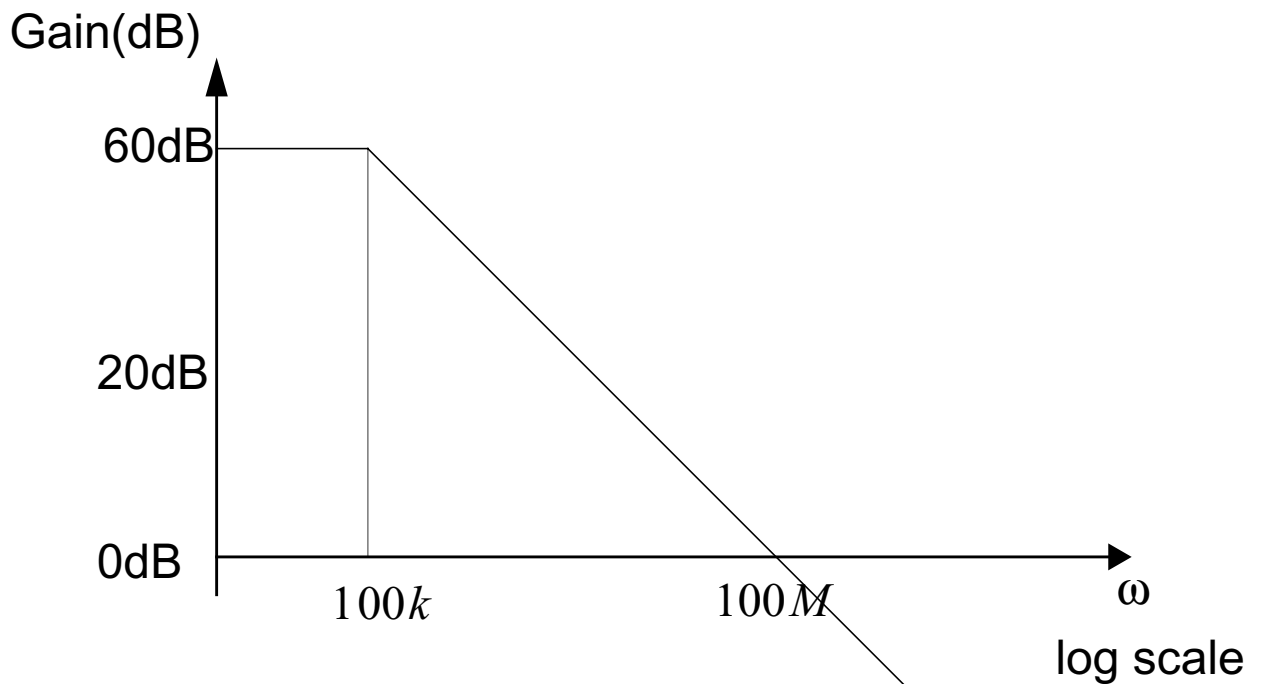
$$PM = 0$$

Marginally stable

Reduce f another 20dB: unity gain freq = $100M \Rightarrow PM = 45^\circ$

Note: these are approximate values

Example: First order system, Gain = 60dB, BW = 100k, GBW = 100M



What is effect of second pole at GBW, $0.5 \cdot \text{GBW}$, $2 \cdot \text{GBW}$ if system is used in unity gain configuration?

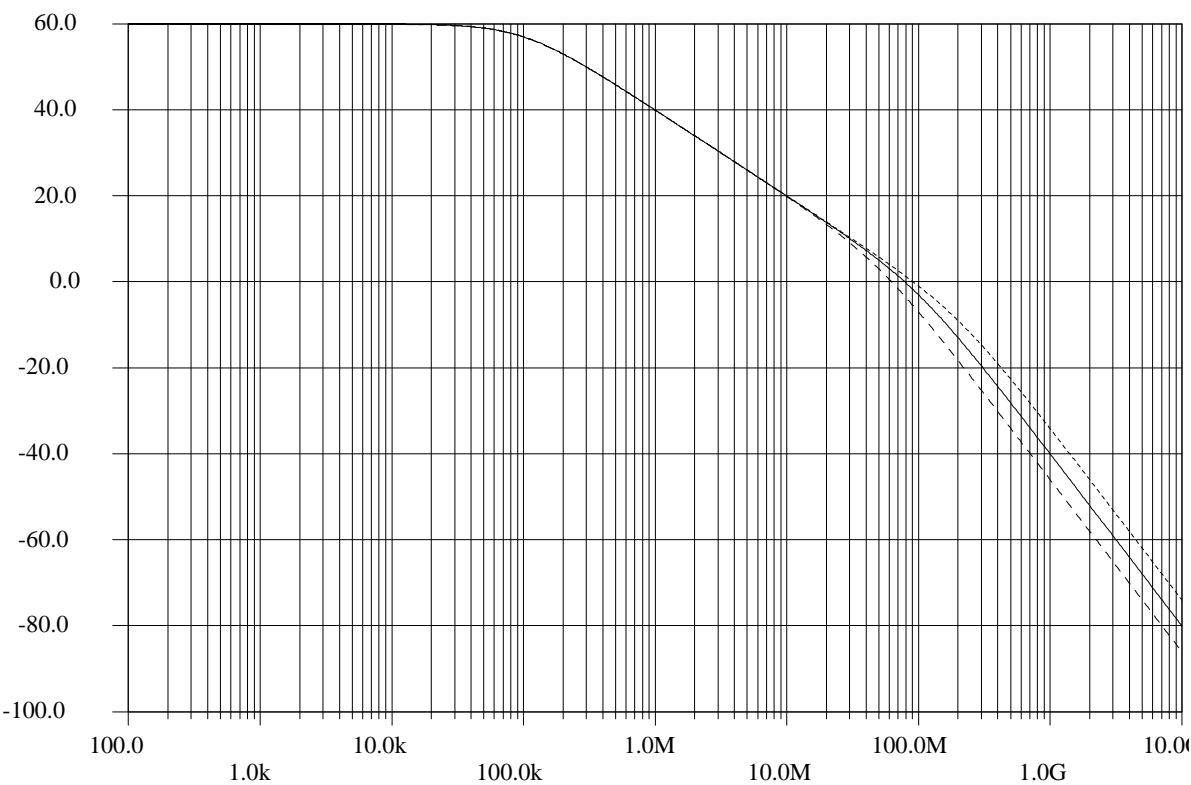
Note: Using the Bode approximation this would give us PM's of 45° , 26.6° and 63° respectively.

The following plots give 51.9° , 38.7° and 65.5° respectively due to the gain curve being 3dB lower at the second pole compared with the Bode approximation, i.e. the unity gain frequency occurs earlier.

Open-loop response:

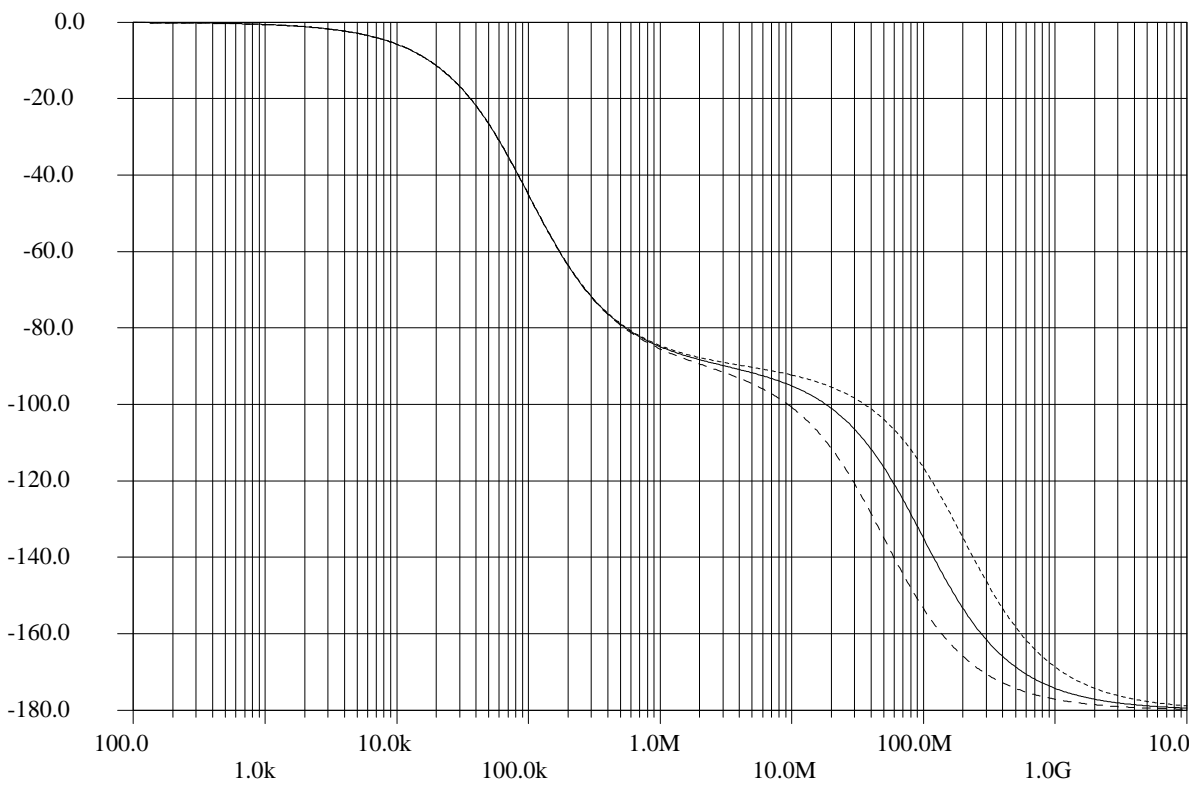
- y1-axis -
DB(VN(OUT2P))

- Subvar -
(0) ———
WP2: 100.0M
(1) - - - - -
WP2: 50.0M
(2) - - - - -
WP2: 200.0M

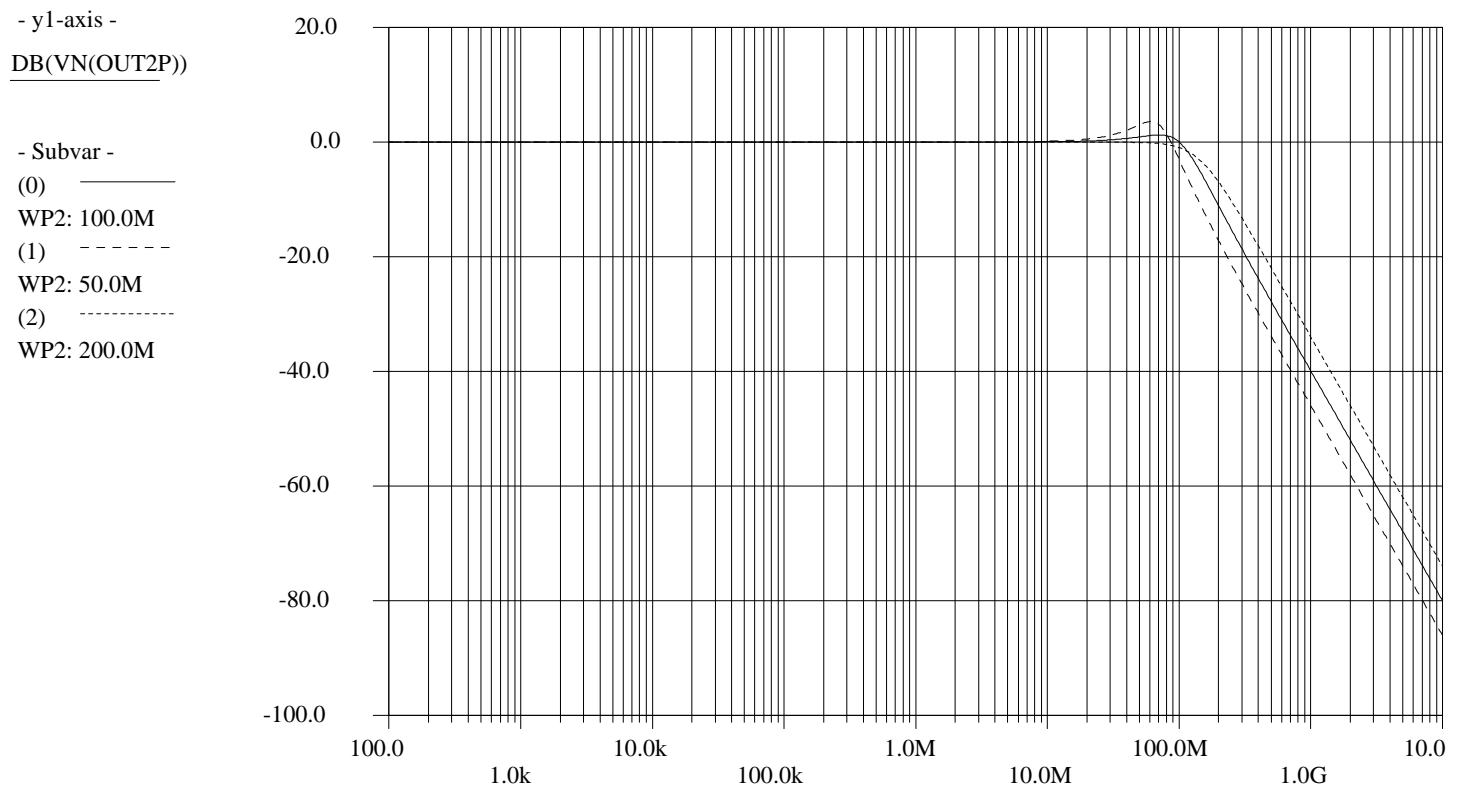


- y1-axis -
PHA(VN(OUT2P))

- Subvar -
(0) ———
WP2: 100.0M
(1) - - - - -
WP2: 50.0M
(2) - - - - -
WP2: 200.0M

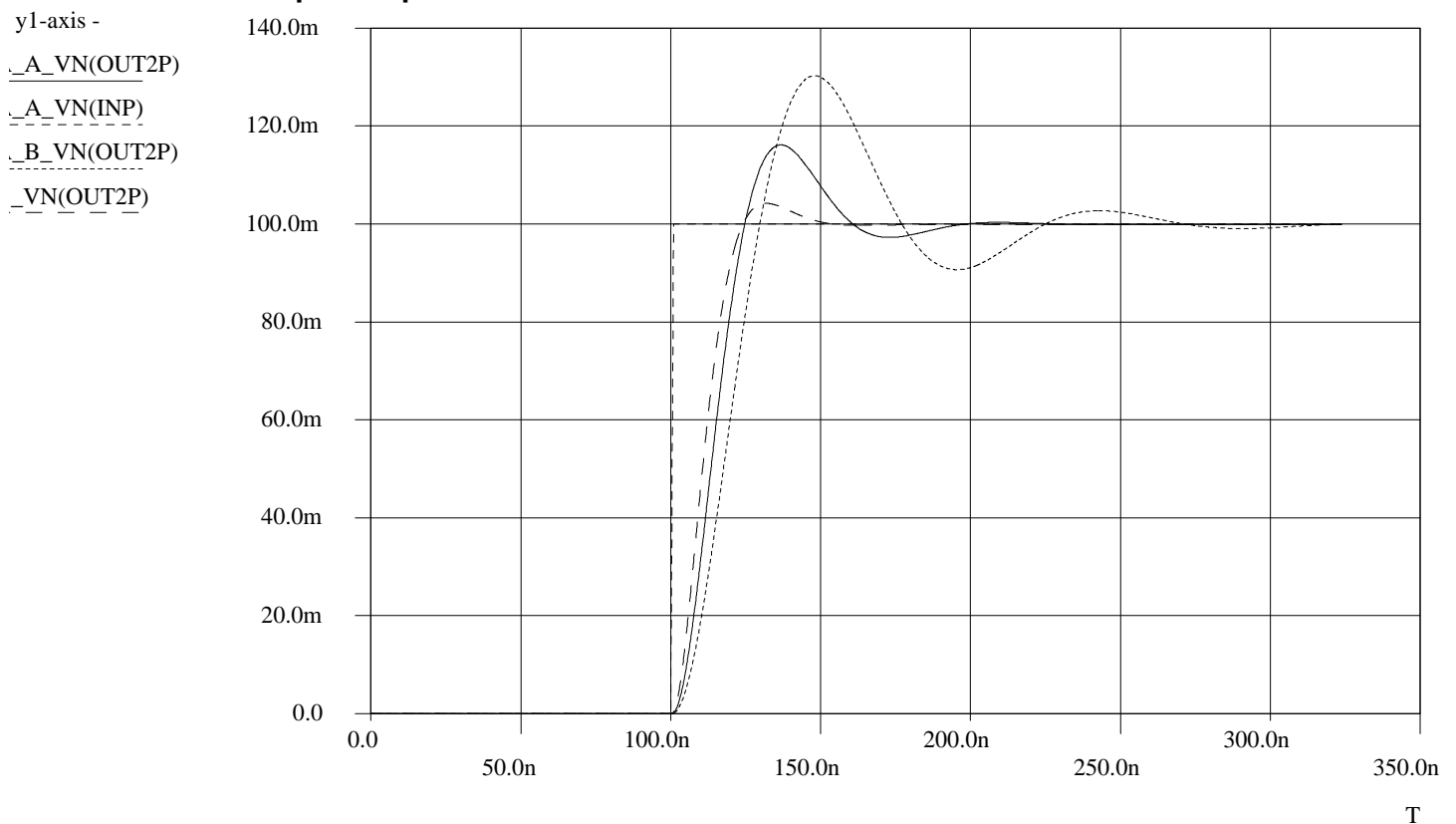


Closed-loop response:



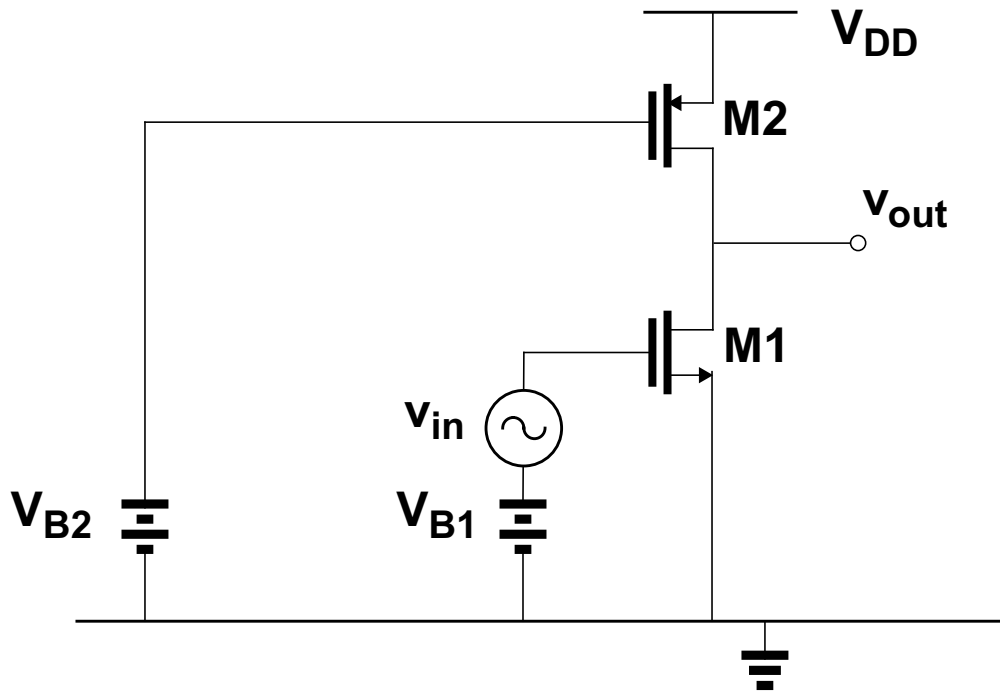
Note peaking in closed loop response

Transient Step response:



Note overshoot in transient step response

Problem P 328: CS with active load noise analysis



Assume M1 and M2 are operating in saturation. Only thermal noise sources need be considered.

For calculations take Boltzmann's constant $k=1.38 \times 10^{-23} \text{ J/}^\circ\text{K}$, temperature $T=300^\circ\text{K}$.

(i) Draw the small-signal model for the circuit shown.

What is the low-frequency small-signal voltage gain ($v_{\text{out}}/v_{\text{in}}$) in terms of the small-signal parameters of M1 and M2?

(ii) What is the input-referred thermal noise voltage density of M1?

What is the input-referred thermal noise voltage density of M2?

Answers should be in terms of the small-signal parameters of M1 and M2, Boltzmann's constant k and temperature T .

(iii) Calculate the input-referred thermal noise voltage density of M1

and the input-referred thermal noise voltage density of M2 if

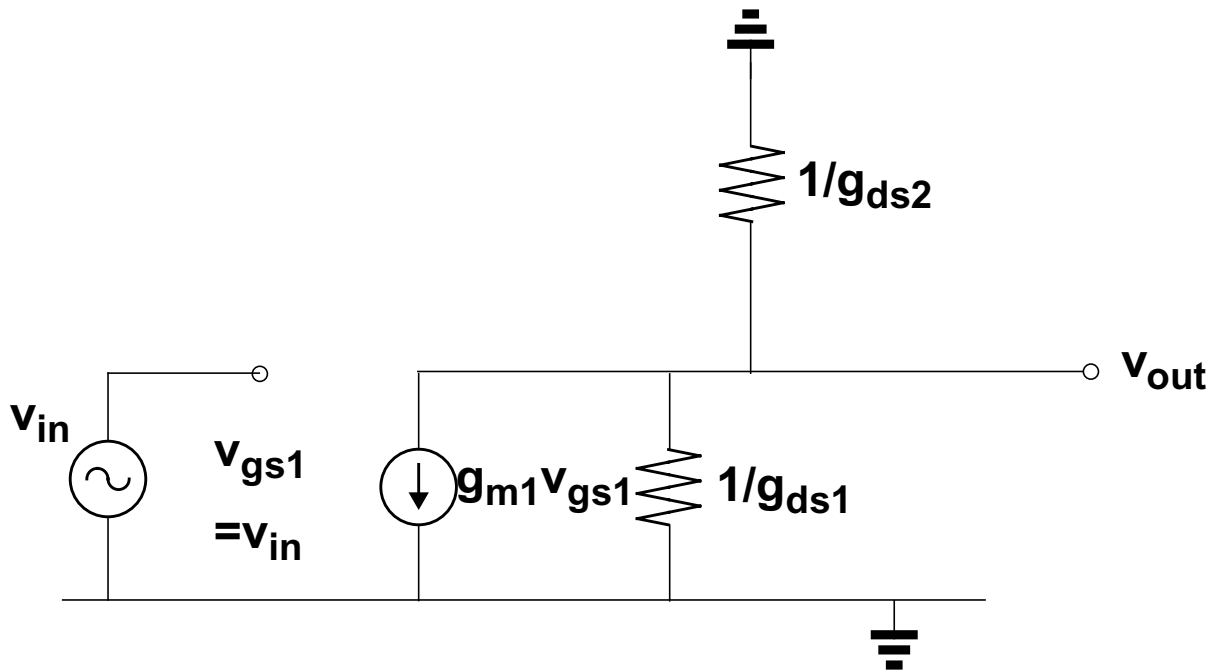
$V_{B1}=1.0\text{V}$, $V_{B2}=1.25\text{V}$, $V_{DD}=3\text{V}$, $V_{tn} = 0.75\text{V}$, $V_{tp} = -0.75\text{V}$, $\lambda_n=\lambda_p=0.04\text{V}^{-1}$. The drain current of M1 is $100\mu\text{A}$.

Which is the dominant noise source?

(iv) Calculate the total noise voltage at the output over a bandwidth of 1MHz. If the input signal v_{in} is a 1mV_{rms} sine wave, calculate the signal-to-noise ratio in dB at the output over a bandwidth of 1MHz.

Solution Problem P 328: CS with active load noise analysis

- (i) Draw the small-signal model for the circuit shown in Figure 4.
What is the low-frequency small-signal voltage gain (v_{out}/v_{in}) in terms of the small-signal parameters of M1 and M2?

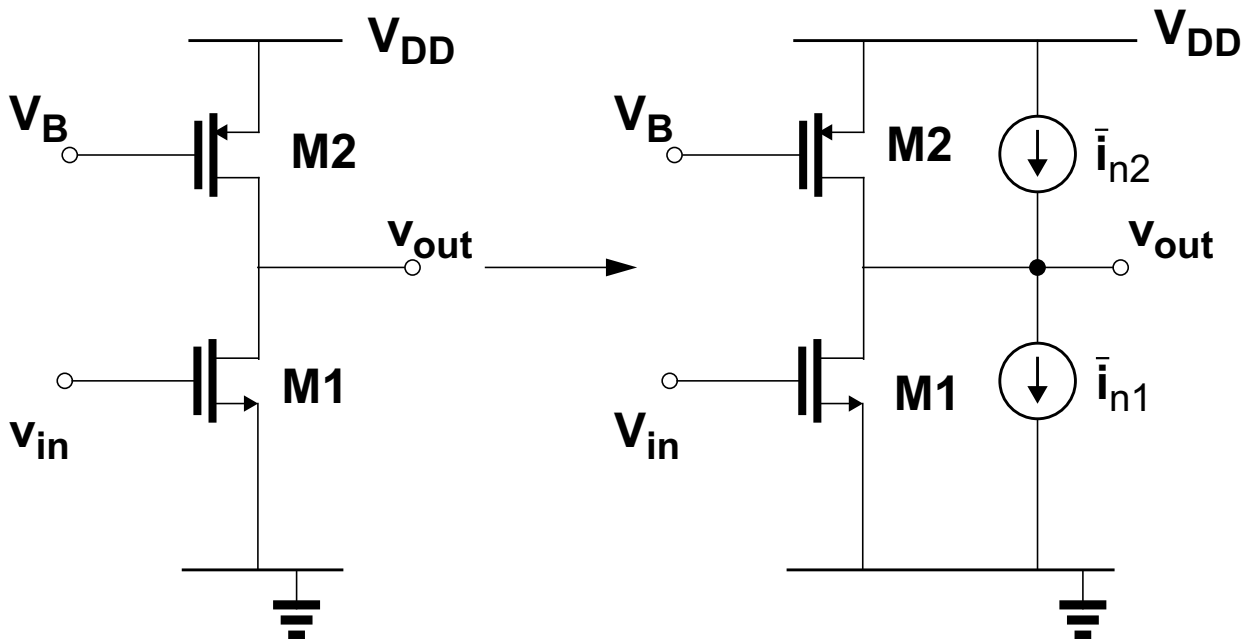


Current at output node

$$g_{m1}v_{in} + v_{out}g_{ds1} + v_{out}g_{ds2} = 0$$

$$\frac{v_{out}}{v_{in}} = -\frac{g_{m1}}{\underline{\underline{g_{ds1} + g_{ds2}}}}$$

- (ii) What is the input-referred thermal noise voltage density of M1?
 What is the input-referred thermal noise voltage density of M2?
 Answers should be in terms of the small-signal parameters of M1 and M2,
 Boltzmann's constant k and temperature T .



Noise current of MOS:

$$\overline{i_n^2} = 4kT\left(\frac{2}{3}g_m\right)$$

Input-referred noise of M1

$$\overline{v_{niM1}} = \frac{\overline{i_{nM1}}}{g_{m1}} = \frac{\sqrt{4kT\left(\frac{2}{3}g_{m1}\right)}}{g_{m1}} = \sqrt{\frac{4kT\left(\frac{2}{3}\right)}{g_{m1}}} \quad \text{rms noise} \quad V / \sqrt{Hz}$$

Input-referred noise of M2

$$\overline{v_{niM2}} = \frac{\overline{i_{M2}}}{g_{m1}} = \frac{\sqrt{4kT\left(\frac{2}{3}g_{m2}\right)}}{g_{m1}} = \sqrt{4kT\left(\frac{2}{3}\frac{g_{m2}}{g_{m1}}\right)} \quad \text{rms noise} \quad V / \sqrt{Hz}$$

(iii) Calculate the input-referred thermal noise voltage density of M1 and the input-referred thermal noise voltage density of M2 if

$$V_{B1}=1.0V, V_{B2}=1.25V, V_{DD}=3V, V_{tn} = 0.75V, V_{tp} = -0.75V, \lambda_n=\lambda_p=0.04V^{-1}.$$

The drain current of M1 is $100\mu A$.

Which is the dominant noise source?

g_m given by

$$g_m = \frac{2I_D}{(V_{GS}-V_T)}$$

$$g_{m1} = \frac{2 \cdot 100\mu A}{1V - 0.75V} = 800\mu A/V \quad g_{m2} = \frac{2 \cdot 100\mu A}{1.75V - 0.75V} = 200\mu A/V$$

Input-referred noise of M1

$$\overline{v_{niM1}} = \sqrt{\frac{4kT\left(\frac{2}{3}\right)}{g_{m1}}} = \sqrt{\frac{(4 \cdot 1.38 \times 10^{-23} \cdot 300)\left(\frac{2}{3}\right)}{800\mu A/V}} = \underline{\underline{3.71nV/\sqrt{Hz}}}$$

Input-referred noise of M2

$$\overline{v_{niM2}} = \sqrt{4kT\left(\frac{2}{3} \frac{g_{m2}}{g_{m1}}\right)} = \sqrt{(4 \cdot 1.38 \times 10^{-23} \cdot 300)\left(\frac{2}{3}\right) \cdot \frac{200\mu A/V}{800\mu A/V^2}} = \underline{\underline{1.86nV/\sqrt{Hz}}}$$

M1 is dominant noise source

(iv) Calculate the total noise voltage at the output over a bandwidth of 1MHz.

If the input signal v_{in} is a $1mV_{rms}$ sine wave, calculate the signal-to-noise ratio in dB at the output over a bandwidth of 1MHz.

$$g_{ds1} = \lambda_n I_D = 0.04V^{-1} 100\mu A = 4\mu A/V$$

$$g_{ds2} = \lambda_n I_D = 0.04V^{-1} 100\mu A = 4\mu A/V$$

Gain of stage

$$Gain = -\left(\frac{g_{m1}}{g_{ds1} + g_{ds2}}\right) = -\frac{800\mu A/V}{8\mu A/V} = -100$$

Total input-referred noise

$$\overline{v_{nitot}} = \sqrt{\left[\frac{4kT\left(\frac{2}{3}\right)}{g_{m1}}\right]^2 + \left[4kT\left(\frac{2}{3}\frac{g_{m2}}{g_{m1}}\right)\right]^2}$$

$$\overline{v_{nitot}} = \sqrt{(3.71nV/\sqrt{Hz})^2 + (1.86nV/\sqrt{Hz})^2} = 4.15nV/\sqrt{Hz}$$

Total noise at output given by

$$\overline{v_{notot}} = \overline{v_{nitot}} \cdot \left(\frac{g_{m1}}{g_{ds1} + g_{ds2}}\right) \cdot \sqrt{BW} = 4.15nV/\sqrt{Hz} \cdot 100 \cdot \sqrt{1MHz} = \underline{\underline{415\mu V_{rms}}}$$

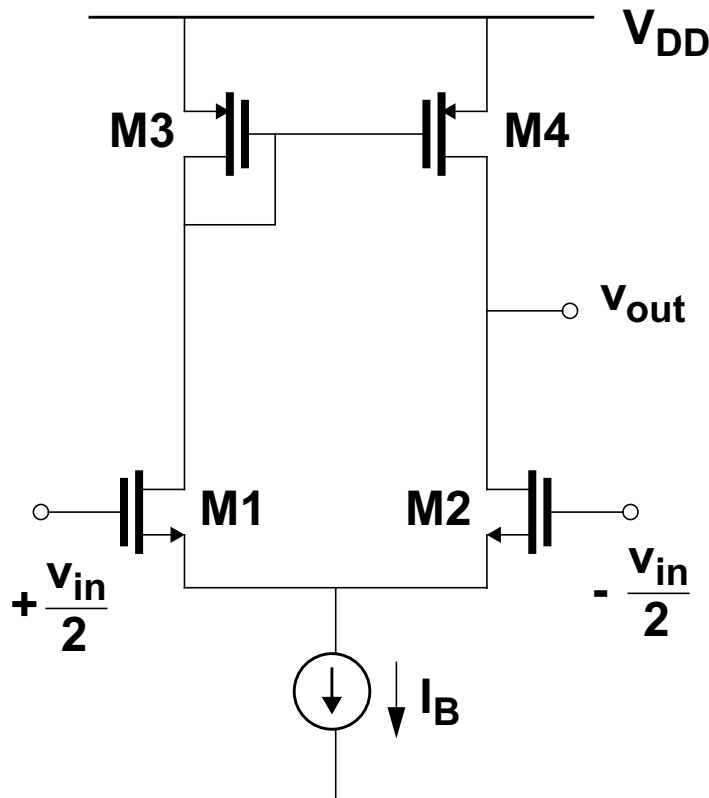
Output signal

$$v_{out} = -\left(\frac{g_{m1}}{g_{ds1} + g_{ds2}}\right)v_{in} = -\frac{800\mu A/V}{8\mu A/V} \cdot 1mV_{rms} = 100mV_{rms}$$

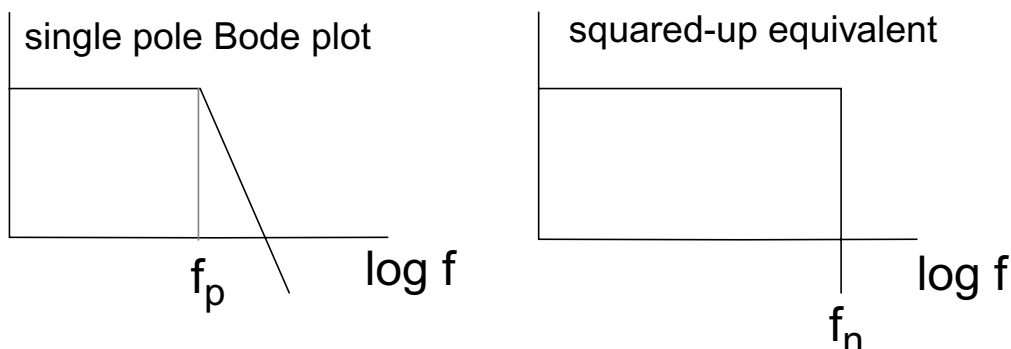
Signal-to-Noise ratio given by

$$\frac{S}{N} = \frac{100mV}{415\mu V_{rms}} = 241 \quad \text{or } \underline{\underline{47.6 \text{ dB}}}$$

Problem P329: Differential pair noise analysis



- (i) What is the input-referred thermal noise voltage density of the circuit shown, in terms of the small signal parameters g_m and g_{ds} ?
 - (ii) Calculate the total noise voltage at the output over a bandwidth of 20kHz. Use $g_{mn}=g_{mp}=100\mu A/V$, $g_{dsn}=g_{dsp}=2\mu A/V$
 - (iii) Calculate the total noise voltage at the output if the output is loaded by a capacitor $C_L=1pF$
- You may assume the following:

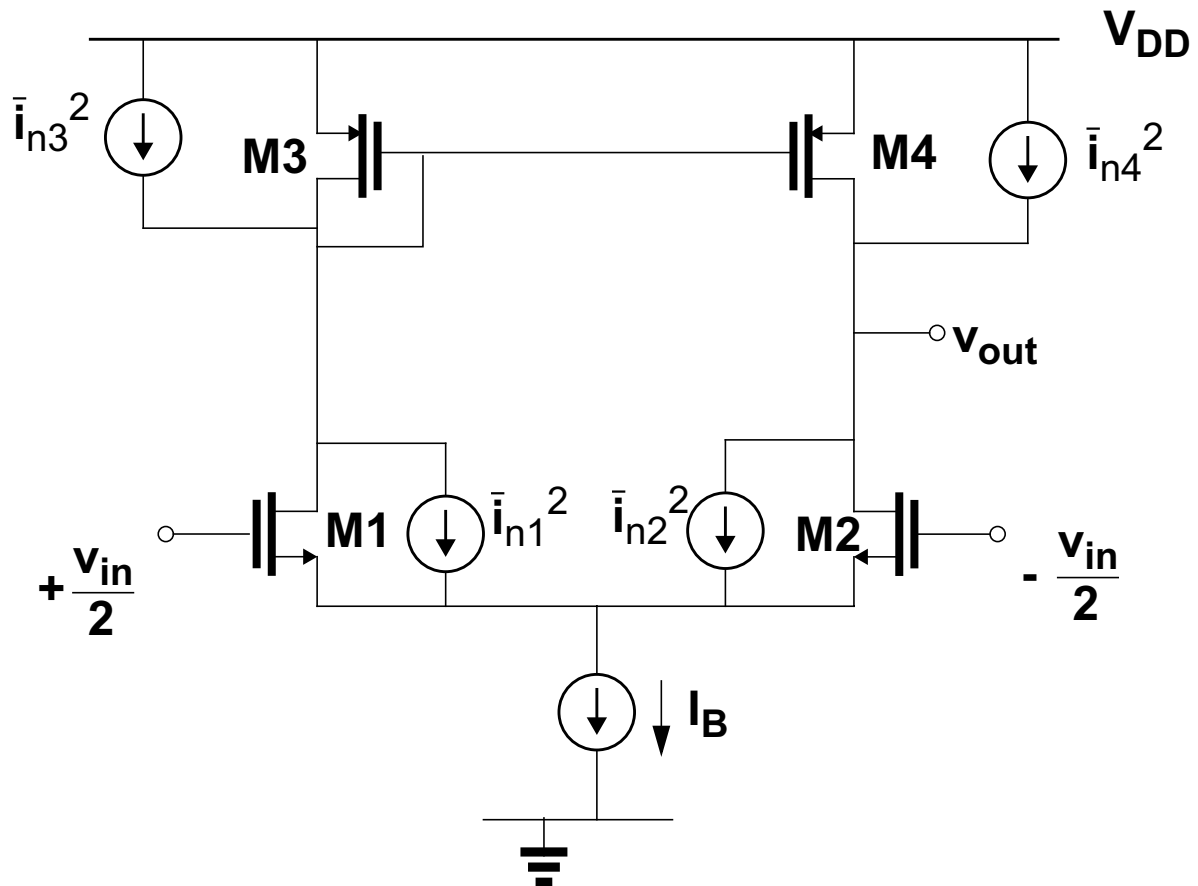


For the area underneath the curves to be the same then $f_n = (\pi/2) \cdot f_p$

- (iv) What is the SNR at the output if the input to the circuit is a differential sine wave of 10mVrms? Assume the frequency of the sine-wave is much less than the pole frequency.

Problem P. 329(Differential pair noise analysis).

- (i) What is the input-referred thermal noise voltage of the circuit shown in terms of the small signal parameters g_m and g_{ds} ?



Total noise current at output is square root of the individual noise currents

$$\overline{i_{nt}} = \sqrt{i_{n1}^2 + i_{n2}^2 + i_{n3}^2 + i_{n4}^2} = \sqrt{4kT\frac{2}{3}(2g_{mn} + 2g_{mp})}$$

where g_{mn}/g_{mp} are the transconductances of the nmos/pmos transistors

(Note that in calculating the total noise at the output, the noise currents of M1 and M3 are mirrored to the output node)

To refer this back to the input divide by g_{mn}

$$\overline{v_{ni}} = \frac{\overline{i_{nt}}}{g_{mn}} = \frac{\sqrt{4kT\frac{2}{3}(2g_{mn} + 2g_{mp})}}{g_{mn}} \quad V/\sqrt{Hz}$$

(ii) Calculate the total noise voltage at the output over a bandwidth of 20kHz.

Use $g_{mn}=g_{mp}=100\mu A/V$, $g_{dsn}=g_{dsp}=2\mu A/V$

Noise voltage at output is given by input-referred noise multiplied by voltage gain

$$\overline{v_{no}} = \overline{v_{ni}} \frac{g_{mn}}{g_{dsn} + g_{dsp}} = \frac{\sqrt{4kT\frac{2}{3}(2g_{mn} + 2g_{mp})}}{g_{mn}} \frac{g_{mn}}{(g_{dsn} + g_{dsp})}$$

$$= \frac{\sqrt{4kT\frac{2}{3}(2g_{mn} + 2g_{mp})}}{g_{dsn} + g_{dsp}}$$

$$= \frac{\sqrt{4 \times 1.38 \times 10^{-23} J/K \times 300 K \times \frac{2}{3} (2 \times 100 \mu A/V + 2 \times 100 \mu A/V)}}{2 \mu A/V + 2 \mu A/V}$$

$$= 525 nV / \sqrt{Hz}$$

Total integrated noise over a bandwidth of 20kHz:

$$\overline{v_{no-20kHz}} = 525 nV \cdot \sqrt{20 kHz} = 74.3 \mu V$$

(iii) Calculate the total noise voltage at the output if the output is loaded by a capacitor $C_L = 1\text{pF}$

Capacitor C_L connected between the output node and ground
=> pole at output node given by

$$|f_p| = \frac{g_{dsn} + g_{dsp}}{2\pi C_L}$$

Total noise voltage at the output is given by

$$\overline{v_{nototal}} = \overline{v_{no}} \sqrt{\frac{\pi}{2} f_p}$$

$$\overline{v_{nototal}} = \frac{\sqrt{4kT \frac{2}{3} (2g_{mn} + 2g_{mp})}}{(g_{dsn} + g_{dsp})} \cdot \sqrt{\frac{\pi}{2} \cdot \frac{(g_{dsn} + g_{dsp})}{2\pi C_L}}$$

$$\overline{v_{nototal}} = 525\text{nV} / \sqrt{\text{Hz}} \cdot \sqrt{\frac{2\mu\text{A}/V + 2\mu\text{A}/V}{4 \times 1\text{pF}}}$$

$$\overline{v_{nototal}} = 525\mu\text{V}$$

(iv) What is the SNR at the output if the input to the circuit is a differential sine wave of 10mV_{rms} ? Assume the frequency of the sine-wave is much less than the pole frequency.

The input signal is multiplied by the voltage gain of the circuit to give

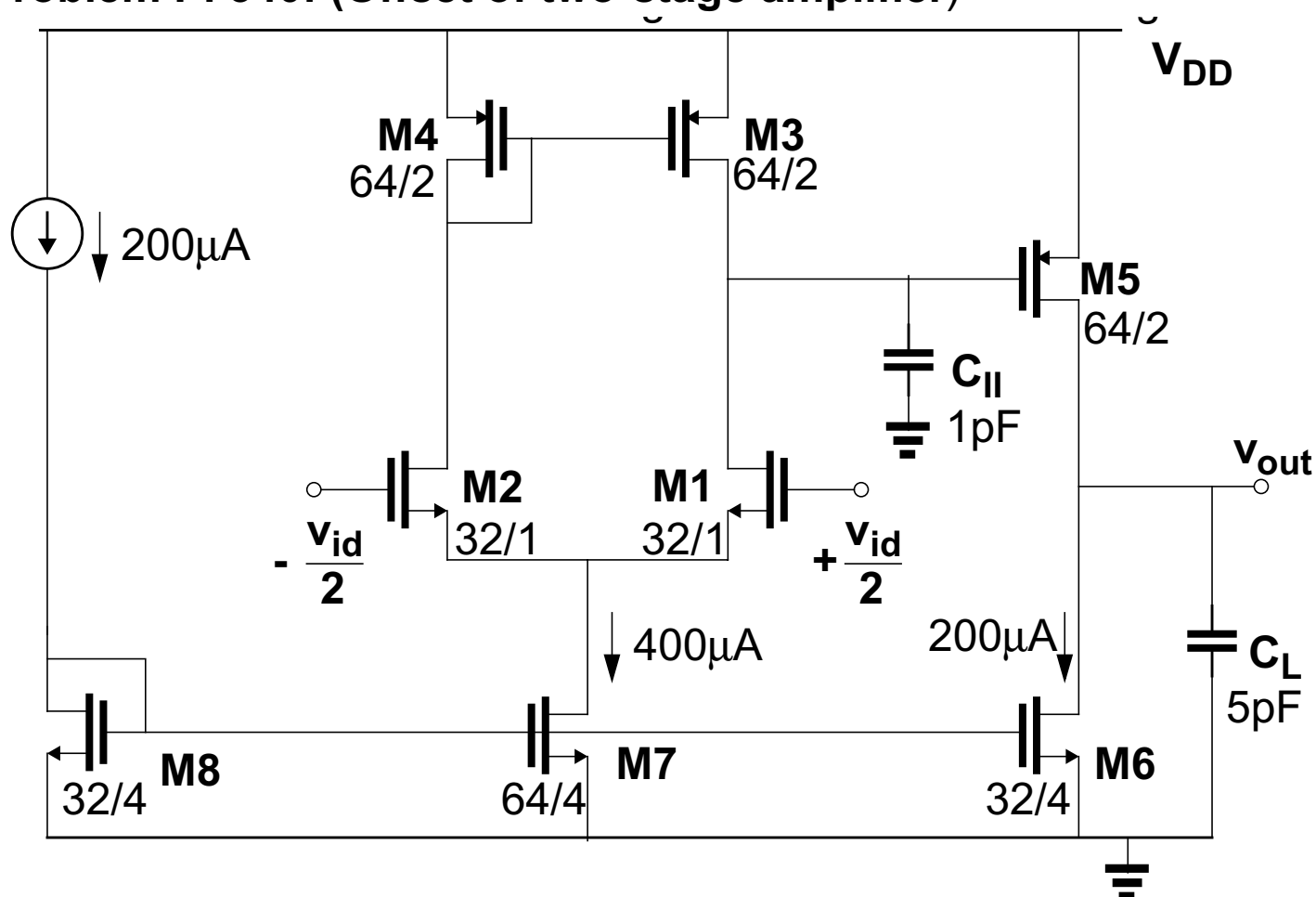
Output signal

$$v_{out} = -\frac{g_{m1}}{g_{dsn} + g_{dsp}} v_{in} = -\frac{100\mu}{2\mu + 2\mu} \cdot 10\text{mV}_{rms} = 250\text{mV}_{rms}$$

Signal-to-Noise ratio at output given by

$$\frac{S}{N} = \frac{250\text{mV}}{525\mu\text{V}} = 476 \quad \text{or } 53.6\text{dB}$$

Problem P. 340: (Offset of two-stage amplifier)



$$g_{m1} = 1.6mA/V$$

$$g_{m5} = 800\mu A/V$$

What is the input-referred offset of the amplifier shown?

Take $A_{Vt} = 10mV/\mu m$.

Note: In the following ΔV_t , ΔI refers to a 1 sigma mismatch in V_t , I , resp.

Solution

1. Contribution of input pair.

Input pair have offset voltage given by

$$\Delta V_{t1} = \frac{A_{Vt}}{\sqrt{(WL)_1}} = \frac{10mV\mu m}{\sqrt{32 \times 1}} = 1.77mV$$

2. Contribution of mirror pair M3 M4.

Mirror pair have offset voltage given by

$$\Delta V_{t3} = \frac{A_{Vt}}{\sqrt{(WL)_3}} = \frac{10mV\mu m}{\sqrt{64 \times 2}} = 0.88mV$$

These cause a mismatch in drain currents ΔI between M3 and M4

$$\Delta I = g_{m3} \Delta V_{t3}$$

To refer this to input divide by g_m of input pair

Input-referred offset voltage from mirror pair then given by

$$\Delta V_{t3inpref} = \frac{g_{m3} \Delta V_{t3}}{g_{m1}} = \frac{800\mu A/V \cdot 0.88mV}{1600\mu A/V} = 0.44mV$$

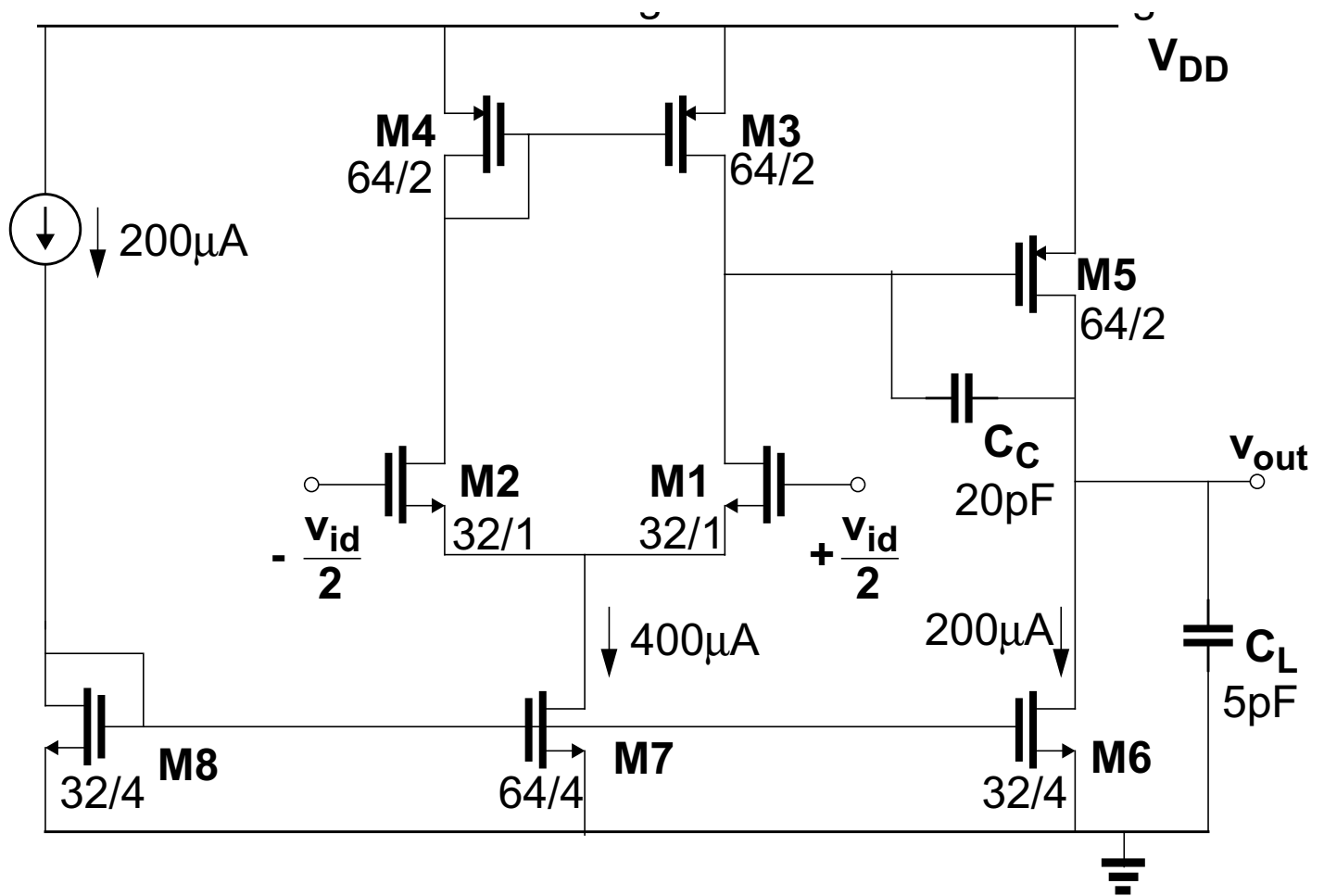
4. Total input referred offset

Sum contributions from input pair and mirror pair quadratically as offset is a random effect

$$\begin{aligned} V_{OSinpref} &= \sqrt{(\Delta V_{t1})^2 + (\Delta V_{t3inpref})^2} \\ &= \sqrt{1.77^2 + 0.44^2} = 1.82mV \end{aligned}$$

Conclusion: Offset of input pair is dominant. If it is required to reduce the overall offset the size of the input pair should be increased. In amplifier chains with large gain, offset cancellation may be required.

Problem P. 345 (Slew Rate of two-stage amplifier)



What is the slew rate of the amplifier shown?

Solution:

For C_{II} : max. current available to charge/discharge C_C is $400\mu A$

$$\text{Slew Rate} = \frac{400\mu A}{20pF} = 20\mu V/\mu s$$

For C_L :

Discharging C_L - max. current available to discharge C_L is the bias current of M6 = $200\mu A$

$$\text{Slew Rate} = \frac{200\mu A}{5pF} = 40\mu V/\mu s$$

Charging C_L - If a large positive step is applied to the input then all the $400\mu A$ bias current will flow through M1 and none through M2, M4, M3.

=> the gate of M5 will be pulled low, increasing the $|V_{GS}|$ of M5 and increasing the current through M5 far beyond the quiescent value of $200\mu A$ giving a slew rate of much greater than that for the case of discharging C_L

The overall slew rate of the amplifier is taken as the worst case value i.e.

$$\text{Slew Rate of amplifier} = 20\mu V/\mu s$$

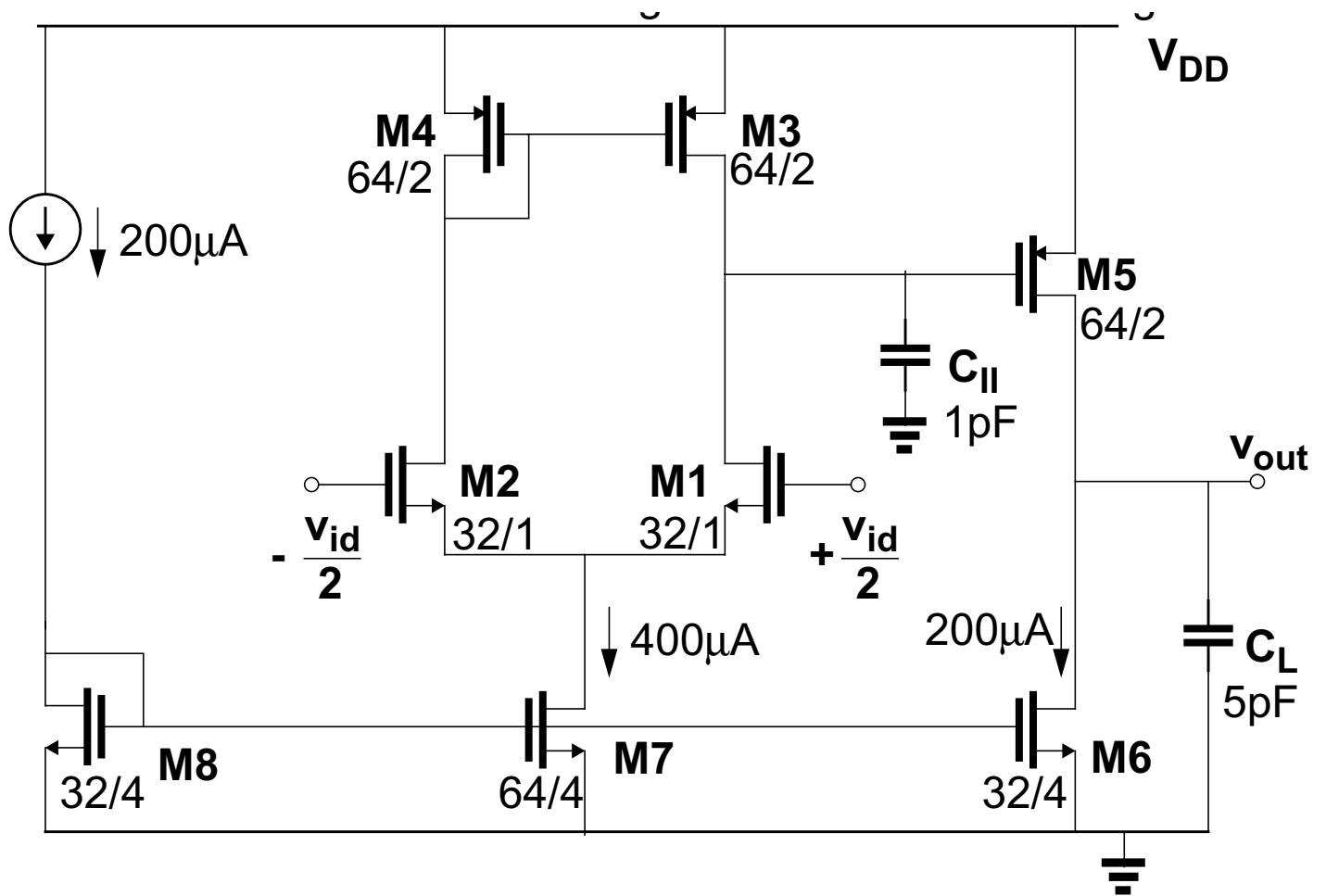
The significance of slew-rate is that even though the small-signal bandwidth may indicate a certain gain bandwidth, the slew-rate will often place a lower limit on the maximum frequency

$$GBW = \frac{g_{m1}}{C_C} = \frac{1.6mA/V}{20pF} = 80Mrad/s = 12.7MHz$$

For no slewing with 1Vpp sine wave at the output

$$f < \frac{I}{2\pi CA} = \frac{400\mu A}{2\pi \times 20pF \times 0.5} = 6.4MHz$$

Problem P. 348(Common-Mode Input Range)



What is the Common-mode input range of the amplifier shown?
 Take $V_{DD}=5\text{V}$, $V_{tn}=V_{tp}=0.8\text{V}$

1. Lower limit on V_{CM} :

$$V_{CM} \geq V_{GS1} + V_{SAT7}$$

$$V_{CM} \geq V_{GS1} + (V_{GS7} - V_t)$$

$$V_{GS} - V_t = \sqrt{\frac{2I_D}{K'_n \frac{W}{L}}}$$

$$\text{M1: } V_{GS1} - V_t = \sqrt{\frac{2 \cdot 200\mu A}{200\mu A/V \cdot \frac{32}{1}}} = 250mV$$

$$V_{GS1} = 250mV + V_t = 1.05V$$

$$\text{M7: } V_{GS7} - V_t = \sqrt{\frac{2 \cdot 400\mu A}{200\mu A/V \cdot \frac{64}{4}}} = 500mV$$

$$V_{CM} \geq 1.05V + 0.5V \Rightarrow V_{CM} \geq 1.55V$$

2. Upper limit:

$$V_{CM} \leq V_{DD} - |V_{GS4}| + V_{tn}$$

$$\text{M4 } |V_{GS4} - V_{tp}| = \sqrt{\frac{2 \cdot 200\mu A}{50\mu A/V \cdot \frac{64}{2}}} = 500mV$$

$$|V_{GS4}| = 500mV + |V_{tp}| = 1.30V$$

$$V_{CM} \leq V_{DD} - |V_{GS4}| + V_{tn}$$

$$V_{CM} \leq 5 - 1.30V + 0.8V$$

$$V_{CM} \leq 4.5V$$

=>Common-mode input range given by

$$1.55V \leq V_{CM} \leq 4.5V$$